

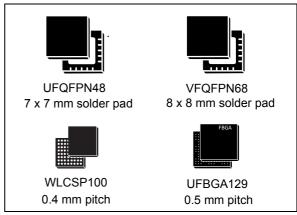
STM32WB55xx STM32WB35xx

Multiprotocol wireless 32-bit MCU Arm[®]-based Cortex[®]-M4 with FPU, Bluetooth[®] 5.3 and 802.15.4 radio solution

Datasheet - production data

Features

- Include ST state-of-the-art patented technology
- Radio
 - 2.4 GHz
 - RF transceiver supporting Bluetooth[®] 5.3 specification, IEEE 802.15.4-2011 PHY and MAC, supporting Thread and Zigbee[®] 3.0
 - RX sensitivity: -96 dBm (Bluetooth[®] Low Energy at 1 Mbps), -100 dBm (802.15.4)
 - Programmable output power up to +6 dBm with 1 dB steps
 - Integrated balun to reduce BOM
 - Support for 2 Mbps
 - Support advertising extension
 - Dedicated Arm[®] 32-bit Cortex[®] M0+ CPU for real-time Radio layer
 - Accurate RSSI to enable power control
 - Suitable for systems requiring compliance with radio frequency regulations ETSI EN 300 328, EN 300 440, FCC CFR47 Part 15 and ARIB STD-T66
 - Support for external PA
 - Available integrated passive device (IPD) companion chip for optimized matching solution (MLPF-WB-01E3, or MLPF-WB55-02E3, or MLPF-WB-02D3)
- Ultra-low-power platform
 - 1.71 to 3.6 V power supply
 - 40 °C to 85 / 105 °C temperature ranges
 - 13 nA shutdown mode
 - 600 nA Standby mode + RTC + 32 KB RAM
 - 2.1 µA Stop mode + RTC + 256 KB RAM
 - Active-mode MCU: < 53 μA / MHz when RF and SMPS on
 - Radio: Rx 4.5 mA / Tx at 0 dBm 5.2 mA



- Core: Arm[®] 32-bit Cortex[®]-M4 CPU with FPU, adaptive real-time accelerator (ART[™] Accelerator) allowing 0-wait-state execution from flash memory, frequency up to 64 MHz, MPU, 80 DMIPS and DSP instructions
- Performance benchmark
 - 1.25 DMIPS/MHz (Drystone 2.1)
 - 219.48 CoreMark[®] (3.43 CoreMark/MHz at 64 MHz)
- Energy benckmark
 - 303 ULPMark™ CP score
- Supply and reset management
 - High efficiency embedded SMPS step-down converter with intelligent bypass mode
 - Ultra-safe, low-power BOR (brownout reset) with five selectable thresholds
 - Ultra-low-power POR/PDR
 - Programmable voltage detector (PVD)
 - V_{BAT} mode with RTC and backup registers
- · Clock sources
 - 32 MHz crystal oscillator with integrated trimming capacitors (Radio and CPU clock)
 - 32 kHz crystal oscillator for RTC (LSE)
 - Internal low-power 32 kHz (±5%) RC (LSI1)
 - Internal low-power 32 kHz (stability ±500 ppm) RC (LSI2)

- Internal multispeed 100 kHz to 48 MHz oscillator, auto-trimmed by LSE (better than ±0.25% accuracy)
- High speed internal 16 MHz factory trimmed RC (±1%)
- 2x PLL for system clock, USB, SAI and ADC

Memories

- Up to 1 MB flash memory with sector protection (PCROP) against R/W operations, enabling radio stack and application
- Up to 256 KB SRAM, including 64 KB with hardware parity check
- 20x 32-bit backup register
- Boot loader supporting USART, SPI, I2C and USB interfaces
- OTA (over the air) Bluetooth[®] Low Energy and 802.15.4 update
- Quad SPI memory interface with XIP
- 1 Kbyte (128 double words) OTP
- Rich analog peripherals (down to 1.62 V)
 - 12-bit ADC 4.26 Msps, up to 16-bit with hardware oversampling, 200 μA/Msps
 - 2x ultra-low-power comparator
 - Accurate 2.5 V or 2.048 V reference voltage buffered output

• System peripherals

- Inter processor communication controller (IPCC) for communication with Bluetooth[®] Low Energy and 802.15.4
- HW semaphores for resources sharing between CPUs
- 2x DMA controllers (7x channels each) supporting ADC, SPI, I2C, USART, QSPI, SAI, AES, timers
- 1x USART (ISO 7816, IrDA, SPI Master, Modbus and Smartcard mode)
- 1x LPUART (low power)
- 2x SPI 32 Mbit/s
- 2x I2C (SMBus/PMBus[®])
- 1x SAI (dual channel high quality audio)

- 1x USB 2.0 FS device, crystal-less, BCD and LPM
- Touch sensing controller, up to 18 sensors
- LCD 8x40 with step-up converter
- 1x 16-bit, four channels advanced timer
- 2x 16-bit, two channels timer
- 1x 32-bit, four channels timer
- 2x 16-bit ultra-low-power timer
- 1x independent Systick
- 1x independent watchdog
- 1x window watchdog

Security and ID

- Secure firmware installation (SFI) for Bluetooth[®] Low Energy and 802.15.4 SW stack
- 3x hardware encryption AES maximum 256-bit for the application, the Bluetooth[®] Low Energy and IEEE802.15.4
- Customer key storage / key manager services
- HW public key authority (PKA)
- Cryptographic algorithms: RSA,
 Diffie-Helman, ECC over GF(p)
- True random number generator (RNG)
- Sector protection against R/W operation (PCROP)
- CRC calculation unit
- Die information: 96-bit unique ID
- IEEE 64-bit unique ID, possibility to derive 802.15.4 64-bit and Bluetooth[®] Low Energy 48-bit EUI
- Up to 72 fast I/Os, 70 of them 5 V-tolerant
- Development support
 - Serial wire debug (SWD), JTAG for the application processor
 - Application cross trigger with input / output
 - Embedded Trace Macrocell™ for application
- All packages are ECOPACK2 compliant

Table 1. Device summary

Reference	Part numbers							
STM32WB55xx	STM32WB55CC, STM32WB55CE, STM32WB55CG, STM32WB55RC, STM32WB55RE, STM32WB55RG, STM32WB55VC, STM32WB55VE, STM32WB55VG, STM32WB55VY							
STM32WB35xx	STM32WB35CC, STM32WB35CE							



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1 Introduction

This document provides the ordering information and mechanical device characteristics of the STM32WB55xx and STM32WB35xx microcontrollers, based on Arm[®] cores^(a).

This document must be read with the reference manual (RM0434), available from the STMicroelectronics website *www.st.com*.

For information on the device errata with respect to the datasheet and reference manual, refer to the STM32WB55xx and STM32WB35xx errata sheet (ES0394), available from the STMicroelectronics website *www.st.com*.

For information on the Arm[®] Cortex[®]-M4 and Cortex[®]-M0+ cores, refer, respectively, to the Cortex[®]-M4 Technical Reference Manual and to the Cortex[®]-M0+ Technical Reference Manual, both available on the www.arm.com website.

For information on 802.15.4 refer to the IEEE website (www.ieee.org).

For information on Bluetooth® refer to www.bluetooth.com.







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2 Description

The STM32WB55xx and STM32WB35xx multiprotocol wireless and ultra-low-power devices embed a powerful and ultra-low-power radio compliant with the Bluetooth[®] Low Energy SIG specification 5.3 and with IEEE 802.15.4-2011. They contain a dedicated Arm[®] Cortex[®]-M0+ for performing all the real-time low layer operation.

The devices are designed to be extremely low-power and are based on the high-performance Arm[®] Cortex[®]-M4 32-bit RISC core operating at a frequency of up to 64 MHz. This core features a Floating point unit (FPU) single precision that supports all Arm[®] single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) that enhances application security.

Enhanced inter-processor communication is provided by the IPCC with six bidirectional channels. The HSEM provides hardware semaphores used to share common resources between the two processors.

The devices embed high-speed memories (up to 1 Mbyte of flash memory for STM32WB55xx, up to 512 Kbytes for STM32WB35xx, up to 256 Kbytes of SRAM for STM32WB55xx, 96 Kbytes for STM32WB35xx), a Quad-SPI flash memory interface (available on all packages) and an extensive range of enhanced I/Os and peripherals.

Direct data transfer between memory and peripherals and from memory to memory is supported by fourteen DMA channels with a full flexible channel mapping by the DMAMUX peripheral.

The devices feature several mechanisms for embedded flash memory and SRAM: readout protection, write protection and proprietary code readout protection. Portions of the memory can be secured for Cortex[®] -M0+ exclusive access.

The two AES encryption engines, PKA, and RNG enable lower layer MAC and upper layer cryptography. A customer key storage feature may be used to keep the keys hidden.

The devices offer a fast 12-bit ADC and two ultra-low-power comparators associated with a high accuracy reference voltage generator.

These devices embed a low-power RTC, one advanced 16-bit timer, one general-purpose 32-bit timer, two general-purpose 16-bit timers, and two 16-bit low-power timers.

In addition, up to 18 capacitive sensing channels are available for STM32WB55xx (not on UFQFPN48 package). The STM32WB55xx also embed an integrated LCD driver up to 8x40 or 4x44, with internal step-up converter.

The STM32WB55xx and STM32WB35xx also feature standard and advanced communication interfaces, namely one USART (ISO 7816, IrDA, Modbus, and Smartcard mode), one low- power UART (LPUART), two I2Cs (SMBus/PMBus), two SPIs (one for STM32WB35xx) up to 32 MHz, one serial audio interface (SAI) with two channels and three PDMs, one USB 2.0 FS device with embedded crystal-less oscillator, supporting BCD and LPM and one Quad-SPI with execute-in-place (XIP) capability.

The STM32WB55xx and STM32WB35xx operate in the -40 to +105 °C (+125 °C junction) and -40 to +85 °C (+105 °C junction) temperature ranges from a 1.71 to 3.6 V power supply. A comprehensive set of power-saving modes enables the design of low-power applications.

The devices include independent power supplies for analog input for ADC.



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The STM32WB55xx and STM32WB35xx integrate a high efficiency SMPS step-down converter with automatic bypass mode capability when the V_{DD} falls below V_{BORx} (x = 1, 2, 3, 4) voltage level (default is 2.0 V). It includes independent power supplies for analog input for ADC and comparators, as well as a 3.3 V dedicated supply input for USB.

A V_{BAT} dedicated supply allows the devices to back up the LSE 32.768 kHz oscillator, the RTC and the backup registers, thus enabling the STM32WB55xx and STM32WB35xx to supply these functions even if the main V_{DD} is not present through a CR2032-like battery, a Supercap or a small rechargeable battery.

The STM32WB55xx offer four packages, from 48 to 129 pins. The STM32WB35xx offer one package, 48 pins.

Table 2. STM32WB55xx and STM32WB35xx devices features and peripheral counts

Feature		STM32WB55Cx			STM32WB55Rx			STM32WB55Vx				STM32WB35Cx		
	Flash	256 K	512 K	1 M	256 K	512 K	1 M	256 K	512 K	1 M	640 K	256 K	512 K	
Memory	SRAM	128 K	256 K	256 K	128 K	256 K	256 K	128 K	256 K	25	6 K	96	K	
density (bytes)	SRAM1	64 K	192	2 K	64 K	192	2 K	64 K		192 K		32	32 KB	
	SRAM2						6	4 K						
Bluetooth Low Energy			5.3 (2 Mbps)											
802.15.4							١	⁄es						
	Advanced						1 (1	6 bits)						
Timers	General purpose					2 (16 bits)	+ 1 (32	bits)					
	Low power		2 (16 bits)											
	SysTick							1						
es	SPI		1 2 1											
ıfacı	I2C	2												
Communication interfaces	USART ⁽¹⁾		1											
ation	LPUART	1												
, in	SAI		2 channels											
mm	USB FS		Yes											
_	QSPI		1											
RTC			1											
Tamper p	oin		1					3				,		
Wakeup	pin		2					5				2	2	
LCD, CO	MxSEG	١	es, 4x1	3	Yes, 4x28 Yes, 8x40 or 4x44		4	No						
GPIOs			30		49 72			30						
Capacitiv	e sensing		No		6 18			No						
12-bit AD Number	OC of channels		13 channels (incl. 3 internal) 19 channels (incl. 3 internal) 13 channels (incl. 3 internal)											
Internal \	/ _{ref}						١	⁄es						

Table 2. STM32WB55xx and STM32WB35xx devices features and peripheral counts (continued)

Fe	ature	STM32WB55Cx	(STM32WB35Cx						
Analog o	omparator			2						
Max CPI	J frequency		64	MHz						
ating rature	Ambient	-40	-40 to +85 and -40 to +105 °C							
Operating temperature	Junction	-40	-40 to +105 °C	-40 to +105 and -40 to +125 °C						
Operatin	g voltage	1.71 to 3.6 V								
Package	UFQFPN48 7 mm x 7 mm		VFQFPN68 8 mm x 8 mm	WLCSP100 0.4 mm pitch		UFQFPN48 7 mm x 7 mm				
ackage		0.5 mm pitch, solder pad	0.4 mm pitch, solder pad	UFBGA129 0.5 mm pitch	_	0.5 mm pitch, solder pad				

^{1.} USART peripheral can be used as SPI.

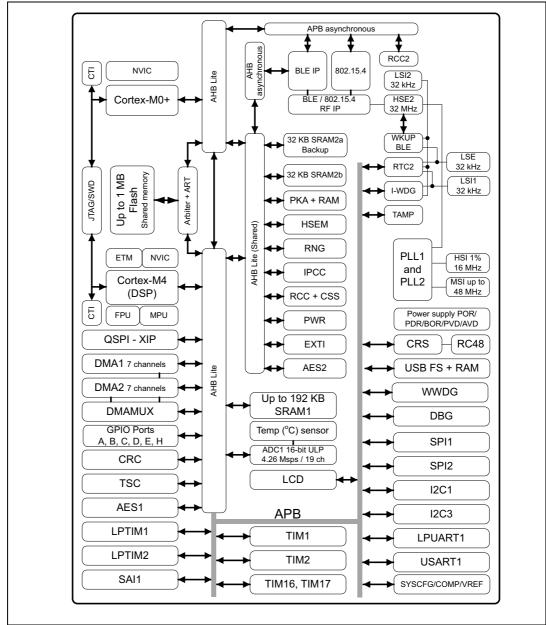


Figure 1. STM32WB55xx block diagram

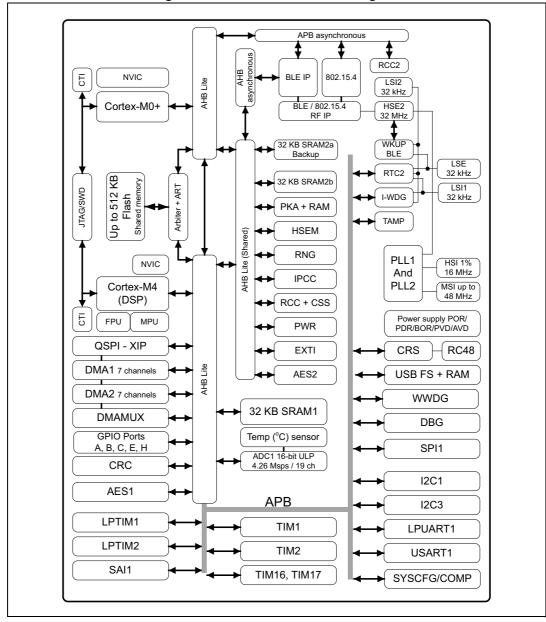


Figure 2. STM32WB35xx block diagram

3 Functional overview

3.1 Architecture

The STM32WB55xx and STM32WB35xx multiprotocol wireless devices embed a Bluetooth Low Energy and an 802.15.4 RF subsystem that interfaces with a generic microcontroller subsystem using an Arm[®] Cortex[®]-M4 CPU (called CPU1) on which the host application resides.

The RF subsystem is composed of an RF analog front end, Bluetooth Low Energy and 802.15.4 digital MAC blocks as well as of a dedicated Arm[®] Cortex[®]-M0+ microcontroller (called CPU2), plus proprietary peripherals. The RF subsystem performs all of the Bluetooth Low Energy and 802.15.4 low layer stack, reducing the interaction with the CPU1 to high level exchanges.

Some functions are shared between the RF subsystem CPU (CPU2) and the Host CPU (CPU1):

- Flash memories
- SRAM1, SRAM2a, and SRAM2b (SRAM2a can be retained in Standby mode)
- Security peripherals (RNG, AES1, PKA)
- Clock RCC
- Power control (PWR)

The communication and the sharing of peripherals between the RF subsystem and the Cortex[®]-M4 CPU is performed through a dedicated inter processor communication controller (IPCC) and semaphore mechanism (HSEM).

3.2 Arm[®] Cortex[®]-M4 core with FPU

The Arm[®] Cortex[®]-M4 with FPU is a processor for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The Arm[®] Cortex[®]-M4 with FPU 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an Arm[®] core in the memory size usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions enabling efficient signal processing and complex algorithm execution.

Its single precision FPU speeds up software development by using metalanguage development tools, while avoiding saturation.

With its embedded ${\rm Arm}^{\rm @}$ core, the STM32WB55xx and STM32WB35xx are compatible with all ${\rm Arm}^{\rm @}$ tools and software.

Figure 1 and Figure 2 show the general block diagram of, respectively, the STM32WB55xx and STM32WB35xx devices.

3.3 Memories

3.3.1 Adaptive real-time memory accelerator (ART Accelerator)

The ART Accelerator is a memory accelerator optimized for STM32 industry-standard Arm[®] Cortex[®]-M4 processors. It balances the inherent performance advantage of the Arm[®] Cortex[®]-M4 over flash memory technologies, which normally require the processor to wait for the flash memory at higher frequencies.

To release the processor near 80 DMIPS performance at 64 MHz, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 64-bit flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from flash memory at a CPU frequency up to 64 MHz.

3.3.2 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU1 accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to eight protected areas, which can be divided up into eight subareas. The protection area sizes are between 32 bytes and the whole 4 Gbytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code must be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location prohibited by the MPU, the RTOS detects it and acts. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.3.3 Embedded flash memory

The STM32WB55xx and STM32WB35xx devices feature, respectively, up to 1 Mbyte and 512 Kbytes of embedded flash memory available for storing programs and data, as well as some customer keys.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
 - Level 0: no readout protection
 - Level 1: memory readout protection: the flash memory cannot be read from or written to if either debug features are connected, boot in SRAM or bootloader is selected
 - Level 2: chip readout protection: debug features (Cortex[®]-M4 and Cortex[®]-M0+ JTAG and serial wire), boot in SRAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Area	Protection level	U	ser executio	on	Debug, boot from SRAM or boot from system memory (loader)					
	ievei	Read	Write	Erase	from sys se	Write	Erase			
Main	1	Yes	Yes	Yes	No	No	No			
memory System	2	Yes	Yes	Yes	N/A	N/A	N/A			
System memory	1	Yes	No	No	Yes	No	No			
	2	Yes	No	No	N/A	N/A	N/A			
Option	1	Yes	Yes	Yes	Yes	Yes	Yes			
bytes	2	Yes	No ⁽¹⁾	No ⁽¹⁾	N/A	N/A	N/A			
Backup	1	Yes	Yes	N/A ⁽²⁾	No	No	N/A ⁽²⁾			
registers	2	Yes	Yes	N/A	N/A	N/A	N/A			
SRAM2a	1	Yes	Yes	Yes ⁽²⁾	No	No	No ⁽²⁾			
SRAM2b	2	Yes	Yes	Yes	N/A	N/A	N/A			

Table 3. Access status vs. readout protection level and execution modes

- 1. The option byte can be modified by the RF subsystem.
- 2. Erased when RDP changes from Level 1 to Level 0.
- Write protection (WRP): the protected area is protected against erasing and programming. Two areas can be selected, with 4-Kbyte granularity.
- Proprietary code readout protection (PCROP): two parts of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. Two areas can be selected, with 2-Kbyte granularity. An additional option bit (PCROP_RDP) makes possible to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

A section of the flash memory is secured for the RF subsystem CPU2, and cannot be accessed by the host CPU1.

The whole nonvolatile memory embeds the error correction code (ECC) feature supporting:

- single error detection and correction
- double error detection
- the address of the ECC fail can be read in the ECC register

The embedded flash memory is shared between CPU1 and CPU2 on a time sharing basis. A dedicated HW mechanism allows both CPUs to perform Write/Erase operations.

3.3.4 Embedded SRAM

The STM32WB55xx devices feature up to 256 Kbytes of embedded SRAM, split in three blocks:

- SRAM1: up to 192 Kbytes mapped at address 0x2000 0000
- **SRAM2a**: 32 Kbytes located at address 0x2003 0000 also mirrored at 0x1000 0000, with hardware parity check (this SRAM can be retained in Standby mode)
- **SRAM2b**: 32 Kbytes located at address 0x2003 8000 (contiguous with SRAM2a) and mirrored at 0x1000 8000 with hardware parity check

The STM32WB35xx devices feature 96 Kbytes of embedded SRAM, split in three blocks:

- SRAM1: 32 Kbytes mapped at address 0x2000 0000
- **SRAM2a**: 32 Kbytes located at address 0x2003 0000 also mirrored at 0x1000 0000, with hardware parity check (this SRAM can be retained in Standby mode)
- SRAM2b: 32 Kbytes located at address 0x2003 8000 (contiguous with SRAM2a) and mirrored at 0x1000 8000 with hardware parity check

SRAM2a and SRAM2b can be write-protected, with 1-Kbyte granularity. A section of the SRAM2a and SRAM2b is secured for the RF sub-system and cannot be accessed by the host CPU1.

The SRAMs can be accessed in read/write with 0 wait states for all CPU1 and CPU2 clock speeds.

3.4 Security and safety

The STM32WB55xx and STM32WB35xx contain many security blocks both for the Bluetooth Low Energy or IEEE 802.15.4 and the Host application.

It includes:

- Customer storage of the Bluetooth Low Energy and 802.15.4 keys
- · Secure flash memory partition for RF subsystem-only access
- Secure SRAM partition, that can be accessed only by the RF subsystem
- True random number generator (RNG)
- Advance encryption standard hardware accelerators (AES-128bit and AES-256bit, supporting chaining modes ECB, CBC, CTR, GCM, GMAC, CCM)
- Private key acceleration (PKA) including:
 - Modular arithmetic including exponentiation with maximum modulo size of 3136 bits
 - Elliptic curves over prime field scalar multiplication, ECDSA signature, ECDSA verification with maximum modulo size of 521 bits
- Cyclic redundancy check calculation unit (CRC)

A specific mechanism is in place to ensure that all the code executed by the RF subsystem CPU2 can be secure, whatever the Host application. For the AES1 a customer key can be managed by the CPU2 and used by the CPU1 to encrypt/decrypt data.

3.5 **Boot modes and FW update**

At startup, BOOT0 pin and BOOT1 option bit are used to select one of three boot options:

- Boot from user flash
- Boot from system memory
- Boot from embedded SRAM

The devices always boot on CPU1 core. The embedded bootloader code makes it possible to boot from various peripherals:

- **USB**
- **UART**
- 12C
- SPI

Secure Firmware update (especially Bluetooth Low Energy and 802.15.4) from system boot and over the air is provided.

3.6 RF subsystem

The STM32WB55xx and STM32WB35xx embed an ultra-low power multi-standard radio Bluetooth Low Energy and 802.15.4 network processor, compliant with Bluetooth specification 5.3 and IEEE® 802.15.4-2011. The Bluetooth Low Energy features 1 Mbps and 2 Mbps transfer rates, supports multiple roles simultaneously acting at the same time as Bluetooth Low Energy sensor and hub device, embeds Elliptic Curve Diffie-Hellman (ECDH) key agreement protocol, thus ensuring a secure connection.

The Bluetooth Low Energy stack and 802.15.4 Low Level layer run on an embedded Arm® Cortex®-M0+ core (CPU2). The stack is stored on the embedded flash memory, which is also shared with the Arm[®] Cortex[®]-M4 (CPU1) application, making it possible in-field stack update.

3.6.1 RF front-end block diagram

The RF front-end is based on a direct modulation of the carrier in Tx, and uses a low IF architecture in Rx mode.

Thanks to an internal transformer at RF pins, the circuit directly interfaces the antenna (single ended connection, impedance close to 50 Ω). The natural bandpass behavior of the internal transformer, simplifies outside circuitry aimed for harmonic filtering and out of band interferer rejection.

In Transmit mode, the maximum output power is user selectable through the programmable LDO voltage of the power amplifier. A linearized, smoothed analog control offers clean power ramp-up.

In receive mode the circuit can be used in standard high performance or in reduced power consumption (user programmable). The Automatic gain control (AGC) is able to reduce the chain gain at both RF and IF locations, for optimized interference rejection. Thanks to the use of complex filtering and highly accurate I/Q architecture, high sensitivity and excellent linearity can be achieved.

The bill of material is reduced thanks to the high degree of integration. The radio frequency source is synthesized form an external 32 MHz crystal that does not need any external



trimming capacitor network thanks to a dual network of user programmable integrated capacitors.

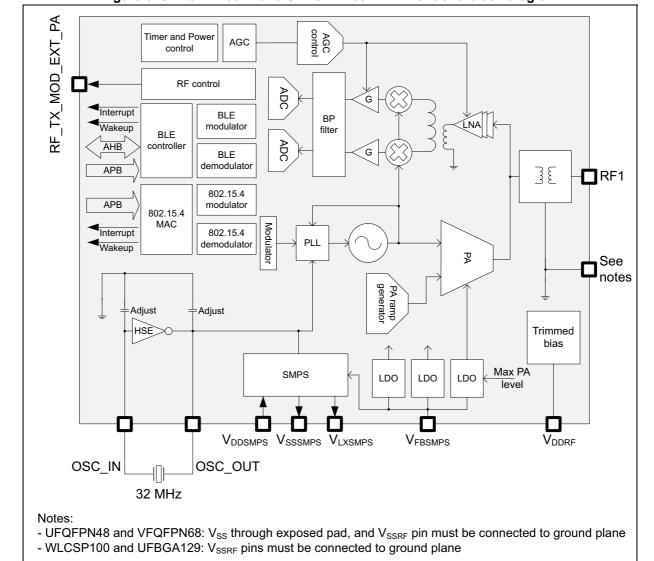


Figure 3. STM32WB55xx and STM32WB35xx RF front-end block diagram

3.6.2 Bluetooth Low Energy general description

The Bluetooth Low Energy block is a master/slave processor, compliant with Bluetooth specification 5.3 standard (2 Mbps).

It integrates a 2.4 GHz RF transceiver and a powerful Cortex[®]-M0+ core, on which a complete power-optimized stack for Bluetooth Low Energy protocol runs, providing master / slave role support

- GAP: central, peripheral, observer or broadcaster roles
- ATT/GATT: client and server
- SM: privacy, authentication and authorization
- L2CAP
- Link layer: AES-128 encryption and decryption

In addition, according to Bluetooth specification 5.3, the Bluetooth Low Energy block provides:

- Multiple roles simultaneous support
- Master/slave and multiple roles simultaneously
- LE data packet length extension (making it possible to reach 800 kbps at application level)
- LE privacy 1.2
- LE secure connections
- Flexible Internet connectivity options
- High data rate (2 Mbps)

The devices support Piconet topology (master with up to eight slaves), Scatternet topology (master with up to six slaves and dynamically as slave with up to two masters, or master with up to four slaves and dynamically as slave with up to four masters), and multi slave topology (slave with up to eight masters).

The device allows the applications to meet the tight peak current requirements imposed by the use of standard coin cell batteries. When the high efficiency embedded SMPS step-down converter is used, the RF front end consumption (I_{tmax}) is only 7.8 mA at the highest output power (+6 dBm).

The power efficiency of the subsystem is optimized: while running with the radio and the applicative cores simultaneously using the SMPS, the Cortex $^{\text{\tiny B}}$ -M4 core consumption reaches 53 μA / MHz in active mode.

Ultra-low-power sleep modes and very short transition time between operating modes result in very low average current consumption during real operating conditions, resulting in longer battery life.

The Bluetooth Low Energy block integrates a full bandpass balun, thus reducing the need for external components.

The link between the Cortex[®]-M4 application processor (CPU1) running the application, and the Bluetooth Low Energy stack running on the dedicated Cortex[®]-M0+ (CPU2) is performed through a normalized API, using a dedicated IPCC.

3.6.3 802.15.4 general description

The STM32WB55xx and STM32WB35xx embed a dedicated 802.15.4 hardware MAC:

- Support for 802.15.4 release 2011
- Advanced MAC frame filtering; hardwired firewall: Programmable filters based on source/destination addresses, frame version, security enabled, frame type
- 256-byte RX FIFO; Up to 8 frames capacity, additional frame information (timing, mean RSSI, LQI)
- 128-byte TX FIFO with retention
 - Content not lost, retransmissions possible under CPU2 control
- Automatic frame acknowledgment, with programmable delay
- Advanced channel access features
 - Full CSMA-CA support
 - Superframe timer
 - Beaconing support (require LSE)
 - Flexible TX control with programmable delay
- Configuration registers with retention available down to Standby mode for software/auto-restore
- Autonomous sniffer, wake-up based on timer or CPU2 request
- Automatic frame transmission/reception/sleep periods, Interrupt to the CPU2 on particular events

3.6.4 RF pin description

The RF block contains dedicated pins, listed in Table 4.

Table 4. RF pin list

Name	Туре	Description				
RF1		RF Input/output, must be connected to the antenna through a low-pass matching network				
OSC_OUT		32 MHz main oscillator, also used as HSE source				
OSC_IN	I/O					
RF_TX_ MOD_EXT_PA		External PA transmit control				
VDDRF	V_{DD}	Dedicated supply, must be connected to V _{DD}				
VSSRF ⁽¹⁾	V _{SS}	To be connected to GND				

^{1.} On packages with exposed pad, this pad must be connected to GND plane for correct RF operation.

3.6.5 Typical RF application schematic

The schematic in *Figure 4* and the external components listed in *Table 4* are purely indicative. For more details refer to the "Reference design" provided in separate documents.

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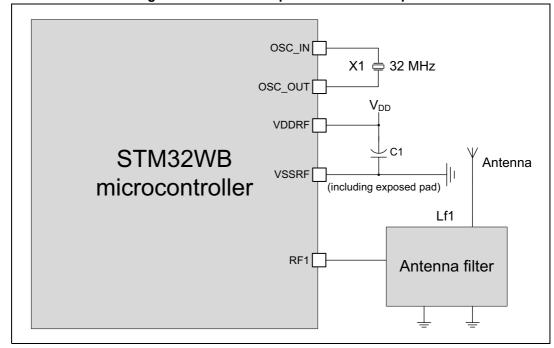


Figure 4. External components for the RF part

Table 5. Typical external components

Component	Description	Value
C1	Decoupling capacitance for RF	100 nF // 100 pF
X1	32 MHz crystal ⁽¹⁾	32 MHz
Antenna filter	Antenna filter and matching network	Refer to AN5165, on www.st.com
Antenna	2.4 GHz band antenna	-

^{1.} e.g. NDK reference: NX2016SA 32 MHz EXS00A-CS06654.

Note: For more details refer to AN5165 "Development of RF hardware using STM32WB microcontrollers" available on www.st.com.

3.7 Power supply management

3.7.1 Power supply distribution

The device integrate an SMPS step-down converter to improve low power performance when the V_{DD} voltage is high enough. This converter has an intelligent mode that automatically enters in bypass mode when the V_{DD} voltage falls below a specific BORx (x = 1, 2, 3 or 4) voltage.

By default, at reset, the SMPS is in bypass mode.

The device can be operated without the SMPS by just wiring its output to V_{DD} . This is the case for applications where the voltage is low, or where the power consumption is not critical.



 V_{DD} VDDSMPS VDDSMPS **SMPS SMPS** VLXSMPS VLXSMPS SMPS mode or (not used) BYPASS mode **LPR LPR** VFBSMPS VFBSMPS **RFR** MR **RFR** MR SMPS configuration LDO configuration MS41409V4

Figure 5. Power distribution

Table 6. Power supply typical components

Component	Descript	Value	
C2	SMPS output capacitor ⁽¹⁾		4.7 μF
I 1 ⁽²⁾	SMPS inductance	For 8 MHz ⁽³⁾	2.2 μΗ
LIV'	SWIF S IIIUUCIAIICE	For 4 MHz ⁽⁴⁾	10 µH

- 1. Such as GRM155R60J475KE19.
- To improve the receiver performance an extra 10 nH inductor (e.g Murata LQG15WZ10NJ02D) in series with L1 is needed.
- 3. Such as Wurth 74479774222.
- 4. Such as Murata LQM21FN100M70L.

The SMPS can also be switched on or set in bypass mode at any time by the application software, for example when very accurate ADC measurement are needed.

3.7.2 Power supply schemes

The devices have different voltage supplies (see *Figure 7* and *Figure 8*) and can operate within the following voltage ranges:

- V_{DD} = 1.71 to 3.6 V: external power supply for I/Os (V_{DDIO}), the internal regulator and system functions such as RF, SMPS, reset, power management and internal clocks. It is provided externally through VDD pins. V_{DDRF} and V_{DDSMPS} must be always connected to VDD pins.
- V_{DDA} = 1.62 (ADC/COMPs) to 3.6 V: external analog power supply for ADC, comparators and voltage reference buffer. The V_{DDA} voltage level can be independent from the V_{DD} voltage. When not used V_{DDA} must be connected to V_{DD}.
- V_{DDUSB} = 3.0 to 3.6 V: external independent power supply for USB transceivers. When not used V_{DDUSB} must be connected to V_{DD} or ground.
- V_{LCD} = 2.5 to 3.6 V: the LCD controller can be powered either externally through the VLCD pin, or internally from an internal voltage generated by the embedded step-up converter. This converter can generate a V_{LCD} voltage up to 3.6 V if V_{DD} is higher than 2.0 V. Note that the LCD is available only on STM32WB55xx devices.

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During power up/down, the following power sequence requirements must be respected:

- When V_{DD} is below 1 V the other power supplies (V_{DDA} , V_{DDUSB} , V_{LCD}), must remain below V_{DD} + 300 mV
- When V_{DD} is above 1 V all power supplies are independent.

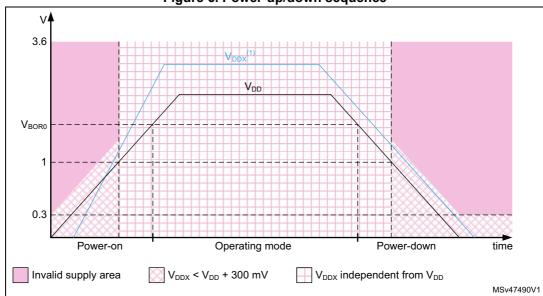


Figure 6. Power-up/down sequence

1. V_{DDX} refers to any power supply among V_{DDA} , V_{DDUSB} and V_{LCD} .

During the power down phase, V_{DD} can temporarily become lower than other supplies only if the energy provided to the MCU remains below 1 mJ. This allows the external decoupling capacitors to be discharged with different time constants during the power down transient phase.

Note:

 V_{DD} , V_{DDRF} and V_{DDSMPS} must be wired together, so they can follow the same voltage sequence.



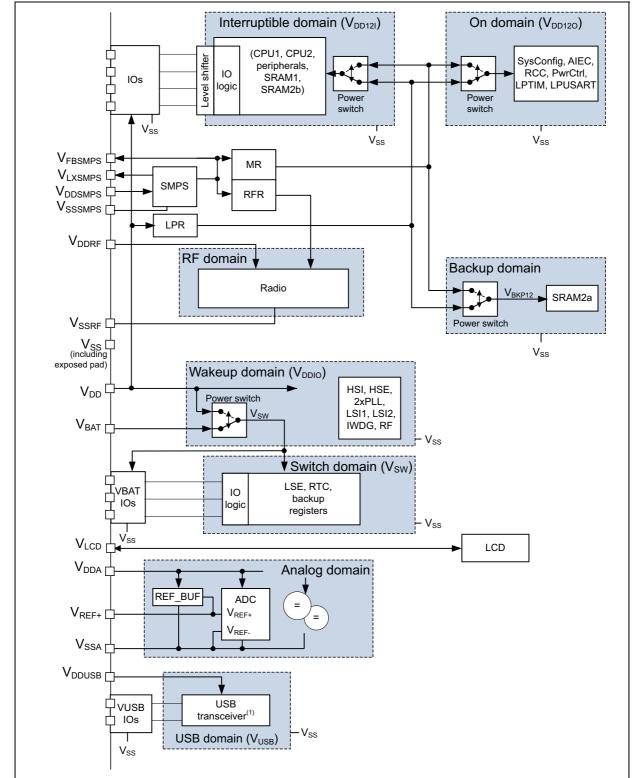


Figure 7. STM32WB55xx - Power supply overview

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The USB transceiver is powered by V_{DDUSB}, and the GPIOs associated with USB are powered by V_{DDUSB} when USB alternate function (PA11 and PA12) is selected. When USB alternate function is not selected the GPIOs associated with USB are powered as standard GPIOs.

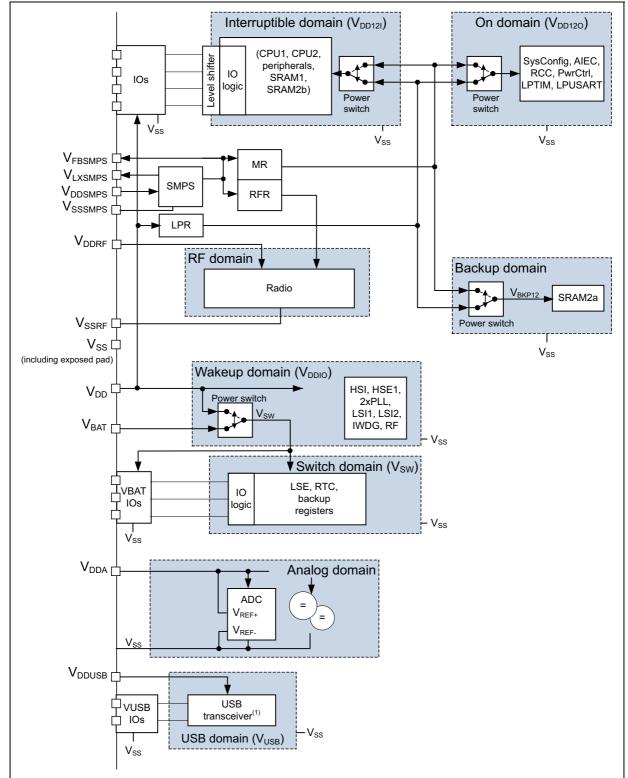


Figure 8. STM32WB35xx - Power supply overview

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The USB transceiver is powered by V_{DDUSB}, and the GPIOs associated with USB are powered by V_{DDUSB} when USB alternate function (PA11 and PA12) is selected. When USB alternate function is not selected the GPIOs associated with USB are powered as standard GPIOs.

3.7.3 Linear voltage regulator

Three embedded linear voltage regulators supply most of the digital and RF circuitries, the main regulator (MR), the low-power regulator (LPR) and the RF regulator (RFR).

- The MR is used in the Run and Sleep modes and in the Stop 0 mode.
- The LPR is used in Low-Power Run, Low-Power Sleep, Stop 1 and Stop 2 modes. It is also used to supply the SRAM2a in Standby with retention.
- The RFR is used to supply the RF analog part, its activity is automatically managed by the RF subsystem.

All the regulators are in power-down in Standby and Shutdown modes: the regulator output is in high impedance, and the kernel circuitry is powered down, inducing zero consumption.

The ultralow-power STM32WB55xx and STM32WB35xx support dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the main regulator that supplies the logic (VCORE) can be adjusted according to the system's maximum operating frequency.

There are two voltage and frequency ranges:

- Range 1, with the CPU running up to 64 MHz
- Range 2, with a maximum CPU frequency of 16 MHz (note that HSE can be active in this mode). All peripheral clocks are also limited to 16 MHz.

VCORE can also be supplied by the low-power regulator, the main regulator being switched off. The system is then in Low-power run mode. In this case the CPU is running at up to 2 MHz, and peripherals with independent clock can be clocked by HSI16 (in this mode the RF subsystem is not available).

3.7.4 Power supply supervisor

An integrated ultra-low-power brown-out reset (BOR) is active in all modes except Shutdown ensuring proper operation after power-on and during power down. The devices remain in reset mode when the monitored supply voltage V_{DD} is below a specified threshold, without the need for an external reset circuit.

The lowest BOR level is 1.71 V at power on, and other higher thresholds can be selected through option bytes. The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it with the V_{PVD} threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

In addition, the devices embed a peripheral voltage monitor (PVM) that compares the independent supply voltage V_{DDA} with a fixed threshold to ensure that the peripheral is in its functional supply range.

Any BOR level can also be used to automatically switch the SMPS step-down converter in bypass mode when the V_{DD} voltage drops below a given voltage level. The mode of operation is selectable by register bit, the BOR level is selectable by option byte.

3.7.5 Low-power modes

These ultra-low-power devices support several low-power modes to achieve the best compromise between low-power consumption, short startup time, available peripherals and available wake-up sources.



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By default, the microcontroller is in Run mode, Range 1, after a system or a power on reset. It is up to the user to select one of the low-power modes described below:

Sleep

In Sleep mode, only the CPU1 is stopped. All peripherals, including the RF subsystem, continue to operate and can wake up the CPU when an interrupt/event occurs.

Low-power run

This mode is achieved with VCORE supplied by the low-power regulator to minimize the regulator operating current. The code can be executed from SRAM or from the flash memory, and the CPU1 frequency is limited to 2 MHz. The peripherals with independent clock can be clocked by HSI16. The RF subsystem is not available in this mode and must be OFF.

Low-power sleep

This mode is entered from the low-power run mode. Only the CPU1 clock is stopped. When wake-up is triggered by an event or an interrupt, the system reverts to the low-power run mode. The RF subsystem is not available in this mode and must be OFF.

Stop 0, Stop 1 and Stop 2

Stop modes achieve the lowest power consumption while retaining the content of all the SRAM and registers. The LSE (or LSI) is still running.

The RTC can remain active (Stop mode with RTC, Stop mode without RTC).

Some peripherals with wake-up capability can enable the HSI16 RC during Stop modes to detect their wake-up condition.

Three modes are available: Stop 0, Stop 1 and Stop 2. In Stop 2 mode, most of the VCORE domain is put in a lower leakage mode.

Stop 1 offers the largest number of active peripherals and wake-up sources, a smaller wake-up time but a higher consumption than Stop 2. In Stop 0 mode the main regulator remains ON, allowing a very fast wake-up time but with higher consumption.

In these modes the RF subsystem can wait for incoming events in all Stop modes.

The system clock when exiting from Stop 0, Stop1 or Stop2 modes can be either MSI up to 48 MHz or HSI16 if the RF subsystem is disabled. If the RF subsystem or the SMPS is used the exits must be set to HSI16 only. If used, the SMPS is restarted automatically.

Standby

The Standby mode is used to achieve the lowest power consumption with BOR. The internal regulator is switched off so that the VCORE domain is powered off.

The RTC can remain active (Standby mode with RTC).

The brown-out reset (BOR) always remains active in Standby mode.

The state of each I/O during standby mode can be selected by software: I/O with internal pull-up, internal pull-down or floating.

After entering Standby mode, SRAM1, SRAM2b and register contents are lost except for registers in the Backup domain and Standby circuitry. Optionally, SRAM2a can be retained in Standby mode, supplied by the low-power regulator (Standby with 32 KB SRAM2a retention mode).

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wake-up, timestamp, tamper) or a failure is detected on LSE (CSS on LSE, or from the RF system wake-up).

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The system clock after wake-up is 16 MHz, derived from the HSI16. If used, the SMPS is restarted automatically. In this mode the RF can be used.

Shutdown

This mode achieves the lowest power consumption. The internal regulator is switched off so that the VCORE domain is powered off.

The RTC can remain active (Shutdown mode with RTC, Shutdown mode without RTC).

The BOR is not available in Shutdown mode. No power voltage monitoring is possible in this mode, therefore the switch to Backup domain is not supported.

SRAM1, SRAM2a, SRAM2b and register contents are lost except for registers in the Backup domain.

The device exits Shutdown mode when an external reset (NRST pin), a WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wake-up, timestamp, tamper).

The system clock after wake-up is 4 MHz, derived from the MSI.

In this mode the RF is no longer operational.

When the RF subsystem is active, it changes the power state according to its needs (Run, Stop, Standby). This operation is transparent for the CPU1 host application and managed by a dedicated HW state machine. At any given time the effective power state reached is the higher one needed by both the CPU1 and RF sub-system.

Table 7 summarizes the peripheral features over all available modes. Wake-up capability is detailed in gray cells.

Tuble 1.1 cutures ever all modes														
						Stop0	/Stop1	Sto	p 2	Stan	dby	Shut	down	
Peripheral ⁽²⁾	Run Range 1	Run Range 2	Sleep	Low-power run	Low-power sleep	-	Wakeup capability		Wakeup capability	-	Wakeup capability	-	Wakeup capability	VBAT
CPU1	Y		-	Υ	-	-		-	-	-	-	-	-	-
CPU2	Y		-	Υ	-	-	-	-	-	-	-	-	-	-
Radio system (Bluetooth Low Energy, 802.15.4)	Υ	Y ⁽³⁾	Υ	-	-	Y	Υ	Υ	Y	Y ⁽⁴⁾	Y ⁽⁴⁾			
Flash memory	Y	(5)	Υ	O ⁽⁶⁾	O ⁽⁶⁾	R	-	R	-	R	-	R	-	R
SRAM1	,	Y	Y ⁽⁷⁾	Υ	Y ⁽⁷⁾	R	-	R	-	-	-	-	-	-
SRAM2a	,	Y	Y ⁽⁷⁾	Υ	Y ⁽⁷⁾	R	-	R	-	R ⁽⁸⁾	-	-	-	-
SRAM2b	,	Y	Y ⁽⁷⁾	Υ	Y ⁽⁷⁾	R	-	R	-	-	-	-	-	-
Quad-SPI	()	0	0	0	-	-	-	-	-	-	-	-	-
Backup registers	,	Υ		Υ	Υ	R	-	R	-	R	-	R	-	R
Brown-out reset (BOR)	Υ		Υ	Υ	Υ	Υ	Υ	Υ	Υ	Υ	Υ	-	1	-
Programmable voltage detector (PVD)	()	0	0	0	0	0	0	0	-	-	-	-	-

Table 7. Features over all modes⁽¹⁾

Table 7. Features over all modes⁽¹⁾ (continued)

						Stop0			p 2	Stan	dby	Shut	down	
Peripheral ⁽²⁾	Run Range 1	Run Range 2	deelS	Low-power run	Low-power sleep	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	VBAT
Peripheral voltage monitor PVMx (x=1, 3)	()	0	0	0	0	0	0	0	-	-	-	1	-
SMPS	()	0	0	0	O ⁽⁹⁾	-	-	-	-	-	-	-	-
DMAx (x = 1, 2)	()	0	0	0	-	-	-	-	-	-	-	-	-
High speed internal (HSI16)	()	0	0	0	O ⁽¹⁰⁾	-	O ⁽¹⁰⁾	-	-	-	-	-	-
Oscillator HSI48	()	0	-	-	-	-	-	-	-	-	-	-	-
High speed external (HSE) ⁽¹¹⁾	0		0	0	0	-	-	-	-	-	-	-	-	-
Low speed internal (LSI1 or LSI2)	0		0	0	0	0	-	0	-	0	-	-	,	-
Low speed external (LSE)	0		0	0	0	0	-	0	-	0	-	0	-	0
Multi-speed internal (MSI) ⁽¹²⁾	48	24	0	48	0	-	-	-		-	-	-	,	-
PLLx VCO maximum frequency	344	128	0	-	-	-	-	-	1	-	-	-	1	-
Clock security system (CSS)	()	0	0	0	0	O ⁽¹³⁾	0	O ⁽¹³⁾	-	-	-	-	-
Clock security system on LSE	()	0	0	0	0	0	0	0	0	0	-	-	-
RTC / Auto wakeup	()	0	0	0	0	0	0	0	0	0	0	0	0
Number of RTC tamper pins	3	3	3	3	3	3	0	3	0	3	0	3	0	3
LCD	()	0	0	0	0	0	0	0	-	-	-	-	-
USB FS	0	-	0	-	ı	-	0	-	-	ı	-	-	-	-
USART1	()	0	0	0	O ⁽¹⁴⁾	O ⁽¹⁴⁾	-	-	-	-	-	-	-
Low-power UART (LPUART1)	0		0	0	0	O ⁽¹⁴⁾	O ⁽¹⁴⁾	O ⁽¹⁴⁾	O ⁽¹⁴⁾	-	-	-	-	-
I2C1	0		0	0	0	O ⁽¹⁵⁾	O ⁽¹⁵⁾	-	-	-	-	-	-	-
I2C3	0		0	0	0	O ⁽¹⁵⁾	O ⁽¹⁵⁾	O ⁽¹⁵⁾	O ⁽¹⁵⁾	-	-	-	-	-
SPIx (x=1, 2)	()	0	0	0	-	-	-	-	-	-	-	-	-
SAI1	()	0	0	0	-	-	-	-	-	-	-	-	-
ADC1	()	0	0	0	-	-	-	-	-	-	-	-	-

Table 7. Features over all modes⁽¹⁾ (continued)

					Stop0	(Ston4	Sto		Stor	ndby	Chut	down		
				u	de	Stopu		510		Star		Snut		
Peripheral ⁽²⁾	Run Range 1	Run Range 2	Sleep	Low-power run	Low-power sleep	•	Wakeup capability	'	Wakeup capability	-	Wakeup capability	-	Wakeup capability	VBAT
VREFBUF	()	0	0	0	0	1	-	-	-	-	-	1	-
COMPx (x=1, 2)	()	0	0	0	0	0	0	0	-	-	-	-	-
Temperature sensor	()	0	0	0	-		-	-	-	-	-		-
Timers TIMx (x=1, 2, 16, 17)	()	0	0	0	-	-	-	-	-	-	-	1	-
Low-power Timer 1 (LPTIM1)	0		0	0	0	0	0	0	0	-	-	-	,	-
Low-power Timer 2 (LPTIM2)	0		0	0	0	0	0	-	-	-	-	-	1	-
Independent watchdog (IWDG)	()	0	0	0	0	0	0	0	0	0	-	,	-
Window watchdog (WWDG)	()	0	0	0	-	-	-	-	-	-	-	1	-
SysTick timer	()	0	0	0	-		-	-	-	-	-		-
Touch sensing controller (TSC)	()	0	0	0	-	1	-	-	-	-	-	,	-
True random number generator (RNG)	0	-	0	-	-	-	-	-	-	-	-	-	1	-
AES2 hardware accelerator	()	0	0	0	-	-	-	-	-	-	-	-	-
CRC calculation unit	()	0	0	0	-	-	-	-	-	-	-	-	-
IPCC	()	-	0	-	-	-	-	-	-	-	-	-	-
HSEM	()	-	0	ı	ı	-	ı	-	-	-	-	-	-
PKA	()	0	0	0	-	-	-	-	-	-	-	-	-
GPIOs	C)	0	0	0	0	0	0	0	(16)	5 pins	(17)	5 pins	-

Legend: Y = Yes (Enabled), O = Optional (Disabled by default, can be enabled by software), R = Data retained,

 Not available.

- 3. Bluetooth Low Energy not possible in this mode.
- 4. Standby with SRAM2a retention mode only.
- 5. Flash memory programming only possible in Range 1 voltage, not in Range 2 and not in Low Power mode.
- 6. The flash memory can be configured in Power-down mode. By default, it is not in Power-down mode.
- 7. The SRAM clock can be gated on or off.
- 8. SRAM2a content is preserved when the bit RRS is set in PWR_CR3 register.



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Available peripherals depend upon package, STM32WB35xx features one SPI, no LCD, no TSC and two wakeup pins. See Table 2 for more details.

- 9. Stop 0 only. SMPS is automatically switched to Bypass or Open mode during Low power operation.
- 10. Some peripherals with wakeup from Stop capability can request HSI16 to be enabled. In this case, HSI16 is woken up by the peripheral, and only feeds the peripheral which requested it. HSI16 is automatically put off when the peripheral does not need it anymore.
- 11. The HSE can be used by the RF subsystem according with the need to perform RF operation (Tx or Rx).
- 12. MSI maximum frequency.
- 13. In case RF will be used and HSE will fail.
- 14. UART and LPUART reception is functional in Stop mode, and generates a wakeup interrupt on Start, address match or received frame event.
- 15. I2C address detection is functional in Stop mode, and generates a wakeup interrupt in case of address match.
- 16. I/Os can be configured with internal pull-up, pull-down or floating in Standby mode.
- 17. I/Os can be configured with internal pull-up, pull-down or floating in Shutdown mode but the configuration is lost when exiting the Shutdown mode.



Table 8. STM32WB55xx and STM32WB35xx modes overview

Mode	Regulator	CPU1	Flash	SRAM	Clocks	DMA and peripherals ⁽¹⁾	Wakeup source	Consumption ⁽²⁾	Wakeup time
Run	Range 1	Yes	ON ⁽³⁾⁽⁴⁾	ON	Any	All	N/A	107 μA/MHz	N/A
ixuii	Range 2	163	ON. A.	Öİ	Ally	All except RNG and USB-FS	19/74	100 μA/MHz	IV/A
LPRun	LPR	Yes	ON ⁽³⁾	ON	Any except PLL	All except RF, RNG and USB-FS	N/A	103 μA/MHz	15.33 µs
Sleep	Range 1	No	ON ⁽³⁾	ON ⁽⁵⁾	Any	All	Any interrupt	41 µA/MHz	9 cycles
Sieep	Range 2	NO	ON	ON	Ally	All except RNG and USB-FS	or event	46 μA/MHz	9 cycles
LPSleep	LPR	No	ON ⁽³⁾	ON ⁽⁵⁾	Any except PLL	All except RF, RNG and USB-FS	Any interrupt or event	45 μA/MHz	9 cycles
Stop 0	Range 1			RTC, LCD, LSE, LSE, LSI, LSART		RF, BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1, 2) USART1 ⁽⁸⁾	Reset pin, all I/Os, RF, BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1, 2)		
	Range 2	Range 2	OFF	ON	HSE ⁽⁶⁾ , HSI16 ⁽⁷⁾	LPUART1 ⁽⁸⁾ I2Cx (x=1, 3) ⁽⁹⁾ LPTIMx (x=1, 2), SMPS All other peripherals are frozen.	USART1 LPUART1 I2Cx (x=1, 3) LPTIMx (x=1, 2) USB	100 μΑ	1.7 µs
Stop 1	LPR	No	OFF	ON	LSE, LSI, HSE ⁽⁶⁾ , HSI16 ⁽⁷⁾	RF, BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1, 2) USART1 ⁽⁸⁾ LPUART1 ⁽⁸⁾ I2Cx (x=1, 3) ⁽⁹⁾ LPTIMx (x=1, 2) All other peripherals are frozen.	Reset pin, all I/Os RF, BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1, 2) USART1 LPUART1 I2Cx (x=1, 3) LPTIMx (x=1, 2) USB	9.2 μA w/o RTC 9.6 μA w RTC	4.7 μs

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Functional overview

Table 8. STM32WB55xx and STM32WB35xx modes overview (continued)

Mode	Regulator	CPU1	Flash	SRAM	Clocks	DMA and peripherals ⁽¹⁾	Wakeup source	Consumption ⁽²⁾	Wakeup time	
Stop 2	LPR	No	OFF	ON	LSE, LSI	RF, BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1, 2) LPUART1 ⁽⁸⁾ I2C3 ⁽⁹⁾ LPTIM1 All other peripherals are frozen.	Reset pin, all I/Os RF, BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1, 2) LPUART1 I2C3 LPTIM1	1.85 μA w/o RTC 2.1 μA w RTC	5.71 μs	
O	LPR		0	SRAM2a ON ⁽¹⁰⁾	LSE,	RF, BOR, RTC, IWDG All other peripherals are	RF, reset pin	0.32 μA w/o RTC 0.60 μA w RTC	-,	
Standby	OFF	No	OFF	OFF	LSI	powered off. I/O configuration can be floating, pull-up or pull-down	5 I/Os (WKUPx) ⁽¹¹⁾ BOR, RTC, IWDG	0.11 μA w/o RTC 0.390 μA w RTC	51 µs	
Shutdown	OFF	No	OFF	OFF	LSE	RTC All other peripherals are powered off. I/O configuration can be floating, pull-up or pull-down ⁽¹²⁾	5 I/Os (WKUPx) ⁽¹¹⁾ , RTC	0.028 μA w/o RTC 0.315 μA w/ RTC	-	

- 1. Available peripherals depend upon package, STM32WB35xx features one SPI, no LCD, no TSC and two wakeup pins. See Table 2 for more details.
- 2. Typical current at V_{DD} = 1.8 V, 25 °C. for STOPx, SHUTDOWN and Standby, else V_{DD} = 3.3 V, 25 °C.
- 3. The flash memory controller can be placed in power-down mode if the RF subsystem is not in use and all the program is run from the SRAM.
- 4. Flash memory programming is only possible in Range 2 voltage.
- 5. The SRAM1 and SRAM2 clocks can be gated off independently.
- 6. HSE (32 MHz) automatically used when RF activity is needed by the RF subsystem.
- 7. HSI16 (16 MHz) automatically used by some peripherals.
- 8. U(S)ART and LPUART reception is functional in Stop mode, and generates a wakeup interrupt on Start, Address match or Received frame event.
- 9. I2C address detection is functional in Stop mode, and generates a wakeup interrupt in case of address match.
- 10. SRAM1 and SRAM2b are OFF.
- 11. I/Os with wakeup from Standby/Shutdown capability: PA0, PC13, PC12, PA2, PC5.
- 12. I/Os can be configured with internal pull-up, pull-down or floating but the configuration is lost immediately when exiting the Shutdown mode.



3.7.6 Reset mode

To improve the consumption under reset, the I/Os state under and after reset is "analog state" (the I/O Schmitt trigger is disabled). In addition, the internal reset pull-up is deactivated when the reset source is internal.

3.8 VBAT operation

The VBAT pin allows to power the device VBAT domain (RTC, LSE and Backup registers) from an external battery, an external supercapacitor, or from V_{DD} when no external battery nor an external supercapacitor are present. Three anti-tamper detection pins are available in VBAT mode.

VBAT operation is automatically activated when V_{DD} is not present.

An internal VBAT battery charging circuit is embedded and can be activated when V_{DD} is present.

Note:

When the microcontroller is supplied only from VBAT, external interrupts and RTC alarm/events do not exit it from VBAT operation.

3.9 Interconnect matrix

Several peripherals have direct connections between them. This allows autonomous communication between peripherals, saving CPU1 resources and, consequently, reducing power supply consumption. In addition, these hardware connections result in fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run and Sleep, Stop 0, Stop 1 and Stop 2 modes.

Table 9. STM32WB55xx and STM32WB35xx CPU1 peripherals interconnect matrix

Source	Destination	Action	Run	Sleep	Low-power run	Low-power	Stop 0 / Stop 1	Stop 2
	TIMx	Timers synchronization or chaining	Υ	Υ	Υ	Υ	-	-
TIMx	ADC1	Conversion triggers	Υ	Υ	Υ	Υ	-	-
THVIX	DMA	DMA Memory to memory transfer trigger				Υ	-	-
	COMPx	Comparator output blanking		Υ	Υ	Υ	-	-
COMPx	TIM1 TIM2	Timer input channel, trigger, break from analog signals comparison	Υ	Υ	Y	Y	-	-
OGIVII A	LPTIMERx	Rx Low-power timer triggered by analog signals comparison		Υ	Υ	Υ	Υ	Y ⁽¹⁾
ADC1	TIM1	Timer triggered by analog watchdog	Υ	Υ	Υ	Υ	-	-

Table 9. STM32WB55xx and STM32WB35xx CPU1 peripherals interconnect matrix (continued)

Source	Destination	Action	Run	Sleep	Low-power run	Low-power	Stop 0 / Stop 1	Stop 2
	TIM16	Timer input channel from RTC events	Υ	Υ	Υ	Υ	-	-
RTC	LPTIMERx	Low-power timer triggered by RTC alarms or tampers	Υ	Υ	Υ	Υ	Υ	Y ⁽¹⁾
All clock sources (internal and external)	TIM2 TIM16, 17	Clock source used as input channel for RC measurement and trimming	Y	Y	Υ	Υ	-	-
USB	TIM2 Timer triggered by USB SOF				-	-	-	-
CSS CPU (hard fault) SRAM (parity error) Flash memory (ECC error) COMPx PVD	TIM1 TIM16,17	Timer break	Y	Y	Y	Y	-	-
	TIMx	External trigger	Υ	Υ	Υ	Υ	-	-
GPIO	LPTIMERx	Υ	Υ	Υ	Υ	Υ	Y ⁽¹⁾	
	ADC1	Conversion external trigger	Υ	Υ	Υ	Υ	-	-

^{1.} LPTIM1 only.

3.10 Clocks and startup

The STM32WB55xx and STM32WB35xx devices integrate several clock sources:

- LSE: 32.768 kHz external oscillator, for accurate RTC and calibration with other embedded RC oscillators
- LSI1: 32 kHz on-chip low-consumption RC oscillator
- LSI2: almost 32 kHz, on-chip high-stability RC oscillator, can be used by the RF subsystem instead of LSE
- HSE: high quality 32 MHz external oscillator with trimming, needed by the RF subsystem
- HSI16: 16 MHz high accuracy on-chip RC oscillator
- MSI: 100 kHz to 48 MHz multiple speed on-chip low power oscillator, can be trimmed using the LSE signal
- HSI48: 48 MHz on-chip RC oscillator, for USB crystal-less purpose

The clock controller (see *Figure 9*) distributes the clocks coming from the different oscillators to the core and the peripherals including the RF subsystem. It also manages clock gating for low power modes and ensures clock robustness. It features:

- Clock prescaler: to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching:** clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management:** to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- System clock source: four different clock sources can be used to drive the master clock SYSCLK:
 - 16 MHz high-speed internal RC oscillator (HSI16), trimmable by software, that can supply a PLL
 - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 12 frequencies from 100 kHz to 48 MHz. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be automatically trimmed by hardware to reach better than ±0.25% accuracy. The MSI can supply a PLL.
 - System PLL that can be fed by HSE, HSI16 or MSI, with a maximum frequency of 64 MHz.
- Auxiliary clock source: two ultralow-power clock sources that can be used to drive the LCD controller and the real-time clock:
 - 32.768 kHz low-speed external crystal (LSE), supporting four drive capability modes. The LSE can also be configured in bypass mode for an external clock.
 - 32 kHz low-speed internal RC (LSI), also used to drive the independent watchdog.
 The LSI clock accuracy is ±5%. The LSI source can be either the LSI1 or the LSI2 on-chip oscillator.
- Peripheral clock sources: Several peripherals (RNG, SAI, USARTs, I2Cs, LPTimers, ADC) have their own independent clock whatever the system clock. Two PLLs, each having three independent outputs for the highest flexibility, can generate independent clocks for the ADC, the RNG and the SAI.
- Startup clock: after reset, the microcontroller restarts by default with an internal 4 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application

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- program as soon as the code execution starts.
- Clock security system (CSS): this feature can be enabled by software. If an HSE
 clock failure occurs, the master clock is automatically switched to HSI16 and a software
 interrupt is generated if enabled. LSE failure can also be detected and an interrupt
 generated.
- Clock-out capability:
 - MCO (microcontroller clock output): it outputs one of the internal clocks for external use by the application. Low frequency clocks (LSIx, LSE) are available down to Stop 1 low power state.
 - LSCO (low-speed clock output): it outputs LSI or LSE in all low-power modes down to Standby.

Several prescalers allow the user to configure the AHB frequencies, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 64 MHz.

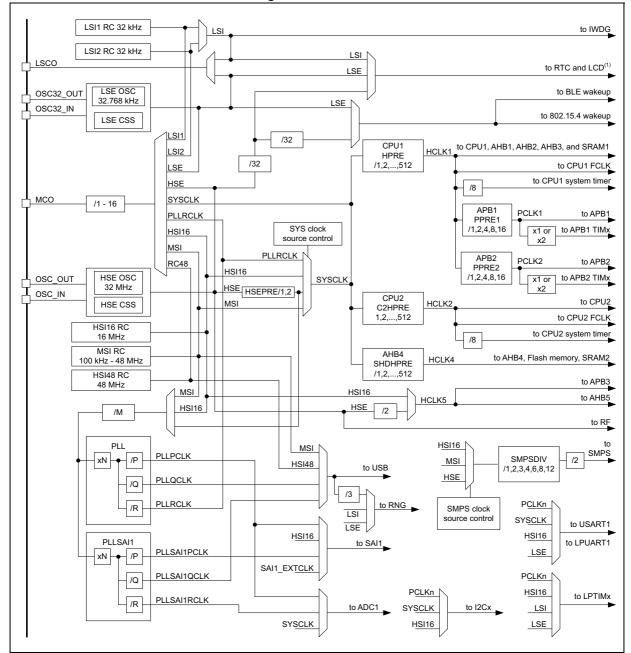


Figure 9. Clock tree

1. The LCD is not available on STM32WB35xx devices.

3.11 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. Fast I/O toggling can be achieved thanks to their mapping on the AHB2 bus.

The I/Os alternate function configuration can be locked, if needed, following a specific sequence in order to avoid spurious writing to the I/Os registers.

3.12 Direct memory access controller (DMA)

The device embeds two DMAs. Refer to *Table 10* for the features implementation.

Direct memory access (DMA) is used to provide high-speed data transfer between peripherals and memory as well as between memories. Data can be quickly moved by DMA without any CPU action. This keeps CPU resources free for other operations.

The two DMA controllers have fourteen channels in total, a full cross matrix allows any peripheral to be mapped on any of the available DMA channels. Each DMA has an arbiter for handling the priority between DMA requests.

The DMA supports:

- fourteen independently configurable channels (requests)
- A full cross matrix between peripherals and all the DMA channels exist. There is also a HW trigger possibility through the DMAMUX.
- Priorities between requests from DMA channels are software programmable (four levels consisting in very high, high, medium and low) or hardware in case of equality (request 1 has priority over request 2, etc.).
- Independent source and destination transfer size (byte, half word, word), emulating packing and unpacking. Source/destination addresses must be aligned on the data size.
- Support for circular buffer management.
- Three event flags (DMA half transfer, DMA transfer complete and DMA transfer error) logically OR-ed together in a single interrupt request for each channel.
- Memory-to-memory transfer.
- Peripheral-to-memory and memory-to-peripheral, and peripheral-to-peripheral transfers.
- Access to flash memory, SRAM, APB and AHB peripherals as source and destination.
- Programmable number of data to be transferred: up to 65536.

Table 10. DMA implementation

DMA features	DMA1	DMA2
Number of regular channels	7	7

A DMAMUX block makes it possible to route any peripheral source to any DMA channel.

3.13 Interrupts and events

3.13.1 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 63 maskable interrupt channels plus the 16 interrupt lines of the Cortex[®]-M4 with FPU.



The NVIC benefits are the following:

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving higher priority interrupts
- Support for tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

The NVIC hardware block provides flexible interrupt management features with minimal interrupt latency.

3.13.2 Extended interrupts and events controller (EXTI)

The EXTI manages wake-up through configurable and direct event inputs. It provides wake-up requests to the Power control, and generates interrupt requests to the CPUx NVIC and events to the CPUx event input.

Configurable events/interrupts come from peripherals able to generate a pulse, and make it possible to select the Event/Interrupt trigger edge and/or a SW trigger.

Direct events/interrupts are coming from peripherals having their own clearing mechanism.

3.14 Analog to digital converter (ADC)

The device embeds a successive approximation analog-to-digital converter with the following features:

- 12-bit native resolution, with built-in calibration
- Up to 16-bit resolution with 256 oversampling ratio
- 4.26 Msps maximum conversion rate with full resolution
 - Down to 39 ns sampling time
 - Increased conversion rate for lower resolution (up to 7.11 Msps for 6-bit resolution)
- Up to sixteen external channels and three internal channels: internal reference voltages, temperature sensor
- Single-ended and differential mode inputs
- Low-power design
 - Capable of low-current operation at low conversion rate (consumption decreases linearly with speed)
 - Dual clock domain architecture: ADC speed independent from CPU frequency
- Highly versatile digital interface
 - Single-shot or continuous/discontinuous sequencer-based scan mode: two groups of analog signals conversions can be programmed to differentiate background and high-priority real-time conversions
 - The ADC supports multiple trigger inputs for synchronization with on-chip timers and external signals
 - Results stored into three data register or in SRAM with DMA controller support

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- Data pre-processing: left/right alignment and per channel offset compensation
- Built-in oversampling unit for enhanced SNR
- Channel-wise programmable sampling time
- Three analog watchdog for automatic voltage monitoring, generating interrupts and trigger for selected timers
- Hardware assistant to prepare the context of the injected channels to allow fast context switching

3.14.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{TS} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC1_IN17 input channel, which is used to convert the sensor output voltage into a digital value.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored in the system memory area, accessible in read-only mode.

Calibration value nameDescriptionMemory addressTS_CAL1TS_ADC raw data acquired at a temperature of 30 °C (\pm 5 °C), $V_{DDA} = V_{REF+} = 3.0 \text{ V} (\pm 10 \text{ mV})$ 0x1FFF 75A8 - 0x1FFF 75A9TS_CAL2TS_ADC raw data acquired at a temperature of 130 °C (\pm 5 °C), $V_{DDA} = V_{REF+} = 3.0 \text{ V} (\pm 10 \text{ mV})$ 0x1FFF 75CA - 0x1FFF 75CB

Table 11. Temperature sensor calibration values

3.14.2 Internal voltage reference (V_{REFINT})

The internal voltage reference (VREFINT) provides a stable (bandgap) voltage output for the ADC and the comparators. VREFINT is internally connected to the ADC1_IN0 input channel. The precise voltage of VREFINT is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 12. Internal voltage reference calibration values

Calibration value name	Description	Memory address
VREFINT	Raw data acquired at a temperature of 30 °C (± 5 °C), V _{DDA} = V _{REF+} = 3.6 V (± 10 mV)	0x1FFF 75AA - 0x1FFF 75AB



3.15 Voltage reference buffer (VREFBUF)

The STM32WB55xx devices embed a voltage reference buffer that can be used as voltage reference for the ADC and also as voltage reference for external components through the VREF+ pin. The internal voltage reference buffer supports two voltages:

- 2.048 V
- 2.5 V

An external voltage reference can be provided through the VREF+ pin when the internal voltage reference buffer is off. The VREF+ pin is double-bonded with VDDA on UFQFPN48 package, hence the internal voltage reference buffer is not available on a dedicated pin, but user can still use the $V_{\rm DDA}$ value.

3.16 Comparators (COMP)

The STM32WB55xx and STM32WB35xx devices embed two rail-to-rail comparators with programmable reference voltage (internal or external), hysteresis and speed (low-speed for low-power) and with selectable output polarity.

The reference voltage can be one of the following:

- External I/O
- Internal reference voltage or submultiple (1/4, 1/2, 3/4).

All comparators can wake up from Stop mode, generate interrupts and breaks for the timers and can be also combined into a window comparator.

3.17 Touch sensing controller (TSC)

The touch sensing controller provides a simple solution for adding capacitive sensing functionality to any application. Capacitive sensing technology is able to detect finger presence near an electrode which is protected from direct touch by a dielectric such as glass or plastic. The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library (free to use) and enables reliable touch sensing functionality in the end application.

The main features of the touch sensing controller are the following:

- Proven and robust surface charge transfer acquisition principle
- Supports up to 18 capacitive sensing channels
- Up to six capacitive sensing channels can be acquired in parallel offering a very good response time
- Spread spectrum feature to improve system robustness in noisy environments
- Full hardware management of the charge transfer acquisition sequence
- Programmable charge transfer frequency
- Programmable sampling capacitor I/O pin
- Programmable channel I/O pin
- Programmable max count value to avoid long acquisition when a channel is faulty
- · Dedicated end of acquisition and max count error flags with interrupt capability
- One sampling capacitor for up to three capacitive sensing channels to reduce the system components
- Compatible with proximity, touchkey, linear and rotary touch sensor implementation
- Designed to operate with STMTouch touch sensing firmware library

Note:

The number of capacitive sensing channels is dependent upon the package (not available on QFPN48) and subject to I/O availability.

4

3.18 Liquid crystal display controller (LCD)

The STM32WB55xx devices embed an LCD controller with the following characteristics:

- Highly flexible frame rate control.
- Supports Static, 1/2, 1/3, 1/4 and 1/8 duty.
- Supports Static, 1/2, 1/3 and 1/4 bias.
- Double buffered memory allows data in LCD_RAM registers to be updated at any time by the application firmware without affecting the integrity of the data displayed.
 - LCD data RAM of up to 16 x 32-bit registers which contain pixel information (active/inactive)
- Software selectable LCD output voltage (contrast) from VLCD_{min} to VLCD_{max}.
- No need for external analog components:
 - A step-up converter is embedded to generate an internal VLCD voltage higher than V_{DD} (up to 3.6 V if V_{DD} > 2.0 V)
 - Software selection between external and internal VLCD voltage source. In case of an external source, the internal boost circuit is disabled to reduce power consumption
 - A resistive network is embedded to generate intermediate VLCD voltages
 - The structure of the resistive network is configurable by software to adapt the power consumption to match the capacitive charge required by the LCD panel
 - Integrated voltage output buffers for higher LCD driving capability.
- The contrast can be adjusted using two different methods:
 - When using the internal step-up converter, the software can adjust VLCD between VLCD_{min} and VLCD_{max}
 - Programmable dead time (up to eight phase periods) between frames.
- Full support of low-power modes: the LCD controller can be displayed in Sleep, Low-power run, Low-power sleep and Stop modes, or can be fully disabled to reduce power consumption.
- Built in phase inversion for reduced power consumption and EMI (electromagnetic interference).
- Start of frame interrupt to synchronize the software when updating the LCD data RAM.
- Blink capability:
 - 1, 2, 3, 4, 8 or all pixels can be programmed to blink at a configurable frequency
 - Software adjustable blink frequency to achieve around 0.5 Hz, 1 Hz, 2 Hz or 4 Hz.

Used LCD segment and common pins should be configured as GPIO alternate functions and unused segment and common pins can be used for general purpose I/O or for another peripheral alternate function.

Note:

When the LCD relies on the internal step-up converter, the VLCD pin should be connected to V_{SS} with a capacitor. Its typical value is 1 μ F.

3.19 True random number generator (RNG)

The devices embed a true RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

4

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3.20 Timers and watchdogs

The STM32WB55xx and STM32WB35xx include one advanced 16-bit timer, one general-purpose 32-bit timer, two 16-bit basic timers, two low-power timers, two watchdog timers and a SysTick timer. *Table 13* compares the features of the advanced control, general purpose and basic timers.

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary outputs
Advanced control	TIM1	16-bits	Up, down, Up/down			4	3
General purpose	TIM2	32-bits	Up, down, Up/down			4	No
General purpose	TIM16	16-bits	Up	Any integer between 1 and 65536	Yes	2	1
General purpose	TIM17	16-bits	Up			2	1
Low power	LPTIM1 LPTIM2	16-bits	Up			1	1

Table 13. Timer features

3.20.1 Advanced-control timer (TIM1)

The advanced-control timer can be seen as a three-phase PWM multiplexed on six channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers. The four independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0 to 100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIMx timers (described in Section 3.20.2) using the same architecture, so the advanced-control timers can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

3.20.2 General-purpose timers (TIM2, TIM16, TIM17)

There are up to three synchronizable general-purpose timers embedded in the STM32WB55xx and STM32WB35xx (see *Table 13* for differences). Each general-purpose timer can be used to generate PWM outputs, or act as a simple time base.

- TIM2
 - Full-featured general-purpose timer

- Features four independent channels for input capture/output compare, PWM or one-pulse mode output. Can work together, or with the other general-purpose timers via the Timer Link feature for synchronization or event chaining.
- The counter can be frozen in debug mode.
- Independent DMA request generation, support of quadrature encoders.
- TIM16 and TIM17
 - General-purpose timers with mid-range features:
 - 16-bit auto-reload upcounters and 16-bit prescalers.
 - 1 channel and 1 complementary channel.
 - All channels can be used for input capture/output compare, PWM or one-pulse mode output.
 - The timers can work together via the Timer Link feature for synchronization or event chaining. The timers have independent DMA request generation.
 - The counters can be frozen in debug mode.

3.20.3 Low-power timer (LPTIM1 and LPTIM2)

The devices embed two low-power timers, having an independent clock running in Stop mode if they are clocked by LSE, LSIx or by an external clock. They are able to wake-up the system from Stop mode.

LPTIM1 is active in Stop 0, Stop 1 and Stop 2 modes.

LPTIM2 is active in Stop 0 and Stop 1 modes.

The low-power timers support the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- · Continuous/ one shot mode
- Selectable software/hardware input trigger
- Selectable clock source
 - Internal clock sources: LSE, either LSI1 or LSI2, HSI16 or APB clock
 - External clock source over LPTIM input (working even with no internal clock source running, used by pulse counter application)
- Programmable digital glitch filter
- Encoder mode (LPTIM1 only)

3.20.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and an 8-bit prescaler. It is clocked from an independent 32 kHz internal RC (LSI) and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

3.20.5 System window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.20.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- a 24-bit down counter
- autoreload capability
- a maskable system interrupt generation when the counter reaches 0
- a programmable clock source.

3.21 Real-time clock (RTC) and backup registers

The RTC is an independent BCD timer/counter, supporting the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 0.95 ppm resolution, to compensate for quartz crystal inaccuracy.
- Three anti-tamper detection pins with programmable filter.
- Timestamp feature, which can be used to save the calendar content. This function can
 be triggered by an event on the timestamp pin, or by a tamper event, or by a switch to
 VBAT mode.
- 17-bit auto-reload wake-up timer (WUT) for periodic events with programmable resolution and period.

The RTC and the 20 backup registers are supplied through a switch that takes power either from the V_{DD} supply (when present) or from the VBAT pin.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. They are not reset by a system or power reset, or when the device wakes up from Standby or Shutdown mode.

The RTC clock sources can be:

- a 32.768 kHz external crystal (LSE)
- an external resonator or oscillator (LSE)
- one of the internal low power RC oscillators (LSI1 or LSI2, with typical frequency of 32 kHz)
- the high-speed external clock (HSE) divided by 32.

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The RTC is functional in VBAT mode and in all low-power modes when it is clocked by the LSE. When clocked by one of the LSIs, the RTC is not functional in VBAT mode, but is functional in all low-power modes except Shutdown mode.

All RTC events (alarm, wake-up timer, timestamp or tamper) can generate an interrupt and wake-up the device from the low-power modes.

3.22 Inter-integrated circuit interface (I2C)

The devices embed two I2Cs. Refer to *Table 14* for the features implementation.

The I²C bus interface handles communications between the microcontroller and the serial I²C bus. It controls all I²C bus-specific sequencing, protocol, arbitration and timing.

The I2C peripheral supports:

- I²C-bus specification and user manual rev. 5 compatibility:
 - Slave and master modes, multimaster capability
 - Standard-mode (Sm), with a bitrate up to 100 kbit/s
 - Fast-mode (Fm), with a bitrate up to 400 kbit/s
 - Fast-mode Plus (Fm+), with a bitrate up to 1 Mbit/s and 20 mA output drive I/Os
 - 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
 - Programmable setup and hold times
 - Optional clock stretching
- System Management Bus (SMBus) specification rev 2.0 compatibility:
 - Hardware PEC (packet error checking) generation and verification with ACK control
 - Address resolution protocol (ARP) support
 - SMBus alert
- Power System Management Protocol (PMBus[™]) specification rev 1.1 compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent from the PCLK reprogramming. Refer to Figure 9: Clock tree.
- Wake-up from Stop mode on address match
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

Table 14. I2C implementation

I2C features ⁽¹⁾	I2C1	I2C3
Standard-mode (up to 100 kbit/s)	Х	Х
Fast-mode (up to 400 kbit/s)	Х	Х
Fast-mode Plus with 20 mA output drive I/Os (up to 1 Mbit/s)	Х	Х
Programmable analog and digital noise filters	Х	Х
SMBus/PMBus hardware support	Х	Х

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I2C features ⁽¹⁾	I2C1	I2C3
Independent clock	Χ	Х
Wakeup from Stop 0 / Stop 1 mode on address match	Х	Х
Wakeup from Stop 2 mode on address match	-	Х

Table 14. I2C implementation (continued)

3.23 Universal synchronous/asynchronous receiver transmitter (USART)

The devices embed one universal synchronous receiver transmitter.

This interface provides asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and has LIN Master/Slave capability. It provides hardware management of the CTS and RTS signals, and RS485 driver enable.

The USART is able to communicate at speeds of up to 4 Mbit/s, and also provides Smart Card mode (ISO 7816 compliant) and SPI-like communication capability.

The USART supports synchronous operation (SPI mode), and can be used as an SPI master.

The USART has a clock domain independent from the CPU clock, allowing it to wake up the MCU from Stop mode using baudrates up to 200 kbaud. The wake up events from Stop mode are programmable and can be:

- the start bit detection
- · any received data frame
- a specific programmed data frame.

The USART interface can be served by the DMA controller.

3.24 Low-power universal asynchronous receiver transmitter (LPUART)

The device embeds one Low-Power UART, enabling asynchronous serial communication with minimum power consumption. The LPUART supports half duplex single wire communication and modem operations (CTS/RTS), allowing multiprocessor communication.

The LPUART has a clock domain independent from the CPU clock, and can wake-up the system from Stop mode using baudrates up to 220 kbaud. The wake up events from Stop mode are programmable and can be:

- · the start bit detection
- any received data frame
- a specific programmed data frame.

Only a 32.768 kHz clock (LSE) is needed for LPUART communication up to 9600 baud. Therefore, even in Stop mode, the LPUART can wait for an incoming frame while having an



^{1.} X: supported

extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

The LPUART interfaces can be served by the DMA controller.

3.25 Serial peripheral interface (SPI1, SPI2)

Two SPI interfaces enable communication up to 32 Mbit/s in master and up to 24 Mbit/s in slave modes, in half-duplex, full-duplex and simplex modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits. The SPI interfaces support NSS pulse mode, TI mode and Hardware CRC calculation.

The SPI interfaces can be served by the DMA controller.

3.26 Serial audio interfaces (SAI1)

The device embeds a dual channel SAI peripheral that supports full duplex audio operation. The SAI bus interface handles communications between the microcontroller and the serial audio protocol.

The SAI peripheral supports:

- One independent audio sub-block that can be a transmitter or a receiver, with the respective FIFO
- 8-word integrated FIFOs
- Synchronous or asynchronous mode
- Master or slave configuration
- Clock generator to target independent audio frequency sampling when audio sub-block is configured in master mode
- Data size configurable: 8-, 10-, 16-, 20-, 24-, 32-bit
- Peripheral with large configurability and flexibility allowing to target as example the following audio protocol: I2S, LSB or MSB-justified, PCM/DSP, TDM, AC'97 and SPDIF out
- Up to 16 slots available with configurable size and with the possibility to select which
 ones are active in the audio frame
- Number of bits by frame may be configurable
- Frame synchronization active level configurable (offset, bit length, level)
- First active bit position in the slot is configurable
- LSB first or MSB first for data transfer
- Mute mode
- Stereo/Mono audio frame capability
- Communication clock strobing edge configurable (SCK)
- Error flags with associated interrupts if enabled respectively
 - Overrun and underrun detection
 - Anticipated frame synchronization signal detection in slave mode
 - Late frame synchronization signal detection in slave mode
 - Codec not ready for the AC'97 mode in reception

- Interruption sources when enabled:
 - Errors
 - FIFO requests
- DMA interface with two dedicated channels to handle access to the dedicated integrated FIFO of the SAI audio sub-block.

The PDM (Pulse Density Modulation) block allows the user to manage up to three digital microphone pairs (with two different clocks). This block performs Right and Left microphone de-interleaving and time alignment through programmable delay lines in order to properly feed the SAI.

3.27 Quad-SPI memory interface (QUADSPI)

The Quad-SPI is a specialized communication interface targeting single, dual or quad SPI flash memories. It can operate in any of the three following modes:

- Indirect mode: all the operations are performed using the QUADSPI registers
- Status polling mode: the external memory status register is periodically read and an interrupt can be generated in case of flag setting
- Memory-mapped mode: the external flash memory is mapped and is seen by the system as if it were an internal memory. This mode can be used for the Execute In Place (XIP)

The Quad-SPI interface supports:

- Three functional modes: indirect, status-polling, and memory-mapped
- SDR and DDR support
- Fully programmable opcode for both indirect and memory mapped mode
- Fully programmable frame format for both indirect and memory mapped mode
- Each of the five following phases can be configured independently (enable, length, single/dual/quad communication)
 - Instruction phase
 - Address phase
 - Alternate bytes phase
 - Dummy cycles phase
 - Data phase
- Integrated FIFO for reception and transmission
- 8, 16, and 32-bit data accesses are allowed
- DMA channel for indirect mode operations
- Programmable masking for external flash memory flag management
- Timeout management
- Interrupt generation on FIFO threshold, timeout, status match, operation complete, and access error

3.28 Development support

3.28.1 Serial wire JTAG debug port (SWJ-DP)

The embedded Arm[®] SWJ-DP interface is a combined JTAG and serial wire debug port that enables either a serial wire debug, or a JTAG probe to be connected to the target.

Debug is performed using only two pins instead of the five required by the JTAG (JTAG pins can then be reused as GPIOs with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

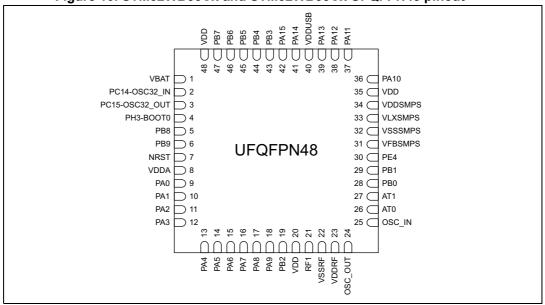
3.28.2 Embedded Trace Macrocell™

The Arm® Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32WB55xx through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. Real-time instruction and data flow activity be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

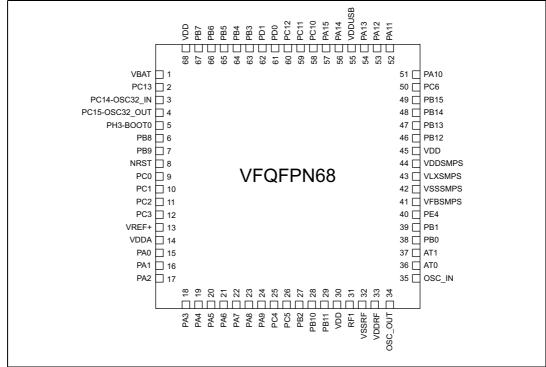
Pinouts and pin description 4

Figure 10. STM32WB55Cx and STM32WB35Cx UFQFPN48 pinout⁽¹⁾⁽²⁾



- The above figure shows the package top view.
- 2. The exposed pad must be connected to ground plane.

Figure 11. STM32WB55Rx VFQFPN68 pinout⁽¹⁾⁽²⁾



- The above figure shows the package top view
- 2. The exposed pad must be connected to ground plane.

5 6 9 10 PA11 PA14 PA15 PA13 PC10 PB3 VDD Α PA12 В vss VDDUSB PA10 vss VDD PC9 PC11 PD5 PD12 PE1 С PE0 VBAT PB13 PD3 PD1 PD0 PC12 PD6 PB4 PD13 PC15-OSC32_OUT PC14-OSC32_IN D VDDSMPS PC6 PD8 PD9 PB5 PB7 Ε VLXSMPS PB14 РН3-ВООТ0 PH0 PC7 PD10 PD11 PE2 PD15 F VSSSMPS VFBSMPS PB15 PB6 PA2 PB9 PC8 G PE4 PE3 PB12 PC4 PC13 PA1 PA0 PC1 PC2 PC3 Н PB1 PB0 AT0 AT1 PC5 PA7 PA6 VREF+ VDDA VSSA OSC_IN OSC_OUT VDDRF VSSRF PB11 PA8 PA3 vss VDD vss Κ VSSRF VSSRF PA4 VSSRF VDD PB10 PA9 PA5 Radio USB **SMPS** VDD VSS MS42407V3

Figure 12. STM32WB55Vx WLCSP100 ballout⁽¹⁾

1. The above figure shows the package top view.

Figure 13. STM32WB55Vx UFBGA129 ballout⁽¹⁾

	1	2	3	4	5	6	7	8	9	10	11	12	13
Α	PE1	PB6	PB5	> <	> <	PD5	PD10	VDD _DCAP4	> <		PA13	VDDUSB	PA12
В	PE2	PE0	PB4	PD12	PD11	PD8	PD2	VSS _DCAP4	PC10	PC12	PD0	VSS	PA11
С	PD13	PD15	PB7	PB3	PD7	PD4	PD1	PC11	PA15	PA14	vss	PA10	PC9
D	> <	VBAT	PD14	PD9	>>	PD6	\times	PD3	\times	PC6	PC8	PC7	>
Е	\supset	PC15- OSC32_OUT	PC14- OSC32_IN	> <	VSS	> <	VSS	> <	VSS	> <	PB14	PB13	\supset
F	PH0	VDD _DCAP1	VSS _DCAP1	PC13	>>	VDD	>>	VDD	\times	PB15	VLXSMPS	VDDSMPS	VDDSMPS
G	РН3-ВООТ0	PH1	PB8	>>	VSS	> <	VDD	>	VSS		VLXSMPS	VSSSMPS	VSSSMPS
Н	PC1	NRST	PC0	PB9	>>	VDD	\times	VDD	\times	PB12	VFBSMPS	PE3	PE4
J	\times	PC2	PC3	\times	VSS	> <	VSS	\times	VSS	><	VSS_DCAP3	VDD_DCAP3	>>
K	\times	VSSA	VDDA	VSS	>>	VSS	>>	VSSRF	\times	VSSRF	AT0	AT1	>
L	VREF+	PA1	PA4	PA9	PC5	PB10	VSSRF	VSSRF	VSSRF	VSSRF	VSSRF	PB1	PB0
М	PA0	PA3	PA6	PA8	PC4	PB11	VSS _DCAP2	VSSRF	RF1	VSSRF	VSSRF	VSSRF	OSC_IN
N	PA2	PA5	PA7	>>	\times	PB2	VDD _DCAP2	VSSRF	\times	><	VSSRF	VDDRF	OSC_OUT
											-		_
		$\overline{}$											
	N	o pin	•	Power	supply		SMP	S	U	SB	_	Radio	

1. The above figure shows the package top view.

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Table 15. Legend/abbreviations used in the pinout table

Na	me	Abbreviation	Definition				
Pin r	name	Unless otherwise specified in reset is the same as the actu	brackets below the pin name, the pin function during and after al pin name				
		S	Supply pin				
Pin	type	I	Input only pin				
		I/O	Input / output pin				
		FT	5 V tolerant I/O				
		TT	3.6 V tolerant I/O				
		RF	RF I/O				
		RST	Bidirectional reset pin with weak pull-up resistor				
I/O str	ructure	Option for TT or FT I/Os					
		_f ⁽¹⁾	I/O, Fm+ capable				
		_l ⁽²⁾	I/O, with LCD function supplied by V _{LCD}				
		_u ⁽³⁾	I/O, with USB function supplied by V _{DDUSB}				
		_a ^{(4) (5)}	I/O, with Analog switch function supplied by V _{DDA}				
No	tes	Unless otherwise specified by	/ a note, all I/Os are set as analog inputs during and after reset.				
Pin	Alternate functions	Functions selected through G	GPIOx_AFR registers				
functions	Additional functions	Functions directly selected/enabled through peripheral registers					

^{1.} The related I/O structures in *Table 16* are: FT_f, FT_fa, FT_fl, FT_fla.

^{2.} The related I/O structures in *Table 16* are: FT_I, FT_fI, FT_lu.

^{3.} The related I/O structures in *Table 16* are: FT_u, FT_lu.

^{4.} The related I/O structures in *Table 16* are: FT_a, FT_la, FT_fa, FT_fla, TT_a, TT_la.

^{5.} Analog switch for the TSC function is supplied by V_{DD} .

Table 16. STM32WB55xx pin and ball definitions

	Pin ı	numb	er			es		·		
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions	
-	-	C8	B2	PE0	I/O	FT_I	-	TIM1_ETR, TSC_G7_IO3, LCD_SEG36, TIM16_CH1, CM4_EVENTOUT	-	
-	-	B10	A1	PE1	I/O	FT_I	1	TSC_G7_IO2, LCD_SEG37, TIM17_CH1, CM4_EVENTOUT	-	
-	-	E6	B1	PE2	I/O	FT_I	-	TRACECK, SAI1_PDM_CK1, TSC_G7_IO1, LCD_SEG38, SAI1_MCLK_A, CM4_EVENTOUT	-	
-	-	C9	C1	PD13	I/O	FT_I	-	TSC_G6_IO4, LCD_SEG33, LPTIM2_OUT, CM4_EVENTOUT	-	
-	-	D8	D3	PD14	I/O	FT_I	-	TIM1_CH1, LCD_SEG34, CM4_EVENTOUT	-	
-	-	E7	C2	PD15	I/O	FT_I	-	TIM1_CH2, LCD_SEG35, CM4_EVENTOUT	-	
1	1	C10	D2	VBAT	S	-	-	-	-	
-	2	G5	F4	PC13	I/O	FT	(1) (2)	CM4_EVENTOUT	RTC_TAMP1/RTC_TS/ RTC_OUT/WKUP2	
2	3	D10	E3	PC14- OSC32_IN	I/O	FT	(1) (2)	CM4_EVENTOUT	OSC32_IN	
3	4	D9	E2	PC15- OSC32_OUT	I/O	FT	(1) (2)	CM4_EVENTOUT	OSC32_OUT	
-	-	-	E5	VSS	S	-	-	-	-	
-	-	-	F6	VDD	S	-	-	-	-	
-	-	E10	F1	PH0	I/O	FT	-	CM4_EVENTOUT	-	
-	-	E9	G2	PH1	I/O	FT	-	CM4_EVENTOUT	-	
4	5	E8	G1	PH3-BOOT0	I/O	FT	-	CM4_EVENTOUT, LSCO ⁽³⁾	-	
5	6	F7	G3	PB8	I/O	FT_fl	-	TIM1_CH2N, SAI1_PDM_CK1, I2C1_SCL, QUADSPI_BK1_IO1, LCD_SEG16, SAI1_MCLK_A, TIM16_CH1, CM4_EVENTOUT	-	



Table 16. STM32WB55xx pin and ball definitions (continued)

	Pin ı	numb	er			se.			
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
6	7	F10	H4	PB9	I/O	FT_fla	-	TIM1_CH3N, SAI1_PDM_DI2, I2C1_SDA, SPI2_NSS, IR_OUT, TSC_G7_IO4, QUADSPI_BK1_IO0, LCD_COM3, SAI1_FS_A, TIM17_CH1, CM4_EVENTOUT	-
7	8	F9	H2	NRST	I/O	RST	-	-	-
-	9	F8	НЗ	PC0	I/O	FT_fla	-	LPTIM1_IN1, I2C3_SCL, LPUART1_RX, LCD_SEG18, LPTIM2_IN1, CM4_EVENTOUT	ADC1_IN1
-	10	G8	Н1	PC1	I/O	FT_fla	-	LPTIM1_OUT, SPI2_MOSI, I2C3_SDA, LPUART1_TX, LCD_SEG19, CM4_EVENTOUT	ADC1_IN2
-	11	G9	J2	PC2	I/O	FT_la	-	LPTIM1_IN2, SPI2_MISO, LCD_SEG20, CM4_EVENTOUT	ADC1_IN3
-	-	-	E7	VSS	S	-	-	-	-
-	-	-	H6	VDD	S	-	-	-	-
-	12	G10	J3	PC3	I/O	FT_a	-	LPTIM1_ETR, SAI1_PDM_DI1, SPI2_MOSI, LCD_VLCD, SAI1_SD_A, LPTIM2_ETR, CM4_EVENTOUT	ADC1_IN4
-	-	H10	K2	VSSA	Ø	-	-	-	-
-	13	H8	L1	VREF+	S	-	-	-	VREFBUF_OUT
8	14	H9	K3	VDDA	S	-	(4)	-	-
-	-	J9	E9	VSS	S	-	-	-	-
-	1	J10	F8	VDD	S	-	-	-	-
9	15	G7	M1	PA0	I/O	FT_a	-	TIM2_CH1, COMP1_OUT, SAI1_EXTCLK, TIM2_ETR, CM4_EVENTOUT	COMP1_INM, ADC1_IN5, RTC_TAMP2/WKUP1
10	16	G6	L2	PA1	I/O	FT_la	-	TIM2_CH2, I2C1_SMBA, SPI1_SCK, LCD_SEG0, CM4_EVENTOUT	COMP1_INP, ADC1_IN6

Table 16. STM32WB55xx pin and ball definitions (continued)

	Pin ı	numb	er				•	and ban definitions (contin	,
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
11	17	F6	N1	PA2	I/O	FT_la	-	LSCO ⁽³⁾ , TIM2_CH3, LPUART1_TX, QUADSPI_BK1_NCS, LCD_SEG1, COMP2_OUT, CM4_EVENTOUT	COMP2_INM, ADC1_IN7, WKUP4
12	18	J8	M2	PA3	I/O	FT_la	-	TIM2_CH4, SAI1_PDM_CK1, LPUART1_RX, QUADSPI_CLK, LCD_SEG2, SAI1_MCLK_A, CM4_EVENTOUT	COMP2_INP, ADC1_IN8
13	19	K10	L3	PA4	I/O	FT_a	-	SPI1_NSS, SAI1_FS_B, LPTIM2_OUT, LCD_SEG5, CM4_EVENTOUT	COMP1_INM, COMP2_INM, ADC1_IN9
14	20	K9	N2	PA5	I/O	FT_a	ı	TIM2_CH1, TIM2_ETR, SPI1_SCK, LPTIM2_ETR, SAI1_SD_B, CM4_EVENTOUT	COMP1_INM, COMP2_INM, ADC1_IN10
15	21	H7	М3	PA6	I/O	FT_la	1	TIM1_BKIN, SPI1_MISO, LPUART1_CTS, QUADSPI_BK1_IO3, LCD_SEG3, TIM16_CH1, CM4_EVENTOUT	ADC1_IN11
16	22	H6	N3	PA7	I/O	FT_fla	ı	TIM1_CH1N, I2C3_SCL, SPI1_MOSI, QUADSPI_BK1_IO2, LCD_SEG4, COMP2_OUT, TIM17_CH1, CM4_EVENTOUT	ADC1_IN12
17	23	J7	M4	PA8	I/O	FT_la	1	MCO, TIM1_CH1, SAI1_PDM_CK2, USART1_CK, LCD_COM0, SAI1_SCK_A, LPTIM2_OUT, CM4_EVENTOUT	ADC1_IN15
18	24	K8	L4	PA9	I/O	FT_fla	ı	TIM1_CH2, SAI1_PDM_DI2, I2C1_SCL, SPI2_SCK, USART1_TX, LCD_COM1, SAI1_FS_A, CM4_EVENTOUT	COMP1_INM, ADC1_IN16
-	25	G4	M5	PC4	PC4 I/O FT_la		_	LCD_SEG22, CM4_EVENTOUT	COMP1_INM, ADC1_IN13
-	-	-	F3	VSS_DCAP1	S	-	-	-	-
-	-	-	G7	VDD	S	-	-	-	-



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Table 16. STM32WB55xx pin and ball definitions (continued)

	Pin number			Table 10. 311v				,	,
	Pin r	numb	er			es			
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
-	26	H5	L5	PC5	I /O	FT_la	1	SAI1_PDM_DI3, LCD_SEG23, CM4_EVENTOUT	COMP1_INP, ADC1_IN14, WKUP5
19	27	K7	N6	PB2	I/O	FT_a	-	RTC_OUT, LPTIM1_OUT, I2C3_SMBA, SPI1_NSS, LCD_VLCD, SAI1_EXTCLK, CM4_EVENTOUT	COMP1_INP
1	28	K6	L6	PB10	I/O	FT_fl	-	TIM2_CH3, I2C3_SCL, SPI2_SCK, LPUART1_RX, TSC_SYNC, QUADSPI_CLK, LCD_SEG10, COMP1_OUT, SAI1_SCK_A, CM4_EVENTOUT	-
-	29	J6	M6	PB11	I/O	FT_fl	ı	TIM2_CH4, I2C3_SDA, LPUART1_TX, QUADSPI_BK1_NCS, LCD_SEG11, COMP2_OUT, CM4_EVENTOUT	-
-	-	-	G5	VSS	S	ı	1	-	-
	-	-	G9	VSS	S	ı	-	-	-
20	30	K5	H8	VDD	S	ı	-	-	-
-	-	-	N8	VSSRF	S	ı	ı	-	-
-	-	J4	L7	VSSRF	S	ı	-	-	-
-	-	-	L8	VSSRF	S	ı	-	-	-
-	-	-	M8	VSSRF	S	ı	-	-	-
21	31	K4	M9	RF1	I/O	RF	(5)	-	-
22	32	K3	M10	VSSRF	S	-	-	-	-
-	-	K2	M11	VSSRF	S	-	-	-	-
-	-	-	K8	VSSRF	S	-	-	-	-
-	-	-	L9	VSSRF	S	-	-	-	-
-	-	-	L10	VSSRF	S	-	-	-	-
-	-	-	N11	VSSRF	S	-	-	-	-
23	33	J3	N12	VDDRF	S	-	-	-	-
-	-	K1	K10	VSSRF	S	-	-	-	-
-	-	-	M12	VSSRF	S	-	-	-	-
24	34	J2	N13	OSC_OUT	0	RF	(6)	-	-

Table 16. STM32WB55xx pin and ball definitions (continued)

	Pin number					_	•	and ban deminions (contin	,
	Pin r	numb	er			es			
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
25	35	J1	M13	OSC_IN	I	RF	(6)	-	-
-	-	-	L11	VSSRF	S	-	-	-	-
26	36	НЗ	K11	AT0	0	RF	(7)	-	-
27	37	H4	K12	AT1	0	RF	(7)	-	-
28	38	H2	L13	PB0	I/O	TT	(8)	COMP1_OUT, CM4_EVENTOUT, RF_TX_MOD_EXT_PA	-
29	39	H1	L12	PB1	1/0	TT	(8)	LPUART1_RTS_DE, LPTIM2_IN1, CM4_EVENTOUT	-
-	-	J5	-	VSS	S	-	-	-	-
-	-	-	M7	VSS_DCAP2	S	-	-	-	-
-	-	G2	H12	PE3	I/O	FT	-	CM4_EVENTOUT	-
30	40	G1	H13	PE4	I/O	FT	-	CM4_EVENTOUT	-
31	41	F2	H11	VFBSMPS	S	-	-	-	-
-	-	-	G13	VSSSMPS	S	-	-	-	-
32	42	F1	G12	VSSSMPS	S	-	-	-	-
33	43	E1	F11	VLXSMPS	S	-	-	-	-
-	-	-	G11	VLXSMPS	S	ı	-	-	-
34	44	D1	F12	VDDSMPS	S	-	-	-	-
-	-	-	F13	VDDSMPS	S	-	-	-	-
-	-	-	K4	VSS	S	-	-	-	-
35	45	B1	-	VDD	S	-	-	-	-
-	46	G3	H10	PB12	I/O	FT_I	-	TIM1_BKIN, I2C3_SMBA, SPI2_NSS, LPUART1_RTS, TSC_G1_IO1, LCD_SEG12, SAI1_FS_A, CM4_EVENTOUT	-
-	47	C1	E12	PB13	I/O	FT_fl	-	TIM1_CH1N, I2C3_SCL, SPI2_SCK, LPUART1_CTS, TSC_G1_IO2, LCD_SEG13, SAI1_SCK_A, CM4_EVENTOUT	-



Table 16. STM32WB55xx pin and ball definitions (continued)

	Pin r	numb	er			es			
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
-	48	E2	E11	PB14	I/O	FT_fl	1	TIM1_CH2N, I2C3_SDA, SPI2_MISO, TSC_G1_IO3, LCD_SEG14, SAI1_MCLK_A, CM4_EVENTOUT	-
-	49	F3	F10	PB15	I/O	FT_I	-	RTC_REFIN, TIM1_CH3N, SPI2_MOSI, TSC_G1_IO4, LCD_SEG15, SAI1_SD_A, CM4_EVENTOUT	-
-	50	D2	D10	PC6	I/O	FT_I	-	TSC_G4_IO1, LCD_SEG24, CM4_EVENTOUT	-
-	-	E3	D12	PC7	I/O	FT_I	-	TSC_G4_IO2, LCD_SEG25, CM4_EVENTOUT	-
-	-	F4	D11	PC8	I/O	FT_I	-	TSC_G4_IO3, LCD_SEG26, CM4_EVENTOUT	-
-	-	B4	C13	PC9	I/O	FT_I	-	TIM1_BKIN, TSC_G4_IO4, USB_NOE, LCD_SEG27, SAI1_SCK_B, CM4_EVENTOUT	-
-	-	-	K6	VSS	S	-	-	-	-
-	-	B2	-	VSS	S	-	-	-	-
36	51	B5	C12	PA10	I/O	FT_fl	-	TIM1_CH3, SAI1_PDM_DI1, I2C1_SDA, USART1_RX, USB_CRS_SYNC, LCD_COM2, SAI1_SD_A, TIM17_BKIN, CM4_EVENTOUT	-
37	52	A1	B13	PA11	I/O	FT_u	-	TIM1_CH4, TIM1_BKIN2, SPI1_MISO, USART1_CTS, USB_DM, CM4_EVENTOUT	-
38	53	A2	A13	PA12	I/O	FT_u	-	TIM1_ETR, SPI1_MOSI, LPUART1_RX, USART1_RTS_DE, USB_DP, CM4_EVENTOUT	-
39	54	A5	A11	PA13 (JTMS_SWDIO)	I/O	FT_u	(9)	JTMS-SWDIO, IR_OUT, USB_NOE, SAI1_SD_B, CM4_EVENTOUT	-
40	55	В3	A12	VDDUSB	S	-	-	-	-
	-	-	C11	VSS	S	-	-	-	-

Table 16. STM32WB55xx pin and ball definitions (continued)

	Pin r	numb	er			se.			
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
41	56	А3	C10	PA14 (JTCK_SWCLK)	I/O	FT_I	(9)	JTCK-SWCLK, LPTIM1_OUT, I2C1_SMBA, LCD_SEG5, SAI1_FS_B, CM4_EVENTOUT	-
42	57	A4	С9	PA15 (JTDI)	I/O	FT_I	(9)	JTDI, TIM2_CH1, TIM2_ETR, SPI1_NSS, TSC_G3_IO1, LCD_SEG17, CM4_EVENTOUT, MCO	-
-	-	-	J11	VSS_DCAP3	S	-	-	-	-
-	58	A6	В9	PC10	I/O	FT_I	-	TRACED1, TSC_G3_IO2, LCD_COM4/LCD_SEG28/ LCD_SEG40, CM4_EVENTOUT	-
-	59	В6	C8	PC11	I/O	FT_I	-	TSC_G3_IO3, LCD_COM5/LCD_SEG29/ LCD_SEG41, CM4_EVENTOUT	-
-	60	C5	B10	PC12	I/O	FT_I	-	LSCO ⁽³⁾ , TRACED3, TSC_G3_IO4, LCD_COM6/LCD_SEG30/ LCD_SEG42, CM4_EVENTOUT	RTC_TAMP3/WKUP3
-	61	C4	B11	PD0	I/O	FT	-	SPI2_NSS, CM4_EVENTOUT	-
-	62	C3	C7	PD1	I/O	FT	-	SPI2_SCK, CM4_EVENTOUT	-
-	1	A7	В7	PD2	I/O	FT_I	-	TRACED2, TSC_SYNC, LCD_COM7/LCD_SEG31/LC D_SEG43, CM4_EVENTOUT	-
-	-	C2	D8	PD3	I/O	FT	-	SPI2_SCK, SPI2_MISO, QUADSPI_BK1_NCS, CM4_EVENTOUT	-
-	-	D3	C6	PD4	I/O	FT	-	SPI2_MOSI, TSC_G5_IO1, QUADSPI_BK1_IO0, CM4_EVENTOUT	-
-	-	В7	A6	PD5	I/O	FT	-	TSC_G5_IO2, QUADSPI_BK1_IO1, SAI1_MCLK_B, CM4_EVENTOUT	-



Table 16. STM32WB55xx pin and ball definitions (continued)

	Pin r	numb	er				•	and ban definitions (contin	,
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
-	1	C6	D6	PD6	I/O	FT	-	SAI1_PDM_DI1, TSC_G5_IO3, QUADSPI_BK1_IO2, SAI1_SD_A, CM4_EVENTOUT	-
-	-	A8	C5	PD7	I/O	FT_I	-	TSC_G5_IO4, QUADSPI_BK1_IO3, LCD_SEG39, CM4_EVENTOUT	-
-	-	В9	B12	VSS	S	-	-	-	-
-	-	D4	В6	PD8	I/O	FT_I	-	TIM1_BKIN2, LCD_SEG28, CM4_EVENTOUT	-
-	-	D5	D4	PD9	I/O	FT_I	-	TRACED0, LCD_SEG29, CM4_EVENTOUT	-
-	1	E4	A7	PD10	I/O	FT_I	-	TRIG_INOUT, TSC_G6_IO1, LCD_SEG30, CM4_EVENTOUT	-
-	1	E5	B5	PD11	I/O	FT_I	-	TSC_G6_IO2, LCD_SEG31, LPTIM2_ETR, CM4_EVENTOUT	-
-	-	B8	B4	PD12	I/O	FT_I	-	TSC_G6_IO3, LCD_SEG32, LPTIM2_IN1, CM4_EVENTOUT	-
43	63	A9	C4	PB3 (JTDO)	I/O	FT_la	(9)	JTDO-TRACESWO, TIM2_CH2, SPI1_SCK, USART1_RTS_DE, LCD_SEG7, SAI1_SCK_B, CM4_EVENTOUT	COMP2_INM
44	64	C7	В3	PB4 (NJTRST)	I/O	FT_fla	(9)	NJTRST, I2C3_SDA, SPI1_MISO, USART1_CTS, TSC_G2_IO1, LCD_SEG8, SAI1_MCLK_B, TIM17_BKIN, CM4_EVENTOUT	COMP2_INP
45	65	D6	A3	PB5	I/O	FT_I	-	LPTIM1_IN1, I2C1_SMBA, SPI1_MOSI, USART1_CK, LPUART1_TX, TSC_G2_IO2, LCD_SEG9, COMP2_OUT, SAI1_SD_B, TIM16_BKIN, CM4_EVENTOUT	-

1able 16. 511V	1321	VB55XX	pın	and ball definitions (contin	iuea)

	Pin ı	numb	er			se.			
UFQFPN48	VFQFPN68	WLCSP100	UFBGA129	Pin name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
46	66	F5	A2	PB6	I/O	FT_fla	1	LPTIM1_ETR, I2C1_SCL, USART1_TX, TSC_G2_IO3, LCD_SEG6, SAI1_FS_B, TIM16_CH1N, MCO, CM4_EVENTOUT	COMP2_INP
47	67	D7	C3	PB7	I/O	FT_fla	-	LPTIM1_IN2, TIM1_BKIN, I2C1_SDA, USART1_RX, TSC_G2_IO4, LCD_SEG21, TIM17_CH1N, CM4_EVENTOUT	COMP2_INM, PVD_IN
-	-	-	J5	VSS	S	-	-	-	-
-	-	-	J7	VSS	S	-	-	-	-
-	-	-	J9	VSS	S	-	-	-	-
-	-	-	B8	VSS_DCAP4	S	-	-	-	-
48	68	A10	1	VDD	S	-	-	-	-
-	-	-	A8	VDD_DCAP4	S	-	-	-	-
-	-	-	F2	VDD_DCAP1	S	-	-	-	-
-	-	-	J12	VDD_DCAP3	S	-	-	-	-
-	-	-	N7	VDD_DCAP2	S	-	-	-	-

PC13, PC14 and PC15 are supplied through the power switch. As this switch only sinks a limited amount of current (3 mA), the use of the PC13, PC14 and PC15 GPlOs in output mode is limited:
- the speed must not exceed 2 MHz with a maximum load of 30 pF

- 3. The clock on LSCO is available in Run and Stop modes, and on PA2 in Standby and Shutdown modes.
- 4. On UFQFPN48 VDDA is connected to VREF+.
- 5. RF pin, use the nominal PCB layout.
- 6. 32 MHz oscillator pins, use the nominal PCB layout according to reference design (see AN5165).
- 7. Reserved, must be kept unconnected.
- High frequency (above 32 kHz) may impact the RF performance. Set output speed GPIOB_OSPEEDRy[1:0] to 00 (y = 0 and 1) during RF operation.
- After reset these pins are configured as JTAG/SW debug alternate functions, and the internal pull-up on PA15, PA13 and PB4 pins and the internal pull-down on PA14 pin are activated.

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⁻ these GPIOs must not be used as current sources (e.g. to drive a LED).

^{2.} After a Backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers that are not reset by the system reset. For details on how to manage these GPIOs, refer to the Backup domain and RTC register descriptions in the reference manual RM0434, available on www.st.com.

Table 17. STM32WB35xx pin and ball definitions

	Table 17. STM32WB35XX pin and ball definitions										
	Pin	e	ures								
Number	Name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions					
1	VBAT	S	-	-	-	-					
2	PC14-OSC32_IN	I/O	FT	(1) (2)	CM4_EVENTOUT	OSC32_IN					
3	PC15-OSC32_OUT	I/O	FT	(1) (2)	CM4_EVENTOUT	OSC32_OUT					
4	PH3-BOOT0	I/O	FT	-	CM4_EVENTOUT, LSCO ⁽³⁾	-					
5	PB8	I/O	FT_f	-	TIM1_CH2N, SAI1_PDM_CK1, I2C1_SCL, QUADSPI_BK1_IO1, SAI1_MCLK_A, TIM16_CH1, CM4_EVENTOUT	-					
6	PB9	I/O	FT_f	-	TIM1_CH3N, SAI1_PDM_DI2, I2C1_SDA, IR_OUT, QUADSPI_BK1_IO0, SAI1_FS_A, TIM17_CH1, CM4_EVENTOUT	-					
7	NRST	I/O	RST	-	-	-					
8	VDDA	S	-	-	-	-					
9	PA0	I/O	FT_a	-	TIM2_CH1, COMP1_OUT, SAI1_EXTCLK, TIM2_ETR, CM4_EVENTOUT	COMP1_INM, ADC1_IN5, RTC_TAMP2/WKUP1					
10	PA1	I/O	FT_a	-	TIM2_CH2, I2C1_SMBA, SPI1_SCK, CM4_EVENTOUT	COMP1_INP, ADC1_IN6					
11	PA2	I/O	FT_a	-	LSCO ⁽³⁾ , TIM2_CH3, LPUART1_TX, QUADSPI_BK1_NCS, COMP2_OUT, CM4_EVENTOUT	COMP2_INM, ADC1_IN7, WKUP4					
12	PA3	I/O	FT_a	-	TIM2_CH4, SAI1_PDM_CK1, LPUART1_RX, QUADSPI_CLK, SAI1_MCLK_A, CM4_EVENTOUT	COMP2_INP, ADC1_IN8					
13	PA4	I/O	FT_a	-	SPI1_NSS, SAI1_FS_B, LPTIM2_OUT, CM4_EVENTOUT	COMP1_INM, COMP2_INM, ADC1_IN9					
14	PA5	I/O	FT_a	-	TIM2_CH1, TIM2_ETR, SPI1_SCK, LPTIM2_ETR, SAI1_SD_B, CM4_EVENTOUT	COMP1_INM, COMP2_INM, ADC1_IN10					
15	PA6	I/O	FT_a	-	TIM1_BKIN, SPI1_MISO, LPUART1_CTS, QUADSPI_BK1_IO3, TIM16_CH1, CM4_EVENTOUT	ADC1_IN11					
16	PA7	I/O	FT_fa	-	TIM1_CH1N, I2C3_SCL, SPI1_MOSI, QUADSPI_BK1_IO2, COMP2_OUT, TIM17_CH1, CM4_EVENTOUT	ADC1_IN12					
17	PA8	I/O	FT_a	-	MCO, TIM1_CH1, SAI1_PDM_CK2, USART1_CK, SAI1_SCK_A, LPTIM2_OUT, CM4_EVENTOUT	ADC1_IN15					

Table 17. STM32WB35xx pin and ball definitions (continued)

	Pin	e e	ures	"			
Number	Name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions	
18	PA9	I/O	FT_fa	-	TIM1_CH2, SAI1_PDM_DI2, I2C1_SCL, USART1_TX, SAI1_FS_A, CM4_EVENTOUT	COMP1_INM, ADC1_IN16	
19	PB2	I/O	FT_a	-	RTC_OUT, LPTIM1_OUT, I2C3_SMBA, SPI1_NSS, SAI1_EXTCLK, CM4_EVENTOUT	COMP1_INP	
20	VDD	S	-	-	-	-	
21	RF1	I/O	RF	(4)	-	-	
22	VSSRF	S	-	-	-	-	
23	VDDRF	S	-	-	-	-	
24	OSC_OUT	0	RF	(5)	-	-	
25	OSC_IN	I	RF	(5)	-	-	
26	AT0	0	RF	(6)	-	-	
27	AT1	0	RF	(6)	-	-	
28	PB0	I/O	TT	(7)	COMP1_OUT, CM4_EVENTOUT, RF_TX_MOD_EXT_PA	-	
29	PB1	I/O	TT	(7)	LPUART1_RTS_DE, LPTIM2_IN1, CM4_EVENTOUT	-	
30	PE4	I/O	FT	-	CM4_EVENTOUT	-	
31	VFBSMPS	S	-	-	-	-	
32	VSSSMPS	S	-	-	-	-	
33	VLXSMPS	S	-	-	-	-	
34	VDDSMPS	S	-	-	-	-	
35	VDD	S	-	-	-	-	
36	PA10	I/O	FT_f	-	TIM1_CH3, SAI1_PDM_DI1, I2C1_SDA, USART1_RX, USB_CRS_SYNC, SAI1_SD_A, TIM17_BKIN, CM4_EVENTOUT	-	
37	PA11	I/O	FT_u	-	TIM1_CH4, TIM1_BKIN2, SPI1_MISO, USART1_CTS, USB_DM, CM4_EVENTOUT	-	
38	PA12	I/O	FT_u	ı	TIM1_ETR, SPI1_MOSI, LPUART1_RX, USART1_RTS_DE, USB_DP, CM4_EVENTOUT	-	
39	PA13 (JTMS-SWDIO)	I/O	FT	(8)	JTMS-SWDIO, IR_OUT, USB_NOE, SAI1_SD_B, CM4_EVENTOUT	-	
40	VDDUSB	S	-	-	-	-	



	Pin	90	ures	"		
Number	Name (function after reset)	Pin type	I/O structures	Notes	Alternate functions	Additional functions
41	PA14 (JTCK-SWCLK)	I/O	FT	(8)	JTCK-SWCLK, LPTIM1_OUT, I2C1_SMBA, SAI1_FS_B, CM4_EVENTOUT	-
42	PA15 (JTDI)	I/O	FT	(8)	JTDI, TIM2_CH1, TIM2_ETR, SPI1_NSS, CM4_EVENTOUT, MCO	-
43	PB3 (JTDO)	I/O	FT_a	-	JTDO-TRACESWO, TIM2_CH2, SPI1_SCK, USART1_RTS_DE, SAI1_SCK_B, CM4_EVENTOUT	COMP2_INM
44	PB4 (NJTRST)	I/O	FT_fa	(8)	NJTRST, I2C3_SDA, SPI1_MISO, USART1_CTS, SAI1_MCLK_B, TIM17_BKIN, CM4_EVENTOUT	COMP2_INP
45	PB5	I/O	FT_a	-	LPTIM1_IN1, I2C1_SMBA, SPI1_MOSI, USART1_CK, LPUART1_TX, COMP2_OUT, SAI1_SD_B, TIM16_BKIN, CM4_EVENTOUT	-
46	PB6	I/O	FT_fa	-	LPTIM1_ETR, I2C1_SCL, USART1_TX, SAI1_FS_B, TIM16_CH1N, MCO, CM4_EVENTOUT	COMP2_INP
47	PB7	I/O	FT_fa	1	LPTIM1_IN2, TIM1_BKIN, I2C1_SDA, USART1_RX, TIM17_CH1N, CM4_EVENTOUT	COMP2_INM, PVD_IN
48	VDD S		-	-		

Table 17. STM32WB35xx pin and ball definitions (continued)

- PC14 and PC15 are supplied through the power switch. As this switch only sinks a limited amount of current (3 mA), the
 use of the PC14 and PC15 GPIOs in output mode is limited:

 the speed must not exceed 2 MHz with a maximum load of 30 pF

 - these GPIOs must not be used as current sources (e.g. to drive a LED).
- After a Backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers that are not reset by the system reset. For details on how to manage these GPIOs, refer to the Backup domain and RTC register descriptions in the reference manual RM0434, available on www.st.com.
- 3. The clock on LSCO is available in Run and Stop modes, and on PA2 in Standby and Shutdown modes.
- 4. RF pin, use the nominal PCB layout.
- 5. 32 MHz oscillator pins, use the nominal PCB layout according to reference design (see AN5165).
- 6. Reserved, must be kept unconnected.
- 7. High frequency (above 32 kHz) may impact the RF performance. Set output speed GPIOB_OSPEEDRy[1:0] to 00 (y = 0 and 1) during RF operation.
- 8. After reset these pins are configured as JTAG/SW debug alternate functions, and the internal pull-up on PA15, PA13 and PB4 pins and the internal pull-down on PA14 pin are activated.



Table 18. Alternate functions (STM32WB55xx)

			l	l	I			ı		10113 (01		1		l	l	l	1
		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
F	Port	SYS_AF	TIM1/ TIM2/ LPTIM1	TIM1/ TIM2	SPI2/ SAI1/ TIM1	I2C1/ I2C3	SPI1/ SPI2	RF	USART1	LPUART1	TSC	USB/ QUADSPI	LCD	COMP1/ COMP2/ TIM1	SAI1	TIM2/ TIM16/ TIM17/ LPTIM2	EVENTOUT
	PA0	-	TIM2_ CH1	-	-	-	-	-	-	-	-	-	-	COMP1_ OUT	SAI1_ EXTCLK	TIM2_ ETR	CM4_ EVENTOUT
	PA1	ı	TIM2_ CH2	-	-	I2C1_ SMBA	SPI1_ SCK	-	-		i	-	LCD_SEG0	-	-	-	CM4_ EVENTOUT
	PA2	LSCO	TIM2_ CH3	-	-		-	-	-	LPUART1 _TX	-	QUADSPI_ BK1_NCS	LCD_SEG1	COMP2_ OUT	-	-	CM4_ EVENTOUT
	PA3	-	TIM2_ CH4	-	SAI1_ PDM_CK1	-	-	-	-	LPUART1 _RX	-	QUADSPI_ CLK	LCD_SEG2	-	SAI1 _MCLK_A	-	CM4_ EVENTOUT
	PA4	-	-	-	-		SPI1_ NSS	-	-	-	-	-	LCD_SEG5	-	SAI1 _FS_B	LPTIM2_ OUT	CM4_ EVENTOUT
	PA5	-	TIM2_ CH1	TIM2_ ETR	-		SPI1_ SCK	-	-	-	-	-	-	-	SAI1 _SD_B	LPTIM2_ ETR	CM4_ EVENTOUT
	PA6	-	TIM1_ BKIN	-	-		SPI1_ MISO	-	-	LPUART1 _CTS	-	QUADSPI_ BK1_IO3	LCD_SEG3	TIM1_ BKIN	-	TIM16 _CH1	CM4_ EVENTOUT
A	PA7	-	TIM1_ CH1N	-	-	I2C3_ SCL	SPI1_ MOSI	-	-	-	-	QUADSPI_ BK1_IO2	LCD_SEG4	COMP2_ OUT	-	TIM17 _CH1	CM4_ EVENTOUT
^	PA8	МСО	TIM1_ CH1	-	SAI1_ PDM_CK2		-	-	USART1_ CK	-	-		LCD_COM0	-	SAI1 _SCK_A	LPTIM2_ OUT	CM4_ EVENTOUT
	PA9	-	TIM1_ CH2	-	SAI1_ PDM_DI2	I2C1_ SCL	SPI2_ SCK	-	USART1_ TX	-	-		LCD_COM1	-	SAI1 _FS_A	-	CM4_ EVENTOUT
	PA10	-	TIM1_ CH3	-	SAI1_ PDM_DI1	I2C1_ SDA		-	USART1_ RX	-	-	USB_CRS _SYNC	LCD_COM2	-	SAI1 _SD_A	TIM17 _BKIN	CM4_ EVENTOUT
	PA11	-	TIM1_ CH4	TIM1_ BKIN2	-		SPI1_ MISO	-	USART1_ CTS	-	-	USB_DM	-	TIM1_ BKIN2	-	-	CM4_ EVENTOUT
	PA12	-	TIM1_ ETR	-	-	-	SPI1_ MOSI	-	USART1_ RTS_DE	LPUART1 _RX	-	USB_DP	-	-	-	-	CM4_ EVENTOUT
	PA13	JTMS- SWDIO	-	-	-		-	-	-	IR_OUT	-	USB_NOE	-	-	SAI1 _SD_B	-	CM4_ EVENTOUT
	PA14	JTCK- SWCLK	LPTIM1_ OUT	-	-	I2C1_ SMBA	-	-	-	-	-	-	LCD_SEG5	-	SAI1 _FS_B	-	CM4_ EVENTOUT
	PA15	JTDI	TIM2_ CH1	TIM2_ ETR	-		SPI1_ NSS	MCO	-	-		-	LCD_SEG17	-	-	-	CM4_ EVENTOUT

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/196		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
	Port	SYS_AF	TIM1/ TIM2/ LPTIM1	TIM1/ TIM2	SPI2/ SAI1/ TIM1	I2C1/ I2C3	SPI1/ SPI2	RF	USART1	LPUART1	TSC	USB/ QUADSPI	LCD	COMP1/ COMP2/ TIM1	SAI1	TIM2/ TIM16/ TIM17/ LPTIM2	EVENTOUT
	РВ0	-	-	-	-	-	-	RF_TX_ MOD_ EXT_PA	-		-	-	-	COMP1_ OUT	-	-	CM4_ EVENTOUT
	PB1	-	-	-	-	-	-	-	-	LPUART1 _RTS_DE	-	-	-	-	-	LPTIM2_ IN1	CM4_ EVENTOUT
	PB2	RTC_ OUT	LPTIM1_ OUT	-	-	I2C3_ SMBA	SPI1_ NSS	-	-,	-	-	-	LCD_VLCD	-	SAI1_ EXTCLK	-	CM4_ EVENTOUT
	РВ3	JTDO- TRACE SWO	TIM2_ CH2	-	-	-	SPI1_ SCK	-	USART1_ RTS_DE	-	-	-	LCD_SEG7	-	SAI1_ SCK_B	-	CM4_ EVENTOUT
D	PB4	NJTRST	-	-	-	I2C3_ SDA	SPI1_ MISO	-	USART1_ CTS	-	TSC_G2 _IO1	-	LCD_SEG8	-	SAI1_ MCLK_B	TIM17_ BKIN	CM4_ EVENTOUT
61192	PB5	-	LPTIM1_ IN1	-	-	I2C1_ SMBA	SPI1_ MOSI	-	USART1_ CK	LPUART1 _TX	TSC_G2 _IO2	-	LCD_SEG9	COMP2_ OUT	SAI1_ SD_B	TIM16_ BKIN	CM4_ EVENTOUT
DS11929 Rev 14	PB6	МСО	LPTIM1_ ETR	-	-	I2C1_ SCL	-	-	USART1_ TX	-	TSC_G2 _IO3	-	LCD_SEG6	-	SAI1_ FS_B	TIM16_ CH1N	CM4_ EVENTOUT
14	B PB7	-	LPTIM1_ IN2	-	TIM1_ BKIN	I2C1_ SDA	-	-	USART1_ RX	-	TSC_G2 _IO4	-	LCD_SEG21	-	-	TIM17_ CH1N	CM4_ EVENTOUT
	PB8	-	TIM1_ CH2N	-	SAI1_ PDM_CK1	I2C1_ SCL	-	-	-	-	ı	QUADSPI_ BK1_IO1	LCD_SEG16	ı	SAI1_ MCLK_A	TIM16_ CH1	CM4_ EVENTOUT
	РВ9	-	TIM1_ CH3N	-	SAI1_ PDM_DI2	I2C1_ SDA	SPI2_ NSS	-	-	IR_OUT	TSC_G7 _IO4	QUADSPI_ BK1_IO0	LCD_COM3	-	SAI1_ FS_A	TIM17_ CH1	CM4_ EVENTOUT
	PB1	-	TIM2_ CH3	-	-	I2C3_ SCL	SPI2_SC K	-	-	LPUART1 _RX	TSC _SYNC	QUADSPI_ CLK	LCD_SEG10	COMP1_ OUT	SAI1_ SCK_A	-	CM4_ EVENTOUT
	PB1	1 -	TIM2_ CH4	-	-	I2C3_ SDA	-	-	-	LPUART1 _TX	-	QUADSPI_ BK1_NCS	LCD_SEG11	COMP2_ OUT	-	-	CM4_ EVENTOUT
	PB1	2 -	TIM1_ BKIN	-	TIM1_ BKIN	I2C3_ SMBA	SPI2_ NSS	-	-	LPUART1 _RTS	TSC_G1 _IO1	-	LCD_SEG12	-	SAI1_ FS_A	-	CM4_ EVENTOUT
	PB1	-	TIM1_ CH1N	-	-	I2C3_ SCL	SPI2_ SCK	-	-	LPUART1 _CTS	TSC_G1 _IO2	-	LCD_SEG13	ı	SAI1_ SCK_A	ı	CM4_ EVENTOUT
	PB1	4 -	TIM1_ CH2N	-	-	I2C3_ SDA	SPI2_ MISO	-	-	-	TSC_G1 _IO3	-	LCD_SEG14	-	SAI1_ MCLK_A	-	CM4_ EVENTOUT
4	PB1	RTC_ REFIN	TIM1_ CH3N	-	-	-	SPI2_ MOSI	-	-	-	TSC_G1 _IO4	-	LCD_SEG15	-	SAI1_ SD_A	-	CM4_ EVENTOUT

Table 18. Alternate functions (STM32WB55xx) (continued)





Table 18. Alternate functions (STM32WB55xx) (continued)

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
	Port	SYS_AF	TIM1/ TIM2/ LPTIM1	TIM1/ TIM2	SPI2/ SAI1/ TIM1	I2C1/ I2C3	SPI1/ SPI2	RF	USART1	LPUART1	тѕс	USB/ QUADSPI	LCD	COMP1/ COMP2/ TIM1	SAI1	TIM2/ TIM16/ TIM17/ LPTIM2	EVENTOUT
	PC0	-	LPTIM1_ IN1	-	-	I2C3 _SCL	-	-	-	LPUART1 _RX	-	-	LCD_SEG18	-	-	LPTIM2_ IN1	CM4_ EVENTOUT
	PC1	-	LPTIM1_ OUT	-	SPI2_ MOSI	I2C3 _SDA		-	-	LPUART1 _TX	-	-	LCD_SEG19	-	-	-	CM4_ EVENTOUT
	PC2	-	LPTIM1_ IN2	-	-	-	SPI2_ MISO	-	-	-	-	-	LCD_SEG20	=	-	-	CM4_ EVENTOUT
	PC3	-	LPTIM1_ ETR	-	SAI1_ PDM_DI1		SPI2_ MOSI	-	-	-	-	-	LCD_VLCD	-	SAI1 _SD_A	LPTIM2_ ETR	CM4_ EVENTOUT
	PC4	-	-	-	-	-	-	-	-	-	-	-	LCD_SEG22	-	-	-	CM4_ EVENTOUT
	PC5	-	-	-	SAI1_ PDM_DI3	-	-	-	-	-	-	-	LCD_SEG23	-	-	-	CM4_ EVENTOUT
	PC6	-	-	-	-	-	-	-	-	-	TSC_G4 _IO1	-	LCD_SEG24	-	-	-	CM4_ EVENTOUT
	PC7	1	-	1	-	ı	ı	1	-	-	TSC_G4 _IO2	-	LCD_SEG25	ı	-	-	CM4_ EVENTOUT
С	PC8	-	-	-	-	1	-	-	-	-	TSC_G4 _IO3	-	LCD_SEG26	1	-	-	CM4_ EVENTOUT
	РС9	-	-	1	TIM1 _BKIN	ı	-	-	-	-	TSC_G4 _IO4	USB_NOE	LCD_SEG27	-	SAI1 _SCK_B	-	CM4_ EVENTOUT
	PC10	TRACE D1	-	ı	-	ı	ı	ı	-	-	TSC_G3 _IO2	-	LCD_COM4 LCD_SEG28 LCD_SEG40	ı	-	-	CM4_ EVENTOUT
	PC11	ı	-	ı	-	ı	ı	ı	-	-	TSC_G3 _IO3	-	LCD_COM5 LCD_SEG29 LCD_SEG41	ı	-	-	CM4_ EVENTOUT
	PC12	TRACE D3	-	-	-	ı	ı	LSCO	-	-	TSC_G3 _IO4	-	LCD_COM6 LCD_SEG30 LCD_SEG42	ı	-	-	CM4_ EVENTOUT
	PC13	-	-	-	-	ı	-	=	-	-	-	-	-	-	-	-	CM4_ EVENTOUT
	PC14	-	-	ı	-	ı	-	-	-	-	-	-	-	-	-	-	CM4_ EVENTOUT
	PC15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	CM4_ EVENTOUT

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AF13

SAI1

AF14

TIM2/

TIM16/

TIM17/

LPTIM2

AF15

EVENTOUT

CM4 **EVENTOUT** CM4 **EVENTOUT** CM4 EVENTOUT CM4 **EVENTOUT** CM4 **EVENTOUT**

CM4 **EVENTOUT**

CM4

CM4 EVENTOUT

CM4_

CM4 **EVENTOUT**

CM4_

EVENTOUT

CM4_ EVENTŌUT CM4 EVENTOUT

EVENTŌUT

LPTIM2

ETR

LPTIM2

LPTIM2_

OUT

EVENTOUT CM4 EVENTOUT CM4 **EVENTOUT** CM4_ EVENTOUT

AF12

COMP1/

COMP2/

TIM1

		PD0	-	-	-	-	-	SPI2_ NSS	-	-	-	-	-	-	-	-
		PD1	-	-	-	-	-	SPI2_ SCK	-	-	-	-	-	-	-	-
		PD2	TRACE D2	-	-	-	-	-	-	-	-	TSC_ SYNC	-	LCD_COM7 LCD_SEG31 LCD_SEG43	-	-
		PD3	-	-	-	SPI2_SCK	-	SPI2_ MISO	-	-	-	-	QUADSPI_ BK1_NCS	-	-	-
		PD4	-	-	-	-	-	SPI2_ MOSI	-	-	-	TSC_ G5_IO1	QUADSPI_ BK1_IO0	-	-	-
DS11929 Rev 14		PD5	-	-	-	-	-	-	-	-	-	TSC_ G5_IO2	QUADSPI_ BK1_IO1	-	-	SAI1_ MCLK_B
)29 R		PD6	-	-	-	SAI1_ PDM_DI1	-	-	-	-	-	TSC_ G5_IO3	QUADSPI_ BK1_IO2	-	-	SAI1_ SD_A
ev 14	D	PD7	-	-	-	-	-	-	-	-	-	TSC_ G5_IO4	QUADSPI_ BK1_IO3	LCD_SEG39	-	-
		PD8	-	-	TIM1 _BKIN2	-	-	-	-	-	-	-	-	LCD_SEG28	-	-
		PD9	TRACE D0	-	-	-	-	-	-	-	-	-	-	LCD_SEG29	-	-
		PD10	TRIG _INOUT	-	-	-	-	-	-	-	-	TSC_ G6_IO1	-	LCD_SEG30	-	-
		PD11	-	-	-	-	-	-	-	-	-	TSC_ G6_IO2	-	LCD_SEG31	-	-
		PD12	-	-	-	-	-	-	-	-	-	TSC_ G6_IO3	-	LCD_SEG32	-	-
		PD13	-	-	-	-	-	-	-	-	-	TSC_ G6_IO4	-	LCD_SEG33	-	-
		PD14	-	TIM1_ CH1	-	-	-	-	-	-	-	-	-	LCD_SEG34	-	-
3		PD15	-	TIM1_ CH2	-	-	=	-	-	-	-	-	-	LCD_SEG35	-	-

Table 18. Alternate functions (STM32WB55xx) (continued)

USART1 LPUART1

AF8

AF9

TSC

AF10

USB/

QUADSPI

AF11

LCD

AF7

76/196

AF0

SYS_AF

Port

AF1

TIM2/

LPTIM1

AF2

TIM1/

TIM2

AF3

SPI2/

SAI1/

TIM1

AF4

I2C1/

I2C3

AF5

SPI1/

SPI2

AF6

RF



Table 18. Alternate functions (STM32WB55xx) (continued)

							0. /			,	. = 00,000,	Continu	,				
		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
P	Port	SYS_AF	TIM1/ TIM2/ LPTIM1	TIM1/ TIM2	SPI2/ SAI1/ TIM1	I2C1/ I2C3	SPI1/ SPI2	RF	USART1	LPUART1	TSC	USB/ QUADSPI	LCD	COMP1/ COMP2/ TIM1	SAI1	TIM2/ TIM16/ TIM17/ LPTIM2	EVENTOUT
	PE0	-	TIM1_ ETR	-	-	-	-	-	-	-	TSC_ G7_IO3	-	LCD_SEG36	-	-	TIM16_ CH1	CM4_ EVENTOUT
	PE1	-	ı	-	-	-	ı	ı	ı	-	TSC_ G7_IO2	-	LCD_SEG37	ı	ı	TIM17_ CH1	CM4_ EVENTOUT
E	PE2	TRACECK	1	-	SAI1_ PDM_CK1	-	1	-	-	-	TSC_ G7_IO1	-	LCD_SEG38	-	SAI1_ MCLK_A	-	CM4_ EVENTOUT
	PE3	-	ı	-	-	-	ı	ı	ı	-	-	-	-	ı	ı	-	CM4_ EVENTOUT
	PE4	-	ı	-	-	-	ı	ı	ı	-	-	-	-	ı	ı	-	CM4_ EVENTOUT
	РН0	-	-	-	-	-	-	ı	-	-	-	-	-	-	-	-	CM4_ EVENTOUT
н	PH1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	CM4_ EVENTOUT
	РН3	LSCO	1	-	-	-	1	-	-	-	-	-	-	-	-	-	CM4_ EVENTOUT

Table 19. Alternate functions (STM32WB35xx) AF5 AF13 AF0 AF1 AF2 AF3 AF4 AF6 AF7 AF8 AF10 AF12 AF14 AF15 TIM2/ Port TIM1/ COMP1/ TIM1/ USB/ SAI1/ I2C1/ TIM16/ LPUART1 SYS AF TIM2/ SPI1 RF USART1 COMP2/ SAI1 **EVENTOUT** TIM2 TIM1 I2C3 QUADSPI TIM17/ LPTIM1 TIM1 LPTIM2 COMP1 CM4 TIM2 SAI1 TIM2 PA0 EVENTOUT CH1 OUT EXTCLK ETR TIM2 I2C1 SPI1 CM4 PA1 CH2 SMBA SCK **EVENTOUT** LPUART1 QUADSPI COMP2_ CM4 TIM2 PA2 LSCO CH3 BK1 NCS OUT **EVENTOUT** _TX LPUART1 TIM2 QUADSPI CM4 SAI1 SAI1 PA3 PDM CK1 **EVENTOUT** CH4 $_{\mathsf{RX}}$ CLK MCLK A SPI1 SAI1 LPTIM2 CM4 PA4 **EVENTOUT** NSS _FS_B OUT LPTIM2 TIM2 TIM2 SPI1 SAI1 CM4 PA5 **EVENTOUT** SCK _SD_B CH1 ETR ETR SPI1 LPUART1 QUADSPI TIM1 TIM16 CM4 TIM1 PA6 BKIN MISŌ _CTS BK1 IO3 BKIN CH1 **EVENTOUT** COMP2_ TIM1 12C3_ SPI1 QUADSPI TIM17 CM4 PA7 CH1N SCL MOSĪ BK1_IO2 OUT _CH1 **EVENTOUT** Α TIM1 SAI1 USART1 SAI1 LPTIM2 CM4 PA8 MCO CH1 PDM CK2 CK _SCK_A OUT **EVENTOUT** I2C1 TIM1 SAI1 USART1_ SAI1 CM4 PA9 PDM DI2 CH2 _FS_A **EVENTOUT** TIM17 SAI1 I2C1 USART1 USB CRS CM4 TIM1 SAI1 PA10 _SYNC PDM_DI1 SDA **EVENTŌUT** CH3 RX _SD_A _BKIN USART1_ TIM1 CM4 TIM1 TIM1 **PA11** USB_DM CH4 BKIN2 MISO CTS BKIN2 **EVENTŌUT** LPUART1 TIM1 SPI1 USART1 CM4 PA12 USB_DP ETR MOSĪ RTS_DE _RX **EVENTOUT** JTMS-SAI1 CM4 IR_OUT PA13 USB NOE **EVENTOUT SWDIO** SD B LPTIM1 JTCK-I2C1 SAI1 CM4 **PA14** SWCLK OUT SMBA _FS_B **EVENTOUT** TIM2 TIM2 SPI1 CM4 PA15 JTDI MCO CH1 ETR NSS **EVENTOUT**



								ilctions (31		707077 (00	······································				
		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF10	AF12	AF13	AF14	AF15
ı	Port	SYS_AF	TIM1/ TIM2/ LPTIM1	TIM1/ TIM2	SAI1/ TIM1	I2C1/ I2C3	SPI1	RF	USART1	LPUART1	USB/ QUADSPI	COMP1/ COMP2/ TIM1	SAI1	TIM2/ TIM16/ TIM17/ LPTIM2	EVENTOUT
	PB0	-	-	-	-	1	ı	RF_TX_ MOD_EXT_PA	ı		-	COMP1_ OUT	-	-	CM4_ EVENTOUT
	PB1	-	-	-	-	ı	ı	-	i	LPUART1 _RTS_DE	-	-	-	LPTIM2_ IN1	CM4_ EVENTOUT
	PB2	RTC_ OUT	LPTIM1_ OUT	-	-	I2C3_ SMBA	SPI1_ NSS	-	-	-	-	-	SAI1_ EXTCLK	-	CM4_ EVENTOUT
	РВ3	JTDO- TRACE SWO	TIM2_ CH2	-	-	-	SPI1_ SCK	-	USART1_ RTS_DE	-	-	-	SAI1_ SCK_B	-	CM4_ EVENTOUT
В	PB4	NJTRST	-	-	-	I2C3_ SDA	SPI1_ MISO	-	USART1_ CTS	-	-	-	SAI1_ MCLK_B	TIM17_ BKIN	CM4_ EVENTOUT
	PB5	-	LPTIM1_ IN1	-	-	I2C1_ SMBA	SPI1_ MOSI	-	USART1_ CK	LPUART1 _TX	-	COMP2_ OUT	SAI1_ SD_B	TIM16_ BKIN	CM4_ EVENTOUT
	PB6	MCO	LPTIM1_ ETR	-	-	I2C1_ SCL	1	-	USART1_ TX	-	-	-	SAI1_ FS_B	TIM16_ CH1N	CM4_ EVENTOUT
	PB7	-	LPTIM1_ IN2	1	TIM1_ BKIN	I2C1_ SDA	1	-	USART1_ RX	-	-	-	-	TIM17_ CH1N	CM4_ EVENTOUT
	PB8	-	TIM1_ CH2N	-	SAI1_ PDM_CK1	I2C1_ SCL	ı	-	i	-	QUADSPI_ BK1_IO1	-	SAI1_ MCLK_A	TIM16_ CH1	CM4_ EVENTOUT
	PB9	-	TIM1_ CH3N	-	SAI1_ PDM_DI2	I2C1_ SDA	1	-	ı	IR_OUT	QUADSPI_ BK1_IO0	-	SAI1_ FS_A	TIM17_ CH1	CM4_ EVENTOUT
С	PC14	-	-	-	-	-	-	-	-	-	-	-	-	-	CM4_ EVENTOUT
	PC15	-	-	-	-	-	-	-	-	-	-	-	-	-	CM4_ EVENTOUT
E	PE4	-	-	-	-	ı	1	-	-	-	-	-	-	-	CM4_ EVENTOUT
Н	РН3	LSCO	-	-	-	-	-	-	-	-	-	-	-	-	CM4_ EVENTOUT

5 Memory mapping

The STM32WB55xx and STM32WB35xx devices feature a single physical address space that can be accessed by the application processor and by the RF subsystem.

A part of the flash memory and of the SRAM2a and SRAM2b memories are made secure, exclusively accessible by the CPU2, protected against execution, read and write from CPU1 and DMA.

In case of shared resources the SW should implement arbitration mechanism to avoid access conflicts. This happens for peripherals Reset and Clock Controller (RCC), Power Controller (PWC), EXTI and flash interface, and can be implemented using the built-in semaphore block (HSEM).

By default the RF subsystem and CPU2 operate in secure mode. This implies that part of the flash and of the SRAM2 memories can only be accessed by the RF subsystem and by the CPU2. In this case the Host processor (CPU1) has no access to these resources.

The detailed memory map and the peripheral mapping can be found in the reference manual RM0434.

Ty/

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $V_{DD} = V_{DDA} = V_{DDRF} = 3 \text{ V}$ and $T_A = 25 \,^{\circ}\text{C}$. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

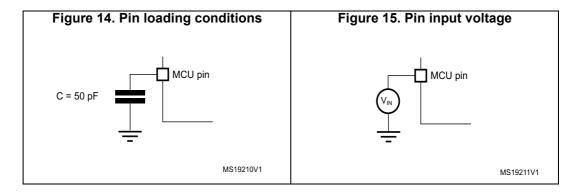
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 14.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in Figure 15.



6.1.6 Power supply scheme

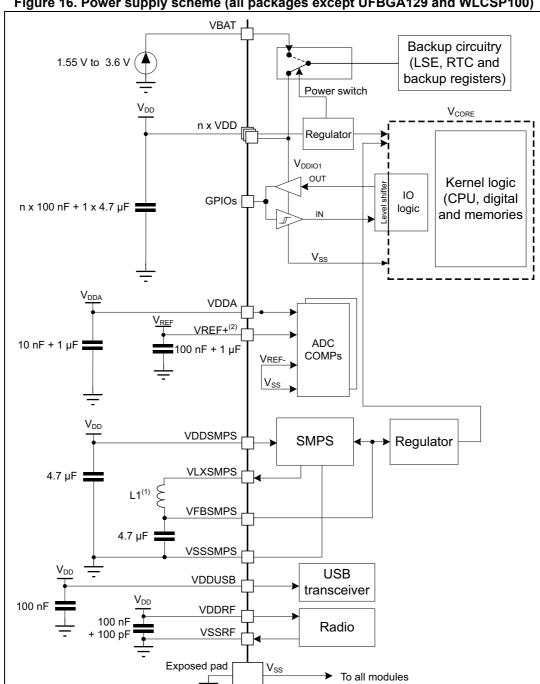


Figure 16. Power supply scheme (all packages except UFBGA129 and WLCSP100)

- 1. The value of L1 depends upon the frequency, as indicated in *Table 6*.
- 2. V_{REF+} connection is not available on UFQFPN48 package.

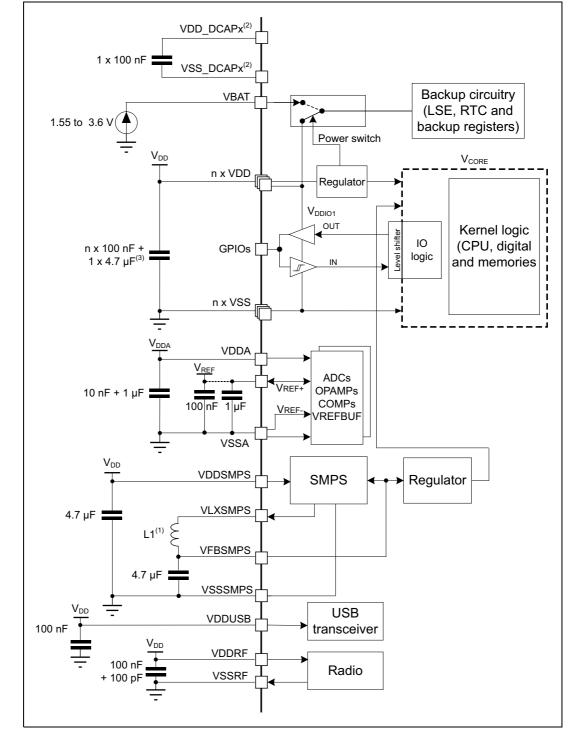


Figure 17. Power supply scheme (UFBGA129 and WLCSP100 packages)

- 1. The value of L1 depends upon the frequency, as indicated in *Table 6*.
- For UFBGA129 package VDD_DCAPx and VSS_DCAPx balls are connected to V_{DD} and V_{SS} internally, to simplify the 2-layer board layout and especially the ground plane below the BGA.
 V_{DD} power supply can be made with a single connection to the center of the BGA on the board bottom layer. The decoupling 100 nF capacitors are connected without cutting the board ground plane.
- 3. n x 100 nF only for WLCSP package.

4

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Caution:

Each power supply pair (V_{DD} / V_{SS} , V_{DDA} / V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown in *Figure 16*. These capacitors must be placed as close as possible to (or below) the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

6.1.7 Current consumption measurement

IDDSMPS

VDDSMPS

IDDNSB

VDDUSB

IDDVBAT

VDDA

VDDA

MS45416V1

Figure 18. Current consumption measurement scheme

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 20*, *Table 21* and *Table 22* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard, extended mission profiles are available on demand.

4

Symbol	Ratings	Min	Max	Unit
V _{DDX} - V _{SS}	External main supply voltage (including V_{DD} , V_{DDA} , V_{DDUSB} , V_{LCD} , V_{DDRF} , V_{DDSMPS} , V_{BAT} , V_{REF+})	-0.3	4.0	
(2)	Input voltage on FT_xxx pins	.,	$\begin{array}{c} \text{min (V}_{\text{DD}}, \text{V}_{\text{DDA}}, \text{V}_{\text{DDUSB}}, \text{V}_{\text{LCD}}, \\ \text{V}_{\text{DDRF}}, \text{V}_{\text{DDSMPS}}) + 4.0^{(3)(4)} \end{array}$	٧
V _{IN} ⁽²⁾	Input voltage on TT_xx pins	V _{SS} -0.3	4.0	
	Input voltage on any other pin		4.0	
ΔV _{DDx}	Variations between different V_{DDX} power pins of the same domain	-	50	mV
V _{SSx} -V _{SS}	Variations between all the different ground pins ⁽⁵⁾	-	50	1110
V _{REF+} - V _{DDA}	Allowed voltage difference for $V_{REF+} > V_{DDA}$	-	0.4	V

Table 20. Voltage characteristics⁽¹⁾

- All main power (V_{DD}, V_{DDRF}, V_{DDA}, V_{DDUSB}, V_{LCD}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
- 2. V_{IN} maximum must always be respected. Refer to Table 21 for the maximum allowed injected current values.
- 3. This formula has to be applied only on the power supplies related to the IO structure described in the pin definition table.
- 4. To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.
- 5. Include VREF- pin.

Table 21. Current characteristics

Symbol	Ratings	Max	Unit
∑IV _{DD}	Total current into sum of all V _{DD} power lines (source) ⁽¹⁾	130	
∑IV _{SS}	Total current out of sum of all V _{SS} ground lines (sink) ⁽¹⁾	130	
IV _{DD(PIN)}	Maximum current into each V _{DD} power pin (source) ⁽¹⁾	100	
IV _{SS(PIN)}	Maximum current out of each V _{SS} ground pin (sink) ⁽¹⁾	100	
	Output current sunk by any I/O and control pin except FT_f	20	
I _{IO(PIN)}	Output current sunk by any FT_f pin	20	mA
	Output current sourced by any I/O and control pin	20	IIIA
Σ1	Total output current sunk by sum of all I/Os and control pins ⁽²⁾	100	
$\sum I_{IO(PIN)}$	Total output current sourced by sum of all I/Os and control pins ⁽²⁾	100	
ı (3)	Injected current on FT_xxx, TT_xx, RST and B pins, except PB0 and PB1	-5 / +0 ⁽⁴⁾	
I _{INJ(PIN)} ⁽³⁾	Injected current on PB0 and PB1	-5/0	
Σ I _{INJ(PIN)}	Total injected current (sum of all I/Os and control pins) ⁽⁵⁾	25	

All main power (V_{DD}, V_{DDRF}, V_{DDA}, V_{DDUSB}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supplies, in the permitted range.

A negative injection is induced by V_{IN} < V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer also to *Table 20: Voltage characteristics* for the maximum allowed input voltage values.



This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count packages.

Positive injection (when V_{IN} > V_{DD}) is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.

5. When several inputs are submitted to a current injection, the maximum ∑|I_{INJ(PIN)}| is the absolute sum of the negative injected currents (instantaneous values).

Table 22. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-65 to +150	°C
T _J	Maximum junction temperature	130	C

6.3 Operating conditions

6.3.1 Summary of main performance

Table 23. Main performance at V_{DD} = 3.3 V

	Parameter		Test conditions	Тур	Unit
			VBAT (V _{BAT} = 1.8 V, V _{DD} = 0 V)	0.002	
			Shutdown (V _{DD} = 1.8 V)	0.013	
			Standby (V _{DD} = 1.8 V, 32 Kbytes RAM retention)	0.320	
			Stop2	1.85	
I _{CORE}	Core current consumption		Sleep (16 MHz)	740	
	Concumption		LP run (2 MHz)	320	
			Run (64 MHz)	5000	
			Radio RX ⁽¹⁾	4500	
			Radio TX 0 dBm output power ⁽¹⁾	5200	μΑ
		Bluetooth	Advertising with Stop $2^{(2)}$ (Tx = 0 dBm; Period 1.28 s; 31 bytes, 3 channels)	13	
	Peripheral	Low Energy	Advertising with Stop $2^{(2)}$ (Tx = 0 dBm, 6 bytes; period 10.24 s, 3 channels)	4	
I _{PERI}	current	LP timers	-	6	
	consumption I2C3 LPUART	I2C3	-	7.1	
		LPUART -			
		RTC	-	2.5	

^{1.} Power consumption including RF subsystem and digital processing.

6.3.2 General operating conditions

Table 24. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock frequency	-	0	64	
f _{PCLK1}	Internal APB1 clock frequency	-	0	64	MHz
f _{PCLK2}	Internal APB2 clock frequency	-	0	64	
V_{DD}	Standard operating voltage	-	1.71 ⁽¹⁾⁽²⁾	3.6	
		ADC or COMP used	1.62		
V _{DDA}	Analog supply voltage	VREFBUF used	2.4	3.6	V
DDA	3 11 7 2 4 3 2	ADC, COMP, VREFBUF not used ⁽³⁾	1.71		
V _{BAT}	Backup operating voltage	-	1.55	3.6	

^{2.} Power consumption averaged over 100 s, including Cortex-M4, RF subsystem, digital processing and Cortex-M0+.

Symbol	Parameter	Conditions	Min	Max	Unit
V_{FBSMPS}	SMPS Feedback voltage	-	1.4	3.6	
V _{DDRF}	Minimum RF voltage	-	1.71	3.6	
V	LICE cumply voltage	USB used	3.0	3.6	
V _{DDUSB}	USB supply voltage	USB not used	0	3.6	V
		TT_xx I/O	-0.3	V _{DD} + 0.3	
V _{IN}	I/O input voltage	All I/O except TT_xx	-0.3	min (min (V_{DD} , V_{DDA} , V_{DDUSB} , V_{LCD}) + 3.6 V, 5.5 V) ⁽⁴⁾⁽⁵⁾	
	Down discipation of	UFQFPN48	-	803	
В	Power dissipation at T _A = 85 °C for suffix 6	VFQFPN68	-	425	mW
P_{D}	or $T_A = 105 ^{\circ}\text{C}$ for suffix $7^{(6)}$	WLCSP100	-	558	IIIVV
	TA = 103 C for sum 7	UFBGA129	-	481	
	Ambient temperature for the	Maximum power dissipation	-40	85	
TA	suffix 6 version	Low-power dissipation ⁽⁷⁾	-4 0	105	
IA	Ambient temperature for the	Maximum power dissipation	-40	105	°C
	suffix 7 version	Low-power dissipation ⁽⁷⁾	-4 0	125	
TJ	Junction temperature range	Suffix 6 version	-40	105	
' J	Juniculon temperature range	Suffix 7 version	-4 0	125	

Table 24. General operating conditions (continued)

6.3.3 RF Bluetooth Low Energy characteristics

RF characteristics are given at 1 Mbps, unless otherwise specified.

Table 25. RF transmitter Bluetooth Low Energy characteristics

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
F _{op}	Frequency operating range	-	2402	1	2480	NAL I—
F _{xtal}	Crystal frequency	-	-	32	-	MHz
ΔF	Delta frequency	-	-	250	-	kHz



^{1.} When RESET is released functionality is guaranteed down to $V_{BOR0}\,Min.$

^{2.} When V_{DDmin} is lower then 1.95 V, the SMPS operation mode must be conditioned by enabling the BORH configuration to force SMPS bypass mode, or the SMPS must not be enabled.

^{3.} When not used, V_{DDA} must be connected to V_{DD} .

^{4.} This formula has to be applied only on the power supplies related to the IO structure described by the pin definition table. Maximum I/O input voltage is the smallest value between min $(V_{DD}, V_{DDA}, V_{DDUSB}, V_{LCD}) + 3.6 \text{ V}$ and 5.5V.

For operation with voltage higher than min (V_{DD}, V_{DDA}, V_{DDUSB}, V_{LCD}) + 0.3 V, the internal pull-up and pull-down resistors must be disabled.

If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_Jmax (see Section 7.5: Thermal characteristics).

In low-power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_Jmax (see Section 7.5: Thermal characteristics).

Table 25. RF transmitter Bluetooth Low Energy characteristics (continued)

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
Rgfsk	On Air data rate	-	-	1	2	Mbps
PLLres	RF channel spacing	-	-	2		MHz

Table 26. RF transmitter Bluetooth Low Energy characteristics (1 Mbps)⁽¹⁾

Symbol	Parameter		Test conditions	Min	Тур	Max	Unit
			SMPS Bypass ($V_{DD} > 1.71 \text{ V}$) or ON ($V_{FBSMPS} = 1.7 \text{ V}$ and $V_{DD} > 1.95 \text{ V}$) ⁽²⁾	-	6.0	-	
P _{rf}	Maximum output power		SMPS Bypass ($V_{DD} > 1.71 \text{ V}$) or ON ($V_{FBSMPS} = 1.4 \text{ V}$ and $V_{DD} > 1.95 \text{ V}$), Code $29^{(2)(3)}$	-	3.7	-	dBm
	0 dBm output power		-	-	0	-	
	Minimum output power		-	-	-20	-	
P _{band}	Output power variation over the band		Tx = 0 dBm - Typical	-0.5	-	0.4	dB
BW6dB	6 dB signal bandwidth		Tx = maximum output power	-	670	-	kHz
IBSE	In band spurious emission 2 MHz ≥ 3 MHz		Bluetooth® Low Energy: -20 dBm	-	-50	-	dBm
IDSE			Bluetooth® Low Energy: -30 dBm	-	-53	-	
f _d	Frequency drift	•	Bluetooth® Low Energy: ±50 kHz	-50	-	+50	kHz
maxdr	Maximum drift rate		Bluetooth [®] Low Energy: ±20 kHz / 50 µs	-20	-	+20	kHz/ 50 µs
fo	Frequency offset		Bluetooth [®] Low Energy: ±150 kHz	-150	-	+150	kHz
Δf1	Frequency deviation avera	age	Bluetooth [®] Low Energy: between 225 and 275 kHz	225	-	275	KΠZ
Δfa	Frequency deviation Δf2 (average) / Δf1 (average)		Bluetooth® Low Energy:> 0.80	0.80	-	-	-
OBSE ⁽⁴⁾	Out of band	< 1 GHz	-	-	-61	-	dBm
OBOL	spurious emission ≥ 1 GHz		-	-	-46	-	UDIII

Measured in conducted mode, based on reference design (see AN5165), using output power specific external RF filter and impedance matching networks to interface with a 50 Ω antenna.



V_{FBSMPS} and V_{DD} must be set to different voltage levels, depending upon the desired TX signal (see AN5246 *Usage of SMPS on STM32WB Series microcontrollers*, available on www.st.com).

^{3.} Code 29 means Tx Power (PA_Level) selection of 29 (25 being 0 dBm).

^{4.} Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).

Table 27. RF transmitter Bluetooth Low Energy characteristics (2 Mbps)⁽¹⁾

Symbol	Parameter		Test conditions	Min	Тур	Max	Unit
			SMPS Bypass ($V_{DD} > 1.71 \text{ V}$) or ON ($V_{FBSMPS} = 1.7 \text{ V}$ and $V_{DD} > 1.95 \text{ V}$) ⁽²⁾	-	6.0	-	
P _{rf}	Maximum output power		SMPS Bypass or ON (V_{FBSMPS} = 1.4 V and V_{DD} > 1.71 V), Code 29 ⁽²⁾⁽³⁾	ı	3.7	-	dBm
	0 dBm output power		-	ı	0	-	
	Minimum output power		-	ı	-20	-	
P _{band}	Output power variation over	er the band	Tx = 0 dBm - Typical	-0.5	-	0.4	dB
BW6dB	6 dB signal bandwidth		Tx = maximum output power	-	670	-	kHz
	4 MHz		Bluetooth® Low Energy: -20 dBm	-	-56	-	
IBSE	In band spurious emission 5 MHz ≥ 6 MHz	5 MHz	Bluetooth® Low Energy: -20 dBm	-	-57	-	dBm
		≥ 6 MHz	Bluetooth® Low Energy: -30 dBm		-58		
f _d	Frequency drift		Bluetooth® Low Energy: ±50 kHz	-50	-	50	kHz
maxdr	Maximum drift rate		Bluetooth [®] Low Energy: ±20 kHz / 50 µs	-20	-	20	kHz/ 50 µs
fo	Frequency offset		Bluetooth® Low Energy: ±150 kHz	-150	-	150	
Δf1	Frequency deviation avera	ge	Bluetooth [®] Low Energy: between 450 and 550 kHz	450	-	550	kHz
Δfa	Frequency deviation Δf2 (average) / Δf1 (average)		Bluetooth [®] Low Energy:> 0.80	0.80	-	-	-
OBSE ⁽⁴⁾	Out of band	< 1 GHz	-	-	-61	-	dBm
OBSE(*)	spurious emission	≥ 1 GHz	-	-	-46	-	ubiii

^{1.} Measured in conducted mode, based on reference design (see AN5165), using output power specific external RF filter and impedance matching networks to interface with a 50 Ω antenna.

V_{FBSMPS} and V_{DD} must be set to different voltage levels, depending upon the desired TX signal (see AN5246 Usage of SMPS on STM32WB Series microcontrollers, available on www.st.com).

^{3.} Code 29 means Tx Power (PA_Level) selection of 29 (25 being 0 dBm).

Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).

Table 28. RF receiver Bluetooth Low Energy characteristics (1 Mbps)

Symbol	Parameter	Test conditions	Тур	Unit
Prx_max	Maximum input signal	PER <30.8% Bluetooth [®] Low Energy: min -10 dBm	0	
Psens ⁽¹⁾	High sensitivity mode (SMPS Bypass)	PER <30.8%	-96	
Psens(1)	High sensitivity mode (SMPS ON)	Bluetooth [®] Low Energy: max -70 dBm	-95.5	dBm
Rssi _{maxrange}	RSSI maximum value	-	-7	
Rssi _{minrange}	RSSI minimum value	-	-94	
Rssi _{accu}	RSSI accuracy	-	2	
C/Ico	Co-channel rejection	Bluetooth [®] Low Energy: 21 dB	8	
		Adj ≥ 5 MHz Bluetooth [®] Low Energy: -27 dB	-53	
		Adj ≤ -5 MHz Bluetooth [®] Low Energy: -27 dB	-53	
	Adjacent channel interference	Adj = 4 MHz Bluetooth [®] Low Energy: -27 dB	-48	
		Adj = -4 MHz Bluetooth [®] Low Energy: -15 dB	-33	
C/I		Adj = 3 MHz Bluetooth [®] Low Energy: -27 dB	-46	dB
		Adj = 2 MHz Bluetooth [®] Low Energy: -17 dB	-39	
		Adj = -2 MHz Bluetooth [®] Low Energy: -15 dB	-35	
		Adj = 1 MHz Bluetooth [®] Low Energy: 15 dB	-2	
		Adj = -1 MHz Bluetooth [®] Low Energy: 15 dB	2	
C/Image	Image rejection (F _{image} = -3 MHz)	Bluetooth [®] Low Energy: -9 dB	-29	
		f2-f1 = 3 MHz Bluetooth [®] Low Energy: -50 dBm	-34	
P_IMD	Intermodulation	f2-f1 = 4 MHz Bluetooth [®] Low Energy: -50 dBm	-30	dBm
		f2-f1 = 5 MHz Bluetooth [®] Low Energy: -50 dBm	-32	

Table 28. RF receiver Bluetooth Low Energy characteristics (1 Mbps) (continued)

Symbol	Parameter	Test conditions	Тур	Unit
		30 to 2000 MHz Bluetooth [®] Low Energy: -30 dBm	-3	
	Out of band blocking	2003 to 2399 MHz Bluetooth® Low Energy: -35 dBm	-5	dBm
P_OBB		2484 to 2997 MHz Bluetooth [®] Low Energy: -35 dBm	-2	ивііі
		3 to 12.75 GHz Bluetooth [®] Low Energy: -30 dBm	7	

^{1.} With ideal TX.

Table 29. RF receiver Bluetooth Low Energy characteristics (2 Mbps)

	ı	· · · ·	·	
Symbol	Parameter	Parameter Test conditions		Unit
Prx_max	Maximum input signal	PER <30.8% Bluetooth [®] Low Energy: min -10 dBm	0	
_ (1)	High sensitivity mode (SMPS Bypass)	PER <30.8%	-93	
Psens ⁽¹⁾	High sensitivity mode (SMPS ON)	Bluetooth [®] Low Energy: max -70 dBm	-92.5	dBm
Rssi _{maxrange}	nge RSSI maximum value -		-7	
Rssi _{minrange}	RSSI minimum value	-	-94	
Rssi _{accu}	RSSI accuracy	-	2	
C/Ico	Co-channel rejection	Bluetooth® Low Energy spec: 21 dB	9	
		Adj ≥ 8MHz Bluetooth [®] Low Energy: -27 dB	-53	
		Adj ≤ -8 MHz Bluetooth [®] Low Energy: -27 dB	-50	
		Adj = 6 MHz Bluetooth [®] Low Energy: -27 dB	-49	
C/I	Adjacent channel interference	Adj = -6 MHz Bluetooth [®] Low Energy: -15 dB	-46	dB
		Adj = 4 MHz Bluetooth [®] Low Energy: -17 dB	-42	
		Adj = 2 MHz Bluetooth [®] Low Energy:15 dB	-3	
		Adj = -2 MHz Bluetooth [®] Low Energy:15 dB	-3	
C/Image	Image rejection (F _{image} = -4 MHz)	Bluetooth® Low Energy: -9 dB	-26	

Table 29. RF receiver Bluetooth Low Energy characteristics (2 Mbps) (continued)

Symbol	Parameter	Test conditions	Тур	Unit
		f2-f1 = 6 MHz Bluetooth [®] Low Energy: -50 dBm	-29	
P_IMD	Intermodulation	f2-f1 = 8 MHz Bluetooth [®] Low Energy: -50 dBm	-30	
		f2-f1 = 10 MHz Bluetooth [®] Low Energy: -50 dBm	-29	
	Out of band blocking	30 to 2000 MHz Bluetooth [®] Low Energy: -30 dBm	-3	dBm
D. ODD		2003 to 2399 MHz Bluetooth® Low Energy: -35 dBm	-9	
P_OBB		2484 to 2997 MHz Bluetooth [®] Low Energy: -35 dBm	-3	
		3 to 12.75 GHz Bluetooth [®] Low Energy: -30 dBm	4	

^{1.} With ideal TX.

Table 30. RF Bluetooth Low Energy power consumption for $V_{DD} = 3.3 V^{(1)}$

Symbol	Parameter		Unit
I _{txmax}	TX maximum output power consumption (SMPS Bypass)	12.7	
	TX maximum output power consumption (SMPS On, V _{FBSMPS} = 1.7 V)	7.8	
	TX 0 dBm output power consumption (SMPS Bypass)	8.8	mA
Itx0dbm	TX 0 dBm output power consumption (SMPS On, V _{FBSMPS} = 1.4 V)	5.2	111/-
	Rx consumption (SMPS Bypass)	7.9	
I _{rxlo}	Rx consumption (SMPS On, V _{FBSMPS} = 1.4 V)	4.5	

^{1.} Power consumption including RF subsystem and digital processing.

6.3.4 RF 802.15.4 characteristics

Table 31. RF transmitter 802.15.4 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
F _{op}	Frequency operating range	-	2405	-	2480	
F _{xtal}	Crystal frequency	-	-	32	-	MHz
ΔF	Delta frequency	-	-	5	-	
Roqpsk	On air data rate	-	-	250	-	kbps
PLLres	RF channel spacing	-	-	5	-	MHz

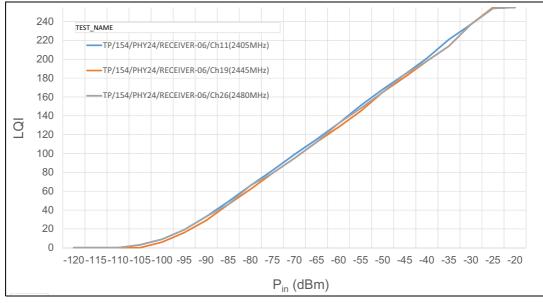
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Prf		SMPS Bypass or ON $(V_{FBSMPS} = 1.7 \text{ V and } V_{DD} > 1.95 \text{ V})$	-	5.7	-	
	Maximum output power ⁽¹⁾	SMPS Bypass $(V_{DD} > 1.71 \text{ V})$ or ON $(V_{FBSMPS} = 1.4 \text{ V})$ and $(V_{DD} > 1.95 \text{ V})$	-	3.7	-	dBm
	0 dBm output power	-	-	0	-	
	Minimum output power	-	-	-20	-	
Pband	Output power variation over the band	Tx = 0 dBm - Typical	-0.5	-	0.4	dB
EVMrms	EVM rms	Pmax	-	8	-	%
Txpd	Transmit power density	f - fc > 3.5 MHz	-	-35	-	dB

Table 31. RF transmitter 802.15.4 characteristics (continued)

Symbol Parameter Conditions Тур Unit Prx max Maximum input signal Min: -20 dBm and PER < 1% -10 Sensitivity (SMPS Bypass) -100 dBm Max: -85 dBm and PER < 1% Rsens Sensitivity (SMPS ON) -98 Adjacent channel rejection 35 C/adj _ dΒ C/alt Alternate channel rejection 46

Table 32. RF receiver 802.15.4 characteristics





^{1.} Measured in conducted mode, based on reference design (see AN5165), using output power specific external RF filter and impedance matching networks to interface with a 50 Ω antenna.

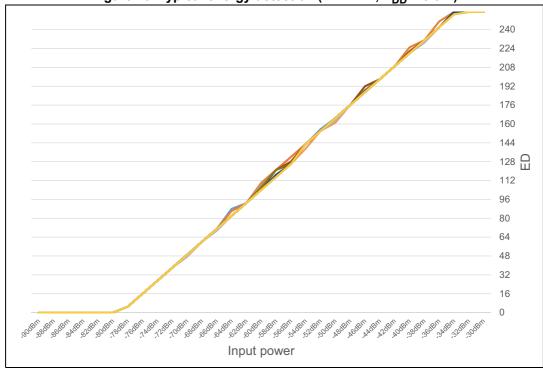


Figure 20. Typical energy detection (T = 27° C, V_{DD} = 3.3 V)

Table 33. RF 802.15.4 power consumption for $V_{DD} = 3.3 V^{(1)}$

Symbol	Parameter	Тур	Unit
	TX maximum output power consumption (SMPS Bypass)	11.7	
Itxmax	TX maximum output power consumption (SMPS On, V _{FBSMPS} = 1.7 V)	6.5	
_	TX 0 dBm output power consumption (SMPS Bypass)	9.1	mA
Itx0dbm	TX 0 dBm output power consumption (SMPS On, V _{FBSMPS} = 1.4 V)	4.5	IIIA
	Rx consumption (SMPS Bypass)	9.2	
Irxlo	Rx consumption (SMPS On)	4.5	

^{1.} Power consumption including RF subsystem and digital processing.

6.3.5 Operating conditions at power-up / power-down

The parameters given in *Table 34* are derived from tests performed under the ambient temperature condition summarized in *Table 24*.

	rance on operating	commissions at position at			
Symbol	Parameter	Conditions	Min	Max	Unit
+	V _{DD} rise time rate		-	∞	
t _{VDD}	V _{DD} fall time rate	-	10	∞	
	V _{DDA} rise time rate		0	∞	
t _{VDDA}	V _{DDA} fall time rate	-	10	∞	υο/\/
+	V _{DDUSB} rise time rate		0	∞	μs/V
t _{VDDUSB}	V _{DDUSB} fall time rate	-	10	∞	
+	V _{DDRF} rise time rate		-	∞	
t _{VDDRF}	V _{DDRF} fall time rate	-	-	8	

Table 34. Operating conditions at power-up / power-down

6.3.6 Embedded reset and power control block characteristics

The parameters given in *Table 35* are derived from tests performed under the ambient temperature conditions summarized in *Table 24: General operating conditions*.

Symbol	Parameter	Conditions ⁽¹⁾	Min	Тур	Max	Unit
t _{RSTTEMPO} ⁽²⁾	Reset temporization after BOR0 is detected	V _{DD} rising	-	250	400	μs
V _{BOR0} ⁽²⁾	Brown-out reset threshold 0	Rising edge	1.62	1.66	1.70	
VBOR0`	Brown-out reset timeshold 0	Falling edge	1.60	1.64	1.69	
V	Brown-out reset threshold 1	Rising edge	2.06	2.10	2.14	
V_{BOR1}	Brown-out reset timeshold 1	Falling edge	1.96	2.00	2.04	
V	Brown-out reset threshold 2	Rising edge	2.26	2.31	2.35	
V_{BOR2}	Brown-out reset timeshold 2	Falling edge	2.16	2.20	2.24	
V	Drawn out road threshold 2	Rising edge	2.56	2.61	2.66	
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.47	2.52	2.57	V
	Description and the school of	Rising edge	2.85	2.90	2.95	V
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.76	2.81	2.86	
V	Due average plant with a second start through old O	Rising edge	2.10	2.15	2.19	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	2.00	2.05	2.10	
.,	DVD three should 4	Rising edge	2.26	2.31	2.36	
V_{PVD1}	PVD threshold 1	Falling edge	2.15	2.20	2.25	
M	PVD2 PVD threshold 2	Rising edge	2.41	2.46	2.51	
V_{PVD2}	PVD (IIIesnoid 2	Falling edge	2.31	2.36	2.41	

Table 35. Embedded reset and power control block characteristics



Table 35. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions ⁽¹⁾	Min	Тур	Max	Unit
V	PVD threshold 3	Rising edge	2.56	2.61	2.66	
V _{PVD3}	F VD tilleshold 3	Falling edge	2.47	2.52	2.57	
V	PVD threshold 4	Rising edge	2.69	2.74	2.79	
V_{PVD4}	F VD tilleshold 4	Falling edge	2.59	2.64	2.69	V
V	PVD threshold 5	Rising edge	2.85	2.91	2.96	V
V_{PVD5}	FVD tilleshold 5	Falling edge	2.75	2.81	2.86	
V	PVD threshold 6	Rising edge	2.92	2.98	3.04	
V _{PVD6}	PVD tilleshold 6	Falling edge	2.84	2.90	2.96	
V	Lhustoresis voltage of DODLIO	Hysteresis in continuous mode	-	20	-	
V _{hyst_} BORH0	Hysteresis voltage of BORH0	Hysteresis in other mode	-	30	-	mV
V _{hyst_BOR_PVD}	Hysteresis voltage of BORH (except BORH0) and PVD	-	-	100	-	
I _{DD} (BOR_PVD) ⁽²⁾	BOR ⁽³⁾ (except BOR0) and PVD consumption from V _{DD}	-	-	1.1	1.6	μΑ
V _{PVM1}	V _{DDUSB} peripheral voltage monitoring	-	1.18	1.22	1.26	
V	V peripheral voltage monitoring	Rising edge	1.61	1.65	1.69	V
$V_{\rm PVM3}$	V _{DDA} peripheral voltage monitoring	Falling edge	1.6	1.64	1.68	
V _{hyst_PVM3}	PVM3 hysteresis	-	-	10	-	mV
V _{hyst_PVM1}	PVM1 hysteresis	-	-	10	-	IIIV
I _{DD} (PVM1) ⁽²⁾	PVM1 consumption from V _{DD}	-	-	0.2	-	^
I _{DD} (PVM3) ⁽²⁾	PVM3 consumption from V _{DD}		-	2	-	μA

^{1.} Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.

^{2.} Guaranteed by design.

^{3.} BOR0 is enabled in all modes (except shutdown) and its consumption is therefore included in the supply current characteristics tables.

6.3.7 Embedded voltage reference

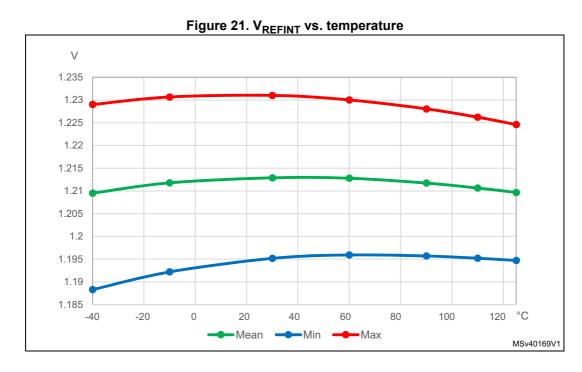
The parameters given in *Table 36* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Symbol Parameter Conditions Min Typ Max Unit -40 °C < T_A < +125 °C V V_{REFINT} Internal reference voltage 1.182 1.212 1.232 ADC sampling time when reading t_{S_vrefint} (1) 4(2) the internal reference voltage μs Start time of reference voltage 12⁽²⁾ 8 t_{start_vrefint} buffer when ADC is enabled V_{REFINT} buffer consumption from 20⁽²⁾ I_{DD}(V_{REFINTBUE}) 12.5 μΑ V_{DD} when converted by ADC Internal reference voltage spread 5 $7.5^{(2)}$ ΔV_{REFINT} $V_{DD} = 3 V$ mV over the temperature range 50⁽²⁾ -40 °C < T_A < +125 °C 30 Temperature coefficient ppm/°C T_{Coeff} 1000⁽²⁾ 1000 hours, T = 25 °C 300 A_{Coeff} Long term stability ppm $1200^{(2)}$ ppm/V Voltage coefficient $3.0 \text{ V} < \text{V}_{DD} < 3.6 \text{ V}$ 250 $V_{DDCoeff}$ 25 V_{REFINT DIV1} 1/4 reference voltage 24 % V_{REFINT DIV2} 1/2 reference voltage 49 50 51 V_{REFINT} 3/4 reference voltage 75 V_{REFINT DIV3} 74

Table 36. Embedded internal voltage reference

^{1.} The shortest sampling time can be determined in the application by multiple iterations.





6.3.8 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 18: Current consumption measurement scheme*.

Typical and maximum current consumption

The MCU is put under the following conditions:

- All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The flash memory access time is adjusted with the minimum wait states number, depending on the f_{HCLK} frequency (refer to the table "Number of wait states according to CPU clock (HCLK) frequency" available in the reference manual).
- When the peripherals are enabled f_{PCLK} = f_{HCLK}
- For flash memory and shared peripherals f_{PCLK} = f_{HCLK} = f_{HCLKS}

The parameters given in *Table 37* to *Table 48* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 37. Current consumption in Run and Low-power run modes, code with data processing running from flash, ART enable (Cache ON Prefetch OFF), V_{DD} = 3.3 V

		Conditi	ons			Ту	/p			Max ⁽¹⁾			
Symbol	Parameter	-	Voltage scaling	f _{HCLK}	25 °C	55 °C	85 °C	105 °C	25 °C	85 °C	105 °C	Unit	
			Dange 2	16 MHz	1.90	1.90	2.00	2.20	2.40	2.52	2.96		
		£ £	Range 2	2 MHz	0.960	0.985	1.10	1.25	1.25	1.57	2.05		
		f _{HCLK} = f _{HSl16} up to 16 MHz included,		64 MHz	8.15	8.25	8.40	8.60	9.30	9.60	10.02		
I (Dup)	Supply	f _{HCLK} = f _{HSE} = 32 MHz	Range 1	32 MHz	4.20	4.25	4.40	4.65	4.25	4.63	5.17		
I _{DD} (Run)	current in Run mode	HSI16 + PLL ON bove 32 MHz	above 32 MHz		16 MHz	2.25	2.30	2.40	2.65	2.65	2.91	3.52	
		All peripherals disabled		64 MHz	5.00	5.00	5.10	5.20	-	-	-	A	
		disabled	SMPS Range 1	32 MHz	3.15	3.15	3.25	3.35	-	-	-	mA	
				16 MHz	2.30	2.30	2.35	2.45	-	-	-		
	Cummbu			2 MHz	0.335	0.360	0.470	0.670	0.480	0.910	1.47		
l (LDDun)	Supply current in $f_{HCLK} = f_{MSI}$		1 MHz	0.170	0.210	0.325	0.520	0.270	0.730	1.31			
I _{DD} (LPRun)	Low-power run mode	All peripherals disabled		400 kHz	0.0815	0.120	0.230	0.425	0.140	0.590	1.18		
	Turrinode			100 kHz	0.0415	0.076	0.190	0.385	0.070	0.550	1.14		

^{1.} Guaranteed by characterization results, unless otherwise specified.





Table 38. Current consumption in Run and Low-power run modes, code with data processing running from SRAM1, V_{DD} = 3.3 V

		Conditi	ons			Ту	/p			Max ⁽¹⁾		
Symbol	Parameter	-	Voltage scaling	f _{HCLK}	25 °C	55 °C	85 °C	105 °C	25 °C	85 °C	105 °C	Unit
			Pango 2	16 MHz	2.00	2.05	2.15	2.30	2.57	3.04	3.64	
		£ £	Range 2	2 MHz	0.970	1.00	1.10	1.25	1.62	1.90	2.55	
		f _{HCLK} = f _{HSl16} up to 16 MHz included,		64 MHz	8.80	8.90	9.00	9.20	10.50	10.80	11.30	
L (Bun)	Supply	f _{HCLK} = f _{HSE} = 32 MHz	Range 1	32 MHz	4.50	4.55	4.70	4.90	4.63	4.89	5.62	
I _{DD} (Run)	current in Run mode	f _{HSI16} + PLL ON above 32 MHz		16 MHz	2.40	2.40	2.55	2.70	2.50	2.70	3.21	
		All peripherals disabled		64 MHz	5.25	5.30	5.35	5.45	-	-	-	A
		disabled	SMPS Range 1	32 MHz	3.25	3.25	3.35	3.45	-	-	-	mA
			i tanige i	16 MHz	2.35	2.35	2.40	2.45	-	-	-	
	O			2 MHz	0.265	0.285	0.385	0.550	0.440	0.940	1.620	
	Supply current in Low-power run mode Supply current in fHCLK = fMSI All peripherals disabled		1 MHz	0.135	0.170	0.270	0.430	0.290	0.760	1.480		
I _{DD} (LPRun)			400 kHz	0.066	0.097	0.195	0.360	0.200	0.670	1.380		
	run mode			100 kHz	0.031	0.0625	0.160	0.325	0.170	0.470	1.330	ļ

^{1.} Guaranteed by characterization results, unless otherwise specified.

Table 39. Typical current consumption in Run and Low-power run modes, with different codes running from flash, ART enable (Cache ON Prefetch OFF), V_{DD}= 3.3 V

		·	Conditio	ns	TYP		TYP			
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit		
			Z	Reduced code ⁽¹⁾	1.90		119			
		N	Range 2 f _{HCLK} = 16 MHz	Coremark	1.85		116			
		f _{HCLK} = f _{HSI16} up to 16 MHz included, f _{HSI16} + PLL ON above 32 MHz All peripherals disable	ange = 16	Dhrystone 2.1	1.85	mA	116	μΑ/MHz		
		32	ŽLK 🥷	Fibonacci	1.75		109			
		bove	r _	While(1)	1.60		100			
		S B	Z	Reduced code ⁽¹⁾	8.15		127			
		L O	Range 1 f _{HCLK} = 64 MHz	Coremark	8.00		125			
		+ B	ange = 64	Dhrystone 2.1	8.10	mA	127	μΑ/MHz		
		HSI16 Jisab	R SCLK	Fibonacci	7.60		119			
I (Dun)	Supply current in	ed, f _r	Ę.	While(1)	6.85		107			
I _{DD} (Run)	Run mode	Slude	On	Reduced code ⁽¹⁾	5.00		78			
		z inc peri	Range 1, SMPS On f _{HCLK} = 64 MHz	Coremark	4.95		77			
		¥ ₹	, SN = 64	Dhrystone 2.1	4.95	mA	77	μΑ/MHz		
		ö 16	ige 1	Fibonacci	4.75		74			
		up 1	Rar fr	While(1)	4.40		69			
		4SI16	On Z,	Reduced code ⁽¹⁾	4.07		64			
		ن ےب اا	MPS MH, Tx = Tx	Coremark	3.99		62			
		J Z	Range 1, SMPS On f _{HCLK} = 64 MHz, When RF Tx level = 0 dBm(²)	Dhrystone 2.1	4.04	mA	63	μΑ/MHz		
		ч-	ge , CLK , Whe	Fibonacci	3.79		59			
			Rar f _H	While(1)	3.42		53			
				Reduced code ⁽¹⁾	320		160			
			= f _{MSI} = 2 MHz	,		Coremark	350		175	
I _{DD} (LPRun)	Supply current in Low-power run	f _{HCLK} = f _{MS} All periphera		Dhrystone 2.1	350	μΑ	175	μΑ/MHz		
		L - France		Fibonacci	390		195			
				While(1)	225		113			

^{1.} Reduced code used for characterization results provided in *Table 37* and *Table 38*.

^{2.} Value computed. MCU consumption when RF TX and SMPS are ON.

Table 40. Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1, V_{DD} = 3.3 V

			Condition	ıs	TYP		TYP		
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit	
			Z	Reduced code ⁽¹⁾	2.00		125		
		N	Range 1, SMPS On	Coremark	1.75		109		
		MHz	Range 1, SMPS On	Dhrystone 2.1	1.95	mA	122	μΑ/MHz	
		32	Range 1, SMPS On	Fibonacci	1.85		116		
		роле	Range 1, SMPS On	While(1)	1.85		116		
		N a	Range 1, SMPS On	Reduced code ⁽¹⁾	8.80		138		
		TT C	⁻ ≥ ±	Coremark	7.50		117		
		+ P	ange = 64	Dhrystone 2.1	8.60	mA	134	μΑ/MHz	
		HSI16 Jisak	Fibonacci	7.90		123			
L (Bup)	Supply current in	ed, f _t	<u>४</u> While(1)		8.00		125		
I _{DD} (Run)	Run mode	dude	On	Reduced code ⁽¹⁾	5.25		82		
		lz ind peri	Range 1, SMPS On	APS F MH	Coremark	4.65		73	
		MH All	Range 1, SMPS On	Dhrystone 2.1	5.15	mA	80	μΑ/MHz	
		to 16	Range 1, SMPS On	Fibonacci	4.85		76		
		dn :	Range 1, SMPS On	While(1)	4.90		77		
		4SI16	Range 1, SMPS On Range 1, SMPS On Range 1 FHCLK = 64 MHz FHCLK =	Reduced code ⁽¹⁾	4.39		69		
		(= ا _ا	APS MH TX Bm(Coremark	3.74		58		
		$f_{\rm HCLK}$ = $f_{\rm HSI16}$ up to 16 MHz included, $f_{\rm HSI16}$ + PLL ON above 32 MHz All peripherals disable	1, SN = 64 = RN = 0 d	Dhrystone 2.1	4.29	mA	67	μΑ/MHz	
		+	CLK Whe	Fibonacci	3.94		62		
			Rar f _H le	While(1)	3.99		62		
				Reduced code ⁽¹⁾	255		128		
			_{MSI} = 2 MHz	Coremark	205		103		
I _{DD} (LPRun)	Supply current in Low-power run	f _{HCLK} = f _{MSI} = 2 MHz All peripherals disable	= f _{MSI} = 2 MHz pherals disable	Dhrystone 2.1	250	μΑ	125	μΑ/MHz	
		• •		Fibonacci	230		115		
				While(1)	220		110		

^{1.} Reduced code used for characterization results provided in Table 37 and Table 38.

^{2.} Value computed. MCU consumption when RF TX and SMPS are ON.

Table 41. Current consumption in Sleep and Low-power sleep modes, flash memory ON

		Con	ditions			T	ΥP			MAX ⁽¹⁾)	
Symbol	Parameter	-	Voltage scaling	f _{HCLK}	25 °C	55 °C	85 °C	105 °C	25 °C	85 °C	105 °C	Unit
		f _{HCLK} = f _{HSI16} up	Range 2	16 MHz	0.740	0.765	0.865	1.05	0.840	1.210	1.810	
		to 16 MHz included,		64 MHz	2.65	2.70	2.80	3.00	3.00	3.33	3.91	
	Supply	Supply $f_{HCLK} = f_{HSE}$ up to 32 MHz	Range 1	32 MHz	1.40	1.45	1.60	1.80	1.55	1.86	2.49	
I _{DD} (Sleep)	leep) current in sleep mode. 32 MHz			16 MHz	0.845	0.875	0.990	1.20	0.970	1.40	2.02	
	sleep mode. THSI16 + PLL O	above 32 MHz		64 MHz	2.60	2.60	2.65	2.75	-	-	-	
			SMPS Range 1	32 MHz	1.90	1.95	2.00	2.10	-	-	-	mA
		disabled		16 MHz	1.70	1.70	1.75	1.80	-	-	-	
	Cummbu	disabled		2 MHz	0.090	0.125	0.235	0.430	0.130	0.600	1.19	
I (I DCloop)	Supply current in low power	 f _{HCLK} = f _{MSI}		1 MHz	0.058	0.093	0.205	0.400	0.090	0.570	1.16	
IDD(LPSleep)	low-power	All peripherals disal	bled	400 kHz	0.044	0.0725	0.185	0.380	0.070	0.540	1.11	
	sleep mode			100 kHz	0.0315	0.0635	0.0175	0.370	0.055	0.530	1.13	

^{1.} Guaranteed by characterization results, unless otherwise specified.

Table 42. Current consumption in Low-power sleep modes, flash memory in Power down

		izi Gaironi G			P		,	, j		= '= '= '	
Symbol	Parameter	Condition	ons		T	/P			MAX ⁽¹⁾		Unit
Syllibol	Parameter	-	f _{HCLK}	25 °C	55 °C	85 °C	105 °C	25 °C	85 °C	105 °C	Offic
	Supply	f _{HCLK} = f _{MSI}	2 MHz	94.0	115	200	335	135	610	1201	
I_{DD}	current in	TICEN WISI	1 MHz	56.5	86.0	170	305	94.2	560	1171	μA
(LPSleep)	low-power	All peripherals	400 kHz	40.5	66.5	150	285	68.0	540	1129	μΛ
	sleep mode	disabled	100 kHz	27.5	57.5	140	275	54.6	539	1131	

^{1.} Guaranteed by characterization results, unless otherwise specified.





Table 43. Current consumption in Stop 2 mode

0	Danamatan	Conditions	;			1	ΥP				M	ΔΧ ⁽¹⁾		11!4
Symbol	Parameter	-	V_{DD}	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	85 °C	105 °C	Unit
		1.00	1.8 V	1.00	1.85	3.15	5.95	21.5	50.0	1.58	4.12	56.9	132.7	
		LCD disabled Bluetooth Low	2.4 V	1.10	1.85	3.20	6.00	22.0	51.0	-	-	-	-	
	Supply current	Energy disabled	3.0 V	1.10	1.85	3.25	6.10	22.0	52.0	1.60	4.17	57.9	135.6	
I_{DD}	in Stop 2		3.6 V	1.15	1.95	3.35	6.25	23.0	53.0	1.69	4.40	58.6	135.7	
(Stop 2)	mode, RTC disabled	LCD enabled ⁽²⁾	1.8 V	1.20	2.00	3.35	6.10	22.0	50.5	1.76	4.30	57.1	133.3	
	uisabieu	and clocked by LSI	2.4 V	1.20	2.00	3.40	6.20	22.0	51.0	-	-	-	-	
		Bluetooth Low	3.0 V	1.25	2.10	3.45	6.30	22.5	52.0	1.85	4.41	58.1	135.8	
		Energy disabled	3.6 V	1.30	2.15	3.60	6.55	23.0	53.5	1.97	4.66	59.4	136.6	
		DTO ded a	1.8 V	1.30	2.10	3.45	6.25	22.0	50.5	1.91	4.50	57.2	133.0	
		RTC clocked by LSI,	2.4 V	1.45	2.25	3.55	6.40	22.5	51.5	-	-	-	-	μA
		LCD disabled	3.0 V	1.50	2.30	3.70	6.55	22.5	52.5	2.11	4.64	58.3	136.1	μπ
	Supply current		3.6 V	1.75	2.50	3.95	6.85	23.5	53.5	2.26	5.12	59.7	136.9	
I _{DD}	in Stop 2	DT0 1 1	1.8 V	1.35	2.20	3.55	6.30	22.0	50.5	1.99	4.57	57.4	133.8	
(Stop 2	mode, RTC enabled,	RTC clocked by LSI,	2.4 V	1.50	2.35	3.65	6.50	22.5	51.5	-	-	-	-	
with	Bluetooth Low	LCD enabled ⁽²⁾	3.0 V	1.70	2.45	3.85	6.65	23.0	52.5	2.17	4.87	58.4	136.3	
RTC)	Energy		3.6 V	1.80	2.60	4.05	6.95	23.5	54.0	2.41	5.11	59.9	137.1	
	disabled	RTC clocked by	1.8 V	1.35	2.20	3.50	6.25	22.0	50.5	1.91	4.29	57.1	133.5	
		LSE quartz ⁽³⁾	2.4 V	1.45	2.25	3.65	6.40	22.5	51.5	-	-	-	-	
		in low drive	3.0 V	1.55	2.45	3.80	6.65	23.0	52.5	2.01	4.31	58.0	135.9	
		mode	3.6 V	1.70	2.55	4.05	6.95	23.5	54.0	2.16	4.40	81.6	137.0	

Table 43. Current consumption in Stop 2 mode (continued)

Cumbal	Downston	Conditions	3			1	ΥP				M	4X ⁽¹⁾		I I m ld
Symbol	Parameter	-	V_{DD}	0°C	25 °C	40 °C	55 °C	85 °C	105 °C	0°C	25 °C	85 °C	105 °C	Unit
		Wakeup clock is HSI16, voltage Range 2. See ⁽⁴⁾ .	3.0 V	-	389	-	-	-	-	-	-	-	-	
I _{DD} (wakeup from Stop 2)	Supply current during wakeup from Stop 2 mode	Wakeup clock is MSI = 32 MHz, voltage Range 1. See ⁽⁴⁾ .	3.0 V	-	320	-	-	-	-	-	-	-	-	μΑ
- (C)	bypass mode	Wakeup clock is MSI = 4 MHz, voltage Range 2. See ⁽⁴⁾ .	3.0 V	-	528	-	-	-	-	-	-	-	-	

^{1.} Guaranteed based on test during characterization, unless otherwise specified.

^{2.} LCD enabled with external voltage source. Consumption from VLCD excluded. Refer to LCD controller characteristics for I_{VLCD}

^{3.} Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

^{4.} Wakeup with code execution from flash memory. Average value given for a typical wakeup time as specified in *Table 51: Low-power mode wakeup timings*.



Table 44. Current consumption in Stop 1 mode

Comple al	Downwater	Conditions				Т	ΥP				M	IAX ⁽¹⁾		Unit
Symbol	Parameter	-	V_{DD}	0°C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	85 °C	105 °C	Unii
		Di atauti i	1.8 V	5.05	9.20	15.5	28.0	96.0	210	7.00	28.4	343.7	738.6	
		Bluetooth Low Energy disabled	2.4 V	5.10	9.25	15.5	28.5	96.5	215	-	1	1	-	
	Supply	LCD disabled	3.0 V	5.15	9.30	15.5	28.5	97.0	215	7.07	28.5	346.8	746.0	
I_{DD}	current in Stop 1 mode.		3.6 V	5.25	9.45	16.0	29.0	97.5	215	7.30	28.8	351.0	749.4	
(Stop 1)	RTC	Bluetooth Low	1.8 V	5.05	9.30	15.5	28.5	96.0	210	7.10	28.7	344.4	739.0	
	disabled	Energy disabled	2.4 V	5.10	9.35	16.0	28.5	96.5	215	ı	ı	1	-	
		LCD enabled ⁽²⁾ ,	3.0 V	5.20	9.65	16.0	28.5	97.0	215	7.26	29.6	345.0	747.0	
		clocked by LSI	3.6 V	5.55	9.85	16.0	29.0	98.5	215	7.62	29.8	349.0	750.8	
			1.8 V	5.30	9.35	16.0	28.5	96.5	215	7.30	29.5	343.7	739.2	
		RTC clocked by LSI	2.4 V	5.40	9.45	16.0	28.5	97.0	215	ı	ı	1	-	μΑ
		LCD disabled	3.0 V	5.70	9.55	16.5	29.0	98.5	220	7.69	29.7	347.2	746.1	μ, ,
	Supply current in		3.6 V	5.85	10.0	16.5	29.5	96.5	215	8.08	29.8	349.9	751.1	
I _{DD}	Stop 1 mode,		1.8 V	5.25	9.60	16.0	28.5	96.5	215	7.10	29.0	344.3	739.9	
(Stop 1	RTC	RTC clocked by LSI	2.4 V	5.30	9.75	16.0	29.0	97.0	215	-	-	-	-	
with	enabled,	LCD enabled ⁽²⁾	3.0 V	5.85	9.80	16.5	29.0	97.5	215	7.53	29.8	347.4	746.2	
RTC)	Bluetooth Low Energy		3.6 V	5.90	10.5	16.5	29.0	98.5	220	8.18	29.9	350.6	751.8	
	disabled	DTO de de de	1.8 V	5.35	9.55	16.0	28.5	96.5	215	6.00	28.7	343.9	738.7	
		RTC clocked by LSE quartz ⁽³⁾ in	2.4 V	5.40	9.70	16.0	29.0	96.5	215	-	-	-	-	
		Low drive mode	3.0 V	5.75	9.70	16.0	29.0	97.5	215	7.40	28.9	346.6	743.8	
			3.6 V	5.90	10.0	16.5	29.5	99.0	220	7.58	29.2	349.0	749.9	

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Table 44. Current consumption in Stop 1 mode (continued)

Symbol	Parameter	Conditions		ТҮР						MAX ⁽¹⁾				Unit
		-	V _{DD}	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	85 °C	105 °C	
I _{DD} (wakeup from Stop1)	current during wakeup from Stop 1 bypass mode	Wakeup clock HSI16, voltage Range 2. See ⁽⁴⁾ .	3.0 V	-	129	-	-	-	-	-	-	-	-	μА
		Wakeup clock MSI = 32 MHz, voltage Range 1. See ⁽⁴⁾ .	3.0 V	-	124	-	-	-	-	-	-	-	-	
		Wakeup clock MSI = 4 MHz, voltage Range 2. See ⁽⁴⁾ .	3.0 V	-	207	-	-	-	-	-	-	-	-	

- 1. Guaranteed based on test during characterization, unless otherwise specified.
- 2. LCD enabled with external voltage source. Consumption from VLCD excluded. Refer to LCD controller characteristics for I_{VLCD}
- 3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
- 4. Wakeup with code execution from flash. Average value given for a typical wakeup time as specified in *Table 51: Low-power mode wakeup timings*.



Table 45. Current consumption in Stop 0 mode

		I			. 00.10	umpu		top c	mouo			· v(1)		
Symbol	Parameter	Conditions	•			1	ΥP				MA	4X ⁽¹⁾		Unit
Cymbol	i arameter	-	V_{DD}	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	85 °C	105 °C	
	Supply current in Stop 0 mode,		1.8 V	95.5	100	110	120	195	315	110.0	114.2	458.1	874.8	
	RTC disabled, Bluetooth Low		2.4 V	97.5	105	110	125	195	315	-	-	-	-	
	Energy	_	3.0 V	98.5	105	110	125	195	320	117.3	134.3	461.8	880.0	
	disabled, LCD disabled		3.6 V	100	105	115	125	200	320	165.0	135.7	494.0	884.1	
I _{DD} (Stop 0)	Supply current during wakeup from Stop 0 Bypass mode	Wakeup clock HSI16, voltage Range 2. See ⁽²⁾ .	3.0 V	-	331	-	-	-	-	-	-	-	-	μΑ
		Wakeup clock is MSI = 32 MHz, voltage Range 1. See ⁽²⁾ .	3.0 V	-	349	-	-	-	-	-	-	-	-	
		Wakeup clock is MSI = 4 MHz, voltage Range 2. See ⁽²⁾ .	3.0 V	-	196	-	-	-	-	-	-	-	-	

^{1.} Guaranteed by characterization results, unless otherwise specified.

^{2.} Wakeup with code execution from flash memory. Average value given for a typical wakeup time as specified in *Table 51: Low-power mode wakeup timings*.

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Table 46. Current consumption in Standby mode

Symbol	Parameter	Conditions				•	ΥP				MA	X ⁽¹⁾		Unit
Symbol	Parameter	-	V_{DD}	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	85 °C	105 °C	Oilit
		Bluetooth Low	1.8 V	0.270	0.320	0.515	0.920	3.45	8.20	0.300	0.828	7.850	19.300	
	Supply current	Energy disabled	2.4 V	0.270	0.350	0.540	0.955	3.50	8.80	-	-	-	-	
	in Standby	No independent watchdog	3.0 V	0.270	0.370	0.575	1.00	3.85	9.50	0.380	0.945	8.505	21.200	
I _{DD}	mode (backup registers and	watchdog	3.6 V	0.300	0.410	0.645	1.15	4.20	10.50	0.400	1.040	8.980	22.400	
(Standby)	SRAM2a	Bluetooth Low	1.8 V	0.265	0.525	0.710	1.10	3.90	8.40	0.520	1.095	8.041	19.500	
	retained),	Energy disabled With	2.4 V	0.280	0.595	0.790	1.20	4.00	9.05	-	-	-	-	
	RTC disabled	independent	3.0 V	0.290	0.670	0.855	1.35	4.15	9.80	0.730	1.253	8.774	21.400	
		watchdog	3.6 V	0.295	0.770	0.990	1.50	4.60	11.00	0.851	1.356	9.360	22.840	
		RTC clocked by	1.8 V	0.500	0.600	0.780	1.20	3.70	8.45	0.680	1.165	8.143	19.660	
		LSI, no	2.4 V	0.630	0.705	0.910	1.30	3.80	9.10	-	-	-	-	μA
	Supply current	independent	3.0 V	0.725	0.825	1.050	1.50	3.95	9.90	0.930	1.463	8.977	21.440	μΑ
	in Standby	watchdog	3.6 V	0.860	0.970	1.200	1.70	4.25	11.00	1.050	1.628	9.634	23.080	
	mode (backup registers and	RTC clocked by	1.8 V	0.565	0.655	0.830	1.25	3.75	8.55	0.734	1.196	8.187	19.710	
l _{DD}	SRAM2a	LSI, with	2.4 V	0.635	0.790	0.975	1.40	4.10	9.20	-	-	-	-	
(Standby with RTC)	retained),	independent	3.0 V	0.725	0.915	1.100	1.55	4.50	10.00	1.028	1.573	9.072	21.810	
,	RTC enabled Bluetooth Low	watchdog	3.6 V	0.870	1.050	1.300	1.80	4.90	11.00	1.144	1.723	9.730	23.200	
	Energy		1.8 V	0.525	0.625	0.840	1.25	3.75	8.60	0.600	1.061	8.029	19.610	
	disabled	RTC clocked by LSE quartz (2) in	2.4 V	0.665	0.755	0.960	1.35	4.05	9.25	-	-	-	-	
		low drive mode	3.0 V	0.775	0.880	1.100	1.55	4.40	10.00	0.600	1.100	8.719	21.570	
			3.6 V	0.935	1.050	1.300	1.80	5.00	11.00	0.750	1.171	9.460	23.030	



Table 46. Current consumption in Standby mode (continued)

		Tubic ici cui			•									
Symbol	Parameter	Conditions	5			Т	ΥP	•			MA	X ⁽¹⁾	•	Unit
Symbol	Farameter	-	V_{DD}	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	85 °C	105 °C	• · · · ·
	Supply current to be		1.8 V	0.160	0.210	0.380	0.660	2.30	5.15	1	-	-	-	
I _{DD}	subtracted in	_	2.4 V	0.165	0.245	0.375	0.650	2.15	5.20	ı	-	-	-	μA
(SRAM2a) ⁽³⁾	mode when SRAM2a is		3.0 V	0.155	0.250	0.385	0.630	2.25	5.20	ı	-	-	-	μ, τ
	not retained		3.6 V	0.155	0.235	0.375	0.670	2.20	5.20	ı	-	-	-	
I _{DD} (wakeup from Standby)	Supply current during wakeup from Standby mode	Wakeup clock is HSI16. See ⁽⁴⁾ . SMPS OFF	3.0 V	-	1.73	-	-	-	-	-	-	-	-	mA

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
- 3. The supply current in Standby with SRAM2a mode is: $I_{DD}(Standby) + I_{DD}(SRAM2a)$. The supply current in Standby with RTC with SRAM2a mode is: $I_{DD}(Standby + RTC) + I_{DD}(SRAM2a)$.
- 4. Wakeup with code execution from flash memory. Average value given for a typical wakeup time as specified in Table 51.

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Table 47. Current consump	tion in	Shutdown	mode
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					onoun	-								
Comple ed	Danamatan	Condition	s			Т	ΥP				MA	AX ⁽¹⁾		l l m li
Symbol	Parameter	-	V_{DD}	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	85 °C	105 °C	Unit
	Supply current in		1.8 V	0.039	0.013	0.030	0.100	0.635	1.950	-	-	2.099	6.200	
I _{DD}	Shutdown mode (backup		2.4 V	0.059	0.014	0.055	0.120	0.785	2.350	-	-	-	-	
(Shutdown) regi	registers retained) RTC		3.0 V	0.064	0.037	0.070	0.180	1.000	2.900	-	0.185	2.670	7.490	
	disabled		3.6 V	0.071	0.093	0.140	0.280	1.300	3.700	-	0.247	3.120	8.450	
	Supply current in		1.8 V	0.320	0.315	0.355	0.420	0.985	2.300	-	0.572	2.702	6.180	μA
I _{DD}	Shutdown mode (backup		2.4 V	0.425	0.405	0.460	0.540	1.200	2.800	-	-	-	-	
with RTC)	registers retained) RTC	quartz ⁽²⁾ in low drive mode	3.0 V	0.535	0.535	0.595	0.700	1.500	3.450	-	0.664	2.990	7.800	
	enabled		3.6 V	0.695	0.720	0.790	0.940	2.000	4.350	-	0.790	3.730	9.140	

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

Table 48. Current consumption in VBAT mode

Symbol	Parameter	Condition	Conditions			٦	ГҮР			MAX ⁽¹⁾						Unit
Oymboi	i arameter	-	V_{BAT}	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	Oille
			1.8 V	1.00	2.00	4.00	10.0	52.0	145	-	-	-	-	-	-	
		RTC disabled	2.4 V	1.00	2.00	5.00	12.0	60.0	165	-	-	-	-	-	-	
	Backup	KTC disabled	3.0 V	2.00	4.00	7.00	16.0	75.0	225	-	-	-	-	-	-	
I _{DD} (VBAT)	domain		3.6 V	7.00	15.0	23.0	42.0	170	450	-	-	-	-	-	-	nA
IDD(APVI)	supply	RTC enabled	1.8 V	295	305	315	325	380	480	-	-	-	-	-	-	IIA
	current	and clocked	2.4 V	385	395	400	415	475	595	-	-	-	-	-	-	
		by LSE quartz ⁽²⁾	3.0 V	495	505	515	530	600	765	-	-	-	-	-	-	
		quartz	3.6 V	630	645	660	685	830	1150	-	-	-	-	-	-	

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.





Table 49. Current under Reset condition

Symbol	Conditions			TY	/P					MA	X ⁽¹⁾			Unit
Symbol	Conditions	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	0 °C	25 °C	40 °C	55 °C	85 °C	105 °C	Oilit
	1.8 V	-	410	-	-	-	-	-	-	-	-	-	-	
1 .	2.4 V	-	-	-	-	-	-	-	-	-	-	-	-	μA
IDD(RST)	3.0 V	-	550	-	-	-	-	-	750	-	-	-	-	μΛ
	3.6 V	-	750	-	-	-	-	-	-	-	-	-	-	

^{1.} Guaranteed by characterization results, unless otherwise specified.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 72: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution:

Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 50: Peripheral current consumption*, the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

- I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load
- V_{DD} is the I/O supply voltage
- f_{SW} is the I/O switching frequency
- C is the total capacitance seen by the I/O pin: C = C_{IO}+ C_{EXT}
- C_{IO} is the I/O pin capacitance
- C_{EXT} is the PCB board capacitance plus any connected external device pin capacitance.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

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On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 50*. The MCU is placed under the following conditions:

- All I/O pins are in Analog mode
- The given value is calculated by measuring the difference of the current consumptions:
 - when the peripheral is clocked on
 - when the peripheral is clocked off
- Ambient operating temperature and supply voltage conditions summarized in Table 20: Voltage characteristics
- The power consumption of the digital part of the on-chip peripherals is given in *Table 50*. The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

Table 50. Peripheral current consumption

	Peripheral	Range 1	Range 2	Low-power run and sleep	Unit
	Bus matrix ⁽¹⁾	2.40	2.00	1.80	
	TSC	1.25	1.05	1.05	
	CRC	0.465	0.375	0.380	
AHB1	DMA1	1.90	1.55	1.80	
	DMA2	2.00	1.65	1.80	
	DMAMUX	4.15	3.40	4.45	
	All AHB1 peripherals	12.0	10.0	11.5	
	AES1	4.00	3.30	3.90	
AHB2 ⁽²⁾	ADC1 independent clock domain	2.55	2.10	2.10	
AUDZ.	ADC1 clock domain	2.25	1.90	1.90	μΑ/MHz
	All AHB2 peripherals	7.45	6.20	6.60	
AHB3	QSPI	7.60	6.25	7.10	
	TRNG independent clock domain	3.80	N/A	N/A	
	TRNG clock domain	2.00	N/A	N/A	
	SRAM2	1.70	1.35	1.35	
AHB Shared	FLASH	8.35	6.90	8.45	
	AES2	6.95	5.75	7.00	
	PKA	4.40	3.65	4.25	
	All AHB shared peripherals	17.5	14.5	16.0	



Table 50. Peripheral current consumption (continued)

	Peripheral	Range 1	Range 2	Low-power run and sleep	Unit
	RTCA	1.10	0.88	1.25	
	CRS	0.24	0.20	0.20	
	USB FS independent clock domain	3.20	N/A	N/A	
	USB FS clock domain	2.05	N/A	N/A	
	I2C1 independent clock domain	2.50	4.40	4.40	
	I2C1 clock domain	4.80	4.00	5.50	
	I2C3 independent clock domain	2.10	3.50	3.55	
	I2C3 clock domain	3.70	3.10	3.55	
	LCD	1.35	1.10	2.10	
APB1	SPI2	1.65	1.40	2.25	
	LPTIM1 independent clock domain	2.10	3.40	3.00	
	LPTIM1 clock domain	3.60	3.00	3.80	
	TIM2	5.65	4.70	4.90	
	LPUART1 independent clock domain	2.70	4.15	3.85	
	LPUART1 clock domain	4.45	3.70	5.25	μΑ/MHz
	LPTIM2 clock domain	3.95	3.25	4.50	μΑνινιπΖ
	LPTIM2 independent clock domain	2.20	3.70	3.80	
	WWDG	0.335	0.285	0.965	
	All APB1 peripherals	27.0	22.5	25.5	
	AHB to APB2 ⁽³⁾	1.10	0.885	1.35	
	TIM1	8.20	6.80	7.25	
	TIM17	2.85	2.40	2.40	
	TIM16	2.75	2.30	2.55	
APB2	USART1 independent clock domain	4.40	7.80	7.00	
APD2	USART1 clock domain	8.80	7.30	7.75	
	SPI1	1.75	1.45	1.45	
	SAI1 independent clock domain	2.50	1.50	3.50	
	SAI1 clock domain	2.40	N/A	N/A	
	All APB2 on	28.0	23.0	25.5	
	ALL	97.5	80.5	90.0	

^{1.} The BusMatrix is automatically active when at least one master is ON (CPU, DMA).

^{2.} GPIOs consumption during read and write accesses.

^{3.} The AHB to APB2 bridge is automatically active when at least one peripheral is ON on the APB2.

6.3.9 Wakeup time from Low-power modes and voltage scaling transition times

The wakeup times given in *Table 51* are the latency between the event and the execution of the first user instruction.

The device goes in Low-power mode after the WFE (Wait For Event) instruction.

Table 51. Low-power mode wakeup timings⁽¹⁾

Symbol	Parameter		Conditions	Тур	Max	Unit
t _{WUSLEEP}	Wakeup time from Sleep mode to Run mode		-	9	10	No. of
t _{WULPSLEEP}	Wakeup time from Low-power sleep mode to Low-power run mode		vith memory in power-down during mode (FPDS = 1 in PWR_CR1) SI = 2 MHz	9	10	CPU cycles
	Make up time from	Range 1	Wakeup clock MSI = 32 MHz	2.38	2.96	
	Wake up time from Stop 0 mode	Range	Wakeup clock HSI16 = 16 MHz	1.69	2.00	
	to Run mode in flash memory	Range 2	Wakeup clock HSI16 = 16 MHz	1.70	2.01	
4	memory	Range 2	Wakeup clock MSI = 4 MHz	7.43	8.59	
t _{WUSTOP0}		Range 1	Wakeup clock MSI = 32 MHz	2.63	3.00	
	Wake up time from Stop 0 mode	Range	Wakeup clock HSI16 = 16 MHz	1.80	2.00	
	to Run mode in SRAM1	Dange 2	Wakeup clock HSI16 = 16 MHz	1.82	2.02	
		Range 2	Wakeup clock MSI = 4 MHz	7.58	8.70	
	Make up time from	Dange 1	Wakeup clock MSI = 32 MHz	4.67	5.56	
	Wake up time from Stop 1 mode	Range 1	Wakeup clock HSI16 = 16 MHz	5.09	6.03	
	to Run in flash memory SMPS bypassed	Dance 2	Wakeup clock HSI16 = 16 MHz	5.08	6.00	
	SWF3 bypassed	Range 2	Wakeup clock MSI = 4 MHz	8.36	9.28	μs
	\\/	Dange 1	Wakeup clock MSI = 32 MHz	4.88	5.55	
	Wake up time from Stop 1 mode	Range 1	Wakeup clock HSI16 = 16 MHz	5.29	5.95	
+	to Run in SRAM1	Dance 2	Wakeup clock HSI16 = 16 MHz	5.28	5.96	
t _{WUSTOP1}	SMPS bypassed	Range 2	Wakeup clock MSI = 4 MHz	8.49	9.30	
	Wake up time from Stop 1 mode to Low-power run mode in flash memory	Regulator in Low-power	Wakeup clock MSI = 4 MHz	7.96	9.59	
	Wake up time from Stop 1 mode to Low-power run mode in SRAM1	mode (LPR = 1 in PWR_CR1)	Wakeup Gock MiSI - 4 MITZ	8.00	9.47	

Parameter Conditions Unit **Symbol** Тур Max Wakeup clock MSI = 32 MHz 5.27 6.07 Wake up time from Range 1 Stop 2 mode Wakeup clock HSI16 = 16 MHz 5.71 6.52 to Run mode in flash Wakeup clock HSI16 = 16 MHz 5.72 6.52 memory Range 2 SMPS bypassed Wakeup clock MSI = 4 MHz 9.10 9.93 μs twustop2 Wakeup clock MSI = 32 MHz 5.20 5.94 Range 1 Wake up time from Wakeup clock HSI16 = 16 MHz 5.64 6.42 Stop 2 mode to Run mode in SRAM1 Wakeup clock HSI16 = 16 MHz 5.64 6.43 SMPS bypassed Range 2 Wakeup clock MSI = 4 MHz 9.05 9.85 Wakeup time from Standby mode Range 1 Wakeup clock HSI16 = 16 MHz 51.0 58.1 μs t_{WUSTBY} to Run mode

Table 51. Low-power mode wakeup timings⁽¹⁾ (continued)

SMPS Bypassed

Table 52. Regulator modes transition times⁽¹⁾

Symbol	Parameter	Conditions	Тур	Max	Unit
t _{WULPRUN}	Wakeup time from Low-power run mode to Run mode ⁽²⁾	Code run with MSI 2 MHz	15.33	16.30	
t _{VOST}	Regulator transition time from Range 2 to Range 1 or Range 1 to Range 2 ⁽³⁾	Code run with HSI16	21.4	28.9	μs

- 1. Guaranteed by characterization results (V_{DD} = 3 V, T = 25 °C).
- 2. Time until REGLPF flag is cleared in PWR_SR2.
- 3. Time until VOSF flag is cleared in PWR_SR2.

Table 53. Wakeup time using USART/LPUART⁽¹⁾

Symbol	Parameter	Conditions	Тур	Max	Unit
twuusart	Wakeup time needed to calculate the maximum USART/LPUART baud rate allowing to wakeup from	Stop mode 0	-	1.7	
twulpuart	Stop modes when USART/LPUART clock source is HSI16	Stop mode 1/2	-	8.5	μs

^{1.} Guaranteed by design.

^{1.} Guaranteed by characterization results (V_{DD} = 3 V, .T = 25 °C).

6.3.10 External clock source characteristics

High-speed external user clock generated from an external source

The high-speed external (HSE) clock is supplied with a 32 MHz crystal oscillator or a sine or a square wave.

The devices include internal programmable capacitances that can be used to tune the crystal frequency in order to compensate the PCB parasitic one.

The characteristics in *Table 54* and *Table 55* are measured over recommended operating conditions, unless otherwise specified. Typical values are referred to T_A = 25 °C and V_{DD} = 3.0 V.

Table 54. HSE crystal requirements⁽¹⁾ (2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{NOM}	Oscillator frequency	-	-	32	-	MHz
f _{TOL}	Frequency tolerance	Includes initial accuracy, stability over temperature, aging and frequency pulling due to incorrect load capacitance.	-	-	(3)	ppm
C _L	Load capacitance	-	6	-	8	pF
ESR	Equivalent series resistance	-	-	-	100	Ω

^{1. 32} MHz XTAL is validated for the specific reference (NX2016SA).

Table 55. HSE clock source requirements⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
f _{HSE_ext}	User external clock source frequency	-	-	32	-	MHz	
f _{TOL}	Frequency tolerance	Includes initial accuracy, stability over temperature and aging.	-	-	(2)	ppm	
V _{HSE}	Clock input voltage limits	Sine or square wave, AC-coupled ⁽³⁾		-	1.6	V _{PP}	
DuCy(HSE)	Duty cycle	-	45	50	55	%	
t _r , t _f	Rise and fall times	10% - 90% square wave	-	-	15 * V _{PP}	ns	
		Offset = 10 kHz	-	-	-127		
φ _{n(HSE)} Phase noise for 32 MHz		Offset = 100 kHz	-	-	-135	dBc/Hz	
		Offset = 1 MHz	-	-	-138		

^{1.} Guaranteed by design.



^{2.} For information about the HSE crystal refer to AN5165 "Development of RF hardware using STM32WB microcontrollers", available on www.st.com.

^{3.} Refer to the standard specification: 50 ppm for Bluetooth Low Energy, 40 ppm for 802.15.4 and when both Bluetooth Low Energy and 802.15.4 are used.

Refer to the standard specification: 50 ppm for Bluetooth Low Energy, 40 ppm for 802.15.4 and when both Bluetooth Low Energy and 802.15.4 are used.

^{3.} Only AC coupled is supported (capacitor 470 pF to 100 nF).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{SUA(HSE)}	Startup time for 80% amplitude stabilization	V _{DDRF} stabilized, XOTUNE=000000,	ı	1000	ı	116
t _{SUR(HSE)}	Startup time for XOREADY signal	-40 to +125 °C range	-	250	-	μs
I _{DDRF(HSE)}	HSE current consumption ⁽¹⁾	HSEGMC=000, XOTUNE=000000	-	50	-	μΑ
$XOT_{g(HSE)}$	XOTUNE granularity		-	1	5	nnm
$XOT_{fp(HSE)}$	XOTUNE frequency pulling	Capacitor hank	±20	±40	-	ppm
XOT _{nb(HSE)}	XOTUNE number of tuning bits	Capacitor bank	-	6	-	bit
XOT _{st(HSE)}	XOTUNE setting time		-	-	0.1	ms

Table 56. HSE oscillator characteristics

Note: For information about oscillator trimming refer to AN5165, available on www.st.com.

Low-speed external user clock generated from an external source

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal resonator oscillator. The information provided in this section is based on design simulation results obtained with typical external components specified in *Table 57*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins to minimize output distortion and startup stabilization time.

Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 57. Low-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DD(LSE)}		LSEDRV[1:0] = 00 Low drive capability	-	250	1	Unit nA μΑ/V
	LSE ourrent consumption	LSEDRV[1:0] = 01 Medium low drive capability	-	315	1	nΛ
	LSE current consumption	LSEDRV[1:0] = 10 Medium high drive capability	-	500	1	IIA
		LSEDRV[1:0] = 11 High drive capability	-	630	1	
		LSEDRV[1:0] = 00 Low drive capability	-	-	0.50	
0	Maximum aritical anyatal a	LSEDRV[1:0] = 01 Medium low drive capability	-	-	0.75	۸ ۸ /
G _{mcritmax}	Maximum critical crystal g _m	LSEDRV[1:0] = 10 Medium high drive capability	-	-	1.70	μΑνν
		LSEDRV[1:0] = 11 High drive capability	-	-	2.70	
t _{SU(LSE)} ⁽²⁾	Startup time	V _{DD} stabilized	-	2	-	S



^{1.} Current consumption in standalone mode. The current consumption at device level is 350 µA in design simulation.

- 1. Guaranteed by design.
- t_{SU(LSE)} is the startup time measured from the moment it is enabled (by software) until a stable 32 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal refer to application note AN2867 "Oscillator design guide for STM8S, STM8A and STM32 microcontrollers" available from www.st.com.

Resonator with integrated capacitors

CL1

OSC32_IN

Drive programmable amplifier

OSC32_OUT

MS30253V2

Figure 22. Typical application with a 32.768 kHz crystal

Note:

No external resistors are required between OSC32_IN and OSC32_OUT, and it is forbidden to add one.

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics detailed in *Section 6.3.17*. The recommend clock input waveform is shown in *Figure 23*.

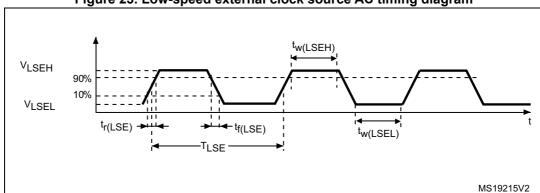


Figure 23. Low-speed external clock source AC timing diagram

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
f _{LSE_ext}	User external clock source frequency	-	21.2	32.768	44.4	kHz	
V _{LSEH}	OSC32_IN input pin high level voltage	-	0.7 V _{DDx}	-	V_{DDx}	V	
V _{LSEL}	OSC32_IN input pin low level voltage	-	V _{SS}	-	0.3 V _{DDx}	V	
t _{w(LSEH)}	OSC32_IN high or low time	-	250	-	-	ns	
f _{tolLSE}	Frequency tolerance	Includes initial accuracy, stability over temperature, aging and frequency pulling	-500	-	+500	ppm	

Table 58. Low-speed external user clock characteristics⁽¹⁾ – Bypass mode

6.3.11 Internal clock source characteristics

The parameters given in *Table 59* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*. The provided curves are characterization results, not tested in production.

High-speed internal (HSI16) RC oscillator

Table 59. HSI16 oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI16}	HSI16 frequency	V _{DD} =3.0 V, T _A =30 °C	15.88	-	16.08	MHz
TRIM	HSI16 user trimming step	Trimming code is not a multiple of 64	0.2	0.3	0.4	
	Tion of the miniming step	Trimming code is a multiple of 64	-4	-6	-8	
DuCy(HSI16) ⁽²⁾	Duty cycle	-	45	-	55	%
۸ (۱۹۵۱)	HSI16 oscillator frequency drift over	T _A = 0 to 85 °C	-1	-	1	
$\Delta_{Temp}(HSI16)$	temperature	T _A = -40 to 125 °C	-2	-	1.5	
Δ _{VDD} (HSI16)	HSI16 oscillator frequency drift over V _{DD}	V _{DD} =1.62 V to 3.6 V	-0.1	-	0.05	
t _{su} (HSI16) ⁽²⁾	HSI16 oscillator start-up time	-	-	0.8	1.2	116
t _{stab} (HSI16) ⁽²⁾	HSI16 oscillator stabilization time	-	-	3	5	μs
I _{DD} (HSI16) ⁽²⁾	HSI16 oscillator power consumption	-	-	155	190	μΑ

^{1.} Guaranteed by characterization results.

^{1.} Guaranteed by design.

^{2.} Guaranteed by design.

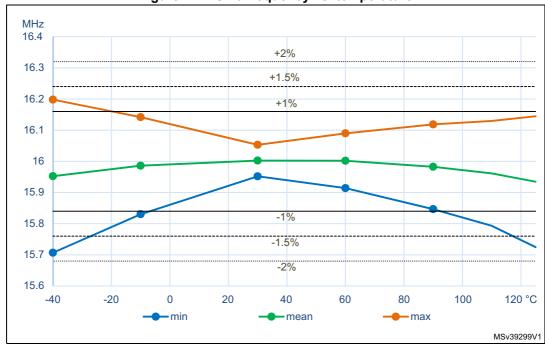


Figure 24. HSI16 frequency vs. temperature

Multi-speed internal (MSI) RC oscillator

Table 60. MSI oscillator characteristics⁽¹⁾

Symbol	Parameter		Conditions	Min	Тур	Max	Unit
			Range 0	98.7	100	101.3	
			Range 1	197.4	200	202.6	
			Range 2	394.8	400	405.2	kHz
			Range 3	789.6	800	810.4	
			Range 4	0.987	1	1.013	
		MSI mode	Range 5	1.974	2	2.026	
		INISI Mode	Range 6	3.948	4	4.052	
			Range 7	7.896	8	8.104	MHz
			Range 8	15.79	16	16.21	IVIMZ
			Range 9	23.69	24	24.31	
	MSI frequency		Range 10	31.58	32	32.42	
	after factory		Range 11	47.38	48	48.62	
f _{MSI}	calibration, done at V _{DD} =3 V and		Range 0	-	98.304	-	
	T _A =30 °C		Range 1	-	196.608	-	kHz
			Range 2	-	393.216	-	KIIZ
			Range 3	-	786.432	-	
			Range 4	-	1.016	-	
		PLL mode XTAL=	Range 5	-	1.999	-	
		32.768 kHz	Range 6	-	3.998	-	
			Range 7	-	7.995	-	NALI-
			Range 8	-	15.991	-	MHz
			Range 9	-	23.986	-	
			Range 10	-	32.014	-	
			Range 11	-	48.005	-	
	MSI oscillator		T _A = -0 to 85 °C	-3.5	-	3	
$\Delta_{TEMP}(MSI)^{(2)}$	frequency drift over temperature	MSI mode	T _A = -40 to 125 °C	-8	-	6	%

Table 60. MSI oscillator characteristics⁽¹⁾ (continued)

		Pange 0 to 3	V _{DD} = 1.62 to 3.6 V	-1.2	1	0.5	
		range o to o	V _{DD} = 2.4 to 3.6 V	-0.5	ı	0.5	
SI oscillator equency drift	MSI mode	Range 4 to 7	V _{DD} = 1.62 to 3.6 V	-2.5	ı	0.7	ws. ms.
ver V _{DD} eference is 3 V)	MSI Mode	range 4 to 1	V _{DD} = 2.4 to 3.6 V	-0.8	ı	0.7	%
		Range 8 to 11	V _{DD} = 1.62 to 3.6 V	-5	ı	1	
		range o to 11	V _{DD} = 2.4 to 3.6 V	-1.6	-	'	
requency		$T_A = -40 \text{ to } 85^{\circ}$	°C	-	1	2	
ariation in ampling mode ⁽³⁾	MSI mode	T _A = -40 to 125	°C	-	2	4	
eriod jitter for	PLL mode	For next transition	-	ı	-	3.458	
SB clock ⁽⁴⁾	Range 11	For paired transition	-	1	-	3.916	ne
edium term jitter	PLL mode	For next transition	-	ı	ı	2	113
r USB clock ⁽⁵⁾	Range 11	For paired transition	-	1	ı	4 3.458 3.916 2 1 - 20 10 8 7 6 6 0.5	
MS cycle-to- /cle jitter	PLL mode R	ange 11	-	ı	60	-	ps
MS period jitter	PLL mode Ra	ange 11	-	-	50	-	
	Range 0		-	-	10	20	
	Range 1		-	-	5	10	
SI oscillator	Range 2		-	-	4	8	IIS
art-up time	Range 3		-	-	3	7	μο
	Range 4 to 7	•	-	-	3	6	
	Range 8 to 1	1	-	-	2.5	6	
		10 % of final frequency	-	-	0.25	0.5	
SI oscillator abilization time	PLL mode Range 11	5 % of final frequency	-	-	0.5	1.25	ms
		1 % of final frequency	-	-	-	2.5	
ere es ler Males	equency drift er V _{DD} ference is 3 V) equency riation in mpling mode ⁽³⁾ riod jitter for B clock ⁽⁴⁾ edium term jitter USB clock ⁽⁵⁾ MS cycle-to- cle jitter MS period jitter SI oscillator art-up time	equency drift er V _{DD} ference is 3 V) Equency riation in mpling mode ⁽³⁾ MSI mode MSI mode PLL mode Range 11 PLL mode Range 11 MS cycle-to-cle jitter MS period jitter PLL mode Range 11 PLL mode Range 11 Range 0 Range 1 Range 2 Range 3 Range 4 to 7 Range 8 to 1	$\begin{array}{c} \text{quency drift} \\ \text{er V}_{DD} \\ \text{ference is 3 V)} \end{array} \qquad \begin{array}{c} \text{MSI mode} \\ \text{Range 8 to 11} \end{array}$ $\begin{array}{c} \text{Range 8 to 11} \\ \text{Range node} \\ \text{Range 11} \end{array}$ $\begin{array}{c} \text{Range 11} \\ \text{For next} \\ \text{For paired} \\ \text{transition} \\ \text{For paired} \\ \text{transition} \end{array}$ $\begin{array}{c} \text{For next} \\ \text{For paired} \\ \text{transition} \\ \text{For paired} \\ \text{To paired} \\ To$		Range 0 to 3	Range 0 to 3 VDD = 2.4 to 3.6 V -0.5	Range 0 to 3



155

190

Symbol	Parameter		Conditions		Min	Тур	Max	Unit
			Range 0	-	-	0.6	1	
			Range 1	-	-	0.8	1.2	
			Range 2	-	-	1.2	1.7	
			Range 3	-	-	1.9	2.5	
			Range 4	-	-	4.7	6	
(MCI)(6)	MSI oscillator	MSI and	Range 5	-	-	6.5	9	
I _{DD} (MSI) ⁽⁶⁾	power consumption	PLL mode	Range 6	-	-	11	15	μA
			Range 7	-	-	18.5	25	
			Range 8	-	-	62	80	
			Range 9	-	-	85	110	
			Range 10	-	-	110	130	

Table 60. MSI oscillator characteristics⁽¹⁾ (continued)

- 1. Guaranteed by characterization results.
- 2. This is a deviation for an individual part once the initial frequency has been measured.
- 3. Sampling mode means Low-power run/Low-power sleep modes with Temperature sensor disable.
- Average period of MSI at 48 MHz is compared to a real 48 MHz clock over 28 cycles. It includes frequency tolerance + jitter of MSI at 48 MHz clock.

Range 11

- Only accumulated jitter of MSI at 48 MHz is extracted over 28 cycles.
 For next transition: min. and max. jitter of 2 consecutive frame of 28 cycles of the MSI at 48 MHz, for 1000 captures over 28 cycles.
 For paired transitions: min. and max. jitter of 2 consecutive frame of 56 cycles of the MSI at 48 MHz, for 1000 captures over 56 cycles.
- 6. Guaranteed by design.

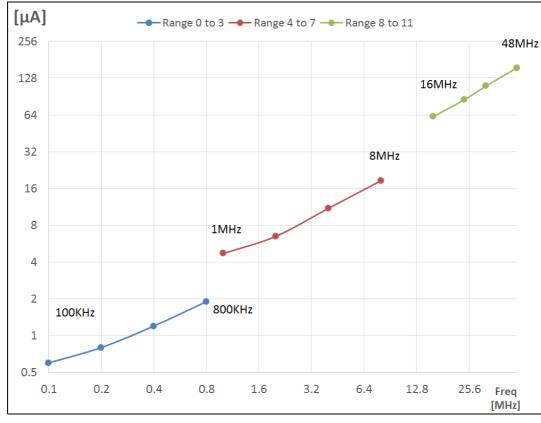


Figure 25. Typical current consumption vs. MSI frequency

High-speed internal 48 MHz (HSI48) RC oscillator

Table 61. HSI48 oscillator characteristics⁽¹⁾

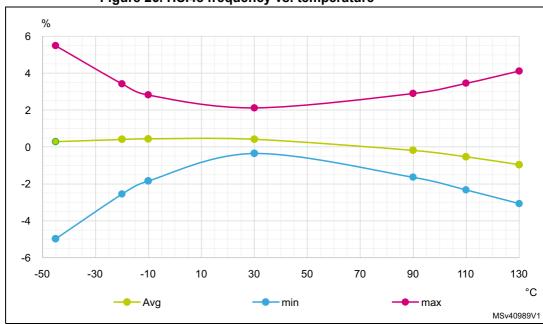
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI48}	HSI48 frequency	V _{DD} = 3.0 V, T _A = 30 °C	-	48	-	MHz
TRIM	HSI48 user trimming step	-	-	0.11 ⁽²⁾	0.18 ⁽²⁾	
USER TRIM COVERAGE	HSI48 user trimming coverage	±32 steps	±3 ⁽³⁾	±3.5 ⁽³⁾	-	
DuCy(HSI48)	Duty cycle	-	45 ⁽²⁾	-	55 ⁽²⁾	
ACC	Accuracy of the HSI48 oscillator	V _{DD} = 3.0 V to 3.6 V, T _A = -15 to 85 °C	-	-	±3 ⁽³⁾	%
ACC _{HSI48_REL}	over temperature (factory calibrated)	V_{DD} = 1.65 V to 3.6 V, T_A = -40 to 125 °C	-	-	±4.5 ⁽³⁾	
D (HSIV8)	HSI48 oscillator frequency drift	V _{DD} = 3 V to 3.6 V	-	0.025 ⁽³⁾	0.05 ⁽³⁾	
D _{VDD} (HSI48)	with V _{DD}	V _{DD} = 1.65 V to 3.6 V	-	0.05 ⁽³⁾	0.1 ⁽³⁾	
t _{su} (HSI48)	HSI48 oscillator start-up time	-	-	2.5 ⁽²⁾	6 ⁽²⁾	μs
I _{DD} (HSI48)	HSI48 oscillator power consumption	-	-	340 ⁽²⁾	380 ⁽²⁾	μA



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
N _T jitter	Next transition jitter Accumulated jitter on 28 cycles ⁽⁴⁾	-	-	±0.15 ⁽²⁾	-	ns
P _T jitter	Paired transition jitter Accumulated jitter on 56 cycles ⁽⁴⁾	-	-	±0.25 ⁽²⁾	-	113

- 1. V_{DD} = 3 V, T_A = -40 to 125 °C unless otherwise specified.
- 2. Guaranteed by design.
- 3. Guaranteed by characterization results.
- 4. Jitter measurement are performed without clock source activated in parallel.

Figure 26. HSI48 frequency vs. temperature



Low-speed internal (LSI) RC oscillator

Table 62. LSI1 oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSI}	LSI1 frequency	V _{DD} = 3.0 V, T _A = 30 °C	31.04	-	32.96	kHz
		V_{DD} = 1.62 to 3.6 V, T_A = -40 to 125 °C	29.5	-	34	KI IZ
t _{SU} (LSI1) ⁽²⁾	LSI1 oscillator start-up time	-	-	80	130	-16
t _{STAB} (LSI1) ⁽²⁾	LSI1 oscillator stabilization time	5% of final frequency	-	125	180	μs
I _{DD} (LSI1) ⁽²⁾	LSI1 oscillator power consumption	-	-	110	180	nA

- 1. Guaranteed by characterization results.
- 2. Guaranteed by design.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LSI2}	LSI2 frequency	V _{DD} = 3.0 V, T _A = 30 °C	21.6	-	44.2	kHz
		V_{DD} = 1.62 to 3.6 V, T_A = -40 to 125 °C	21.2	-	44.4	KI IZ
t _{SU} (LSI2) ⁽²⁾	LSI2 oscillator start-up time	-	0.7	-	3.5	ms
I _{DD} (LSI2) ⁽²⁾	LSI2 oscillator power consumption	-	-	500	1180	nA

Table 63. LSI2 oscillator characteristics⁽¹⁾

6.3.12 **PLL** characteristics

The parameters given in Table 64 are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 64. PLL, PLLSAI1 characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
ť	PLL input clock ⁽²⁾	-	2.66	-	16	MHz	
f _{PLL_IN}	PLL input clock duty cycle	-	45	-	55	%	
f	DLL multiplier output clock D	Voltage scaling Range 1	2	-	64		
f _{PLL_P_OUT}	PLL multiplier output clock P	Voltage scaling Range 2	2	-	16		
f	DLL multiplier output clock O	Voltage scaling Range 1	8	-	64		
†PLL_Q_OUT	PLL multiplier output clock Q	Voltage scaling Range 2	8	-	16	N 41 1-	
f	PLL multiplier output clock R	Voltage scaling Range 1	8	-	64	MHz	
f _{PLL_R_OUT}		Voltage scaling Range 2	8	-	16		
f	PLL VCO output	Voltage scaling Range 1	96	-	344		
f _{VCO_OUT}		Voltage scaling Range 2	64	-	128		
t _{LOCK}	PLL lock time	-	-	15	40	μs	
Jitter	RMS cycle-to-cycle jitter	System clock 64 MHz	-	40	-	20	
Jillei	RMS period jitter	System clock 64 MHz	-	30	-	ps	
		VCO freq = 96 MHz	-	200	260	μА	
I _{DD} (PLL)	PLL power consumption on V _{DD} ⁽¹⁾	VCO freq = 192 MHz	-	300	380		
	00	VCO freq = 344 MHz	-	520	650		

^{1.} Guaranteed by design.

^{1.} Guaranteed by characterization results.

^{2.} Guaranteed by design.

Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between the two PLLs.

6.3.13 Flash memory characteristics

Table 65. Flash memory characteristics⁽¹⁾

Symbol	Parameter	Conditions	Тур	Max	Unit
t _{prog}	64-bit programming time	-	81.7	90.8	μs
	One row (64 double word)	Normal programming	5.2	5.5	
^L prog_row	programming time	Fast programming	3.8	4.0	
4	One page (4 Kbytes) programming time	Normal programming	41.8	43.0	me
^L prog_page		Fast programming	30.4	31.0	ms
t _{ERASE}	Page (4 Kbytes) erase time	-	22.0	24.5	
t _{ME}	Mass erase time	-	22.1	25.0	
	Average consumption from V _{DD}	Write mode	3.4	-	mΛ
I _{DD}	Average consumption from V _{DD}	Erase mode	3.4	-	mA

^{1.} Guaranteed by design.

Table 66. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit
N _{END}	Endurance	T _A = -40 to +105 °C	10	kcycles
	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	
		1 kcycle ⁽²⁾ at T _A = 105 °C	15	Years
4		1 kcycle ⁽²⁾ at T _A = 125 °C	7	
t _{RET}		10 kcycles ⁽²⁾ at T _A = 55 °C	30	
		10 kcycles ⁽²⁾ at T _A = 85 °C	15	
		10 kcycles ⁽²⁾ at T _A = 105 °C	10	

^{1.} Guaranteed by characterization results.

^{2.} Cycling performed over the whole temperature range.

6.3.14 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operation to be resumed.

The test results are given in *Table 67*. They are based on the EMS levels and classes defined in AN1709 "EMC design guide for STM8, STM32 and Legacy MCUs", available on www.st.com.

Symbol	Parameter	Conditions	Level/Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 64 MHz, conforming to IEC 61000-4-2	2B
V _{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V _{DD} and V _{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 64 MHz, conforming to IEC 61000-4-4	5A

Table 67. EMS characteristics

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software.

Good EMC performance is highly dependent on the user application and the software in particular. Therefore it is recommended that the user applies EMC software optimization and pregualification tests in relation with the EMC level requested for the application.

Software recommendations

The software flow must include the management of runaway conditions such as:

- corrupted program counter
- unexpected reset
- critical data corruption (e.g. control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened



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to prevent unrecoverable errors occurring (see AN1015 "Software techniques for improving microcontrollers EMC performance", available on www.st.com).

Electromagnetic interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling two LEDs through the I/O ports). This emission test is compliant with the IEC 61967-2 standard, which specifies the test board and the pin loading.

Table 68. EMI characteristics for f_{HSE} / f_{CPUM4} , f_{CPUM0} = 32 MHz / 64 MHz, 32 MHz

Symbol	Parameter	Conditions	Monitored frequency band	Peripheral ON SMPS OFF or ON	Unit
			0.1 MHz to 30 MHz	1	
	WI	V _{DD} = 3.6 V, T _A = 25 °C, WLCSP100 package compliant with IEC 61967-2	30 MHz to 130 MHz	4	dΒμV
S _{EMI}			130 MHz to 1 GHz	-1	
			1 GHz to 2 GHz	7	
	Level ⁽²⁾		0.1 MHz to 2 GHz	1.5	-

^{1.} Refer to AN1709, "EMI radiated test" section.

6.3.15 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 69. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to ANSI/ESDA/JEDEC JS-001	2	2000	
V	Electrostatic discharge voltage	T _A = +25 °C, conforming to	C2a ⁽²⁾	500 ⁽²⁾	V
V _{ESD(CDM)}	(charge device model)	ANSI/ESD STM5.3.1 JS-002	C1 ⁽³⁾	250 ⁽³⁾	

^{1.} Guaranteed by characterization results.

3. UFBGA129 package.

^{2.} Refer to AN1709, "EMI level classsification section.

^{2.} UFQFPN48, VFQPN68 and WLCSP100 packages.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- a supply overvoltage is applied to each power supply pin
- a current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 70. Electrical sensitivity

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +105 °C conforming to JESD78A	II

6.3.16 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5 μ A / 0 μ A range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in *Table 71*.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Table 71. I/O current injection susceptibility⁽¹⁾

		Functional s		
Symbol	Description	Negative injection	Positive injection	Unit
	Injected current on all pins except PB0, PB1	-5	N/A ⁽²⁾	mA
INJ	Injected current on PB0, PB1 pins	-5	0	IIIA

- 1. Guaranteed by characterization results.
- 2. Injection not possible.

6.3.17 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 72* are derived from tests performed under the conditions summarized in *Table 24: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant.

Table 72. I/O static characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	I/O input low level voltage ⁽¹⁾		-	-	0.3 x V _{DD}	
V IL	I/O input low level voltage ⁽²⁾				0.39 x V _{DD} - 0.06	V
V	I/O input high level voltage ⁽¹⁾	1.62 V < V _{DD} < 3.6 V	0.7 x V _{DD}	ı	-	
V _{IH}	I/O input high level voltage ⁽²⁾		0.49 x V _{DD} + 0.26	ı	-	
V _{hys}	TT_xx, FT_xxx, and NRST I/O input hysteresis		-	200	-	mV
	FT_xx input leakage current	$0 \le V_{IN} \le Max(V_{DDXXX})^{(3)}$	-	-	±100	
		$\begin{aligned} &\text{Max}(\text{V}_{\text{DDXXX}}) \leq \text{V}_{\text{IN}} \leq \\ &\text{Max}(\text{V}_{\text{DDXXX}}) + 1 \text{ V}^{(2)(3)(4)} \end{aligned}$	-	-	650	
		$Max(V_{DDXXX}) +1 V < V_{IN} \le 5.5 V^{(2)(3)(4)(5)(6)}$	-	-	200 ⁽⁷⁾	
		$0 \le V_{IN} \le Max(V_{DDXXX})^{(3)}$	-	-	±150	1
I _{Ikg}	FT_lu, FT_u, and PB2 and PC3 I/Os	$\begin{aligned} &Max(V_{DDXXX}) \leq V_{IN} \leq \\ &Max(V_{DDXXX}) + 1 \ V^{(2)(3)} \end{aligned}$	-	-	2500	nA
	input leakage current	$Max(V_{DDXXX}) +1 V < V_{IN} \le 5.5 V^{(1)(3)(4)(8)}$	-	-	250	
	TT xx	$V_{IN} \le Max(V_{DDXXX})^{(3)}$	-	-	±150	
	input leakage current	$ Max(V_{DDXXX}) \le V_{IN} < \\ 3.6 \ V^{(3)} $	-	-	2000	
R _{PU}	Weak pull-up equivalent resistor ⁽¹⁾	V _{IN} = V _{SS}	25	40	55	kΩ
R _{PD}	Weak pull-down equivalent resistor ⁽¹⁾	$V_{IN} = V_{DD}$	25	40	55	, V77
C _{IO}	I/O pin capacitance ⁽⁹⁾	-	-	5	-	pF

^{1.} Tested in production.

^{2.} Guaranteed by design, not tested in production.

^{3.} Represents the pad leakage of the I/O itself. The total product pad leakage is given by $I_{Total_Ileak_max}$ = 10 μ A + number of I/Os where V_{IN} is applied on the pad x $I_{Ikg(Max)}$.

^{4.} $Max(V_{DDXXX})$ is the maximum value among all the I/O supplies.

^{5.} V_{IN} must be lower than $[Max(V_{DDXXX}) + 3.6 V]$.

- 6. Refer to Figure 27: I/O input characteristics.
- 7. To sustain a voltage higher than $Min(V_{DD}, V_{DDA}, V_{DDUSB}, V_{LCD}) + 0.3 \text{ V}$, the internal pull-up and pull-down resistors must be disabled. All FT_xx IO except FT_lu, FT_u, PB2, and PC3.
- 8. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS, whose contribution to the series resistance is minimal (~10%).
- 9. RF I/O structure excluded.

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters, as shown in *Figure 27*.

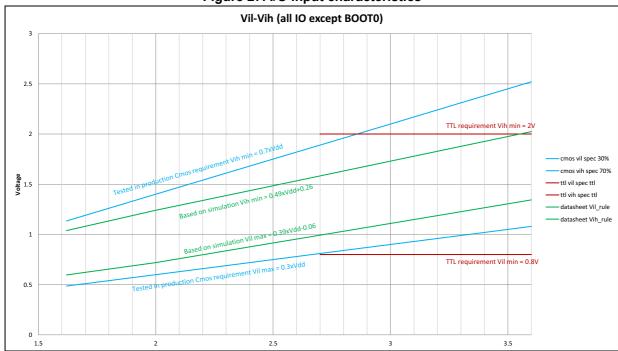


Figure 27. I/O input characteristics

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL} / V_{OH}).

In the user application, the number of I/O pins that can drive current must be limited to respect the absolute maximum rating specified in Section 6.2.

- The sum of the currents sourced by all the I/Os on V_{DD}, plus the maximum consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 20: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS} , plus the maximum consumption of the MCU sunk on V_{SS} , cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 20: Voltage characteristics*).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in

4

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Table 24: General operating conditions. All I/Os are CMOS- and TTL-compliant (FT or TT unless otherwise specified).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{OL} ⁽²⁾	Output low level voltage for an I/O pin	CMOS port ⁽³⁾	-	0.4	
V _{OH} ⁽²⁾	Output high level voltage for an I/O pin	I _{IO} = 8 mA V _{DD} ≥ 2.7 V	V _{DD} - 0.4	-	
V _{OL} ⁽²⁾	Output low level voltage for an I/O pin	TTL port ⁽³⁾	-	0.4	
V _{OH} ⁽²⁾	Output high level voltage for an I/O pin	I _{IO} = 8 mA V _{DD} ≥ 2.7 V	2.4	-	
V _{OL} ⁽²⁾	Output low level voltage for an I/O pin	I _{IO} = 20 mA	-	1.3	
V _{OH} ⁽²⁾	Output high level voltage for an I/O pin	V _{DD} ≥ 2.7 V	V _{DD} - 1.3	-	
V _{OL} ⁽²⁾	Output low level voltage for an I/O pin	I _{IO} = 4 mA	-	0.4	V
V _{OH} ⁽²⁾	Output high level voltage for an I/O pin	V _{DD} ≥ 1.62 V	V _{DD} - 0.45	ı	
		$ I_{IO} = 20 \text{ mA}$ $V_{DD} \ge 2.7 \text{ V}$	-	0.4	
V _{OLFM+} ⁽²⁾	Output low level voltage for an FT I/O pin in FM+ mode (FT I/O with "f" option)	I _{IO} = 10 mA V _{DD} ≥ 1.62 V	-	0.4	
		$ I_{IO} = 2 \text{ mA}$ 1.62 V \ge V _{DD} \ge 1.08 V	-	0.4	

Table 73. Output voltage characteristics⁽¹⁾

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Table 74*.

Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Speed	Symbol	Parameter	Conditions	Min	Max	Unit	
00			C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	5		
	Fmax	Maximum frequency	C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	1	MHz	
	Fillax	waximum nequency	C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	10	IVII IZ	
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	1.5		
00			C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	25		
	Tr/Tf	Output rice and fall time	C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	52	200	
	11/11	Output rise and fall time	C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	17	ns	
			C=10 pF, 1.62 V ≤ V _{DD} ≤ ≤2.7 V	-	37		

Table 74. I/O AC characteristics⁽¹⁾⁽²⁾



The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 20: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings Σ I_{IO}.

^{2.} Guaranteed by design.

^{3.} TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.

Speed	Symbol	Parameter	Conditions	Min	Max	Unit			
			C=50 pF, $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	-	25				
	Fmax	Maximum frequency	C=50 pF, 1.62 V ≤ V _{DD} ≤ ≤2.7 V	-	10	MHz			
01 -	Fillax	Maximum nequency	C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	50	IVIIIZ			
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	15				
			C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	9				
	Tr/Tf	Output rise and fall time	C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	16	200			
	11/11	Output rise and fail time	C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	4.5	ns			
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	9				
			C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	50				
	Fmax	Maximum frequency	C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	25	MHz			
	Fillax		C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	100 ⁽³⁾				
10			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	37.5				
10		Outrout vice and fall time	C=50 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	5.8	200			
	Tr/Tf		C=50 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	11				
	11/11	Output rise and fall time	C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	2.5	ns			
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	5				
			C=30 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	120 ⁽³⁾				
	Fmax	Maximum frequency	C=30 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	50	MHz			
	Fillax	Maximum nequency	C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	180 ⁽³⁾	IVITIZ			
11			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	75 ⁽³⁾				
"			C=30 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	3.3				
	Tr/Tf	Output rise and fall time	C=30 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	6				
	11/11	Output rise and rail tillle	C=10 pF, 2.7 V ≤ V _{DD} ≤ 3.6 V	-	1.7	ns			
			C=10 pF, 1.62 V ≤ V _{DD} ≤ 2.7 V	-	3.3				

Table 74. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

6.3.18 NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} .

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

^{1.} The maximum frequency is defined with $(T_r + T_f) \le 2/3$ T, and Duty cycle comprised between 45 and 55%.

^{2.} The fall and rise time are defined, respectively, between 90 and 10%, and between 10 and 90% of the output waveform.

^{3.} This value represents the I/O capability but the maximum system frequency is limited to 64 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)}	NRST input low level voltage	-	-	-	0.3 x V _{DD}	V
V _{IH(NRST)}	NRST input high level voltage	-	0.7 x V _{DD}	-	-	V
V _{hys(NRST)}	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R _{PU}	Weak pull-up equivalent resistor ⁽²⁾	$V_{IN} = V_{SS}$	25	40	55	kΩ
V _{F(NRST)}	NRST input filtered pulse	-	-	-	70	ns
V _{NF(NRST)}	NRST input not filtered pulse	1.71 V ≤ V _{DD} ≤ 3.6 V	350	-	-	113

Table 75. NRST pin characteristics⁽¹⁾

^{2.} The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10%).

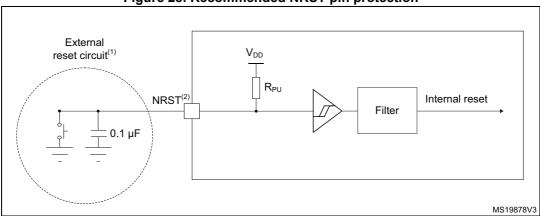


Figure 28. Recommended NRST pin protection

- 1. The reset network protects the device against parasitic resets.
- The user must ensure that the level on the NRST pin can go below the V_{IL(NRST)} max level specified in Table 75, otherwise the reset will not be taken into account by the device.
- 3. The external capacitor on NRST must be placed as close as possible to the device.

^{1.} Guaranteed by design.

6.3.19 Analog switches booster

Table 76. Analog switches booster characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Unit
V _{DD}	Supply voltage	1.62	-	3.6	V
t _{SU(BOOST)}	Booster startup time	-	-	240	μs
	Booster consumption for 1.62 V ≤ V _{DD} ≤ 2.0 V	-	-	250	
I _{DD(BOOST)}	Booster consumption for $2.0 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$	-	-	500	μΑ
	Booster consumption for $2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	-	-	900	

^{1.} Guaranteed by design.

6.3.20 Analog-to-Digital converter characteristics

Unless otherwise specified, the parameters given in *Table 77* are preliminary values derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in *Table 24: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Table 77. ADC characteristics^{(1) (2) (3)}

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DDA}	Analog supply voltage	-	1.62	-	3.6	V
V	Positive reference	V _{DDA} ≥ 2 V	2	-	V_{DDA}	V
V _{REF+}	voltage	V _{DDA} < 2 V		V_{DDA}		V
V _{REF-}	Negative reference voltage	-	V _{SSA}			V
ŧ	ADC aloak fraguanay	Range 1	0.14	-	64	MHz
f _{ADC}	ADC clock frequency	Range 2	0.14	-	16	IVITZ
		Resolution = 12 bits	-	-	4.26	
	Sampling rate	Resolution = 10 bits	-	-	4.92	
	for FAST channels	Resolution = 8 bits	-	-	5.81	
		Resolution = 6 bits	-	-	7.11	Mana
f _s		Resolution = 12 bits	-	-	3.36	Msps
	Sampling rate for SLOW channels	Resolution = 10 bits	-	-	4.00	
		Resolution = 8 bits	-	-	4.57	
		Resolution = 6 bits	-	-	7.11	
f _{TRIG}	External trigger	f _{ADC} = 64 MHz Resolution = 12 bits	-	-	4.26	MHz
11410	frequency	Resolution = 12 bits	-	-	15	1/f _{ADC}
V _{CMIN}	Input common mode	Differential mode	(V _{REF+} + V _{REF-})/2 - 0.18	(V _{REF+} + V _{REF-})/2	(V _{REF+} + V _{REF-})/2 + 0.18	V
V _{AIN} ⁽⁴⁾	Conversion voltage range(2)	-	0	-	V _{REF+}	V
R _{AIN}	External input impedance	-	-	-	50	kΩ
C _{ADC}	Internal sample and hold capacitor	-	-	5	-	pF
t _{STAB}	Power-up time	-	1			Conversion cycle
4	Calibration times	f _{ADC} = 64 MHz	1.8125			μs
t _{CAL}	Calibration time	-	116			1 / f _{ADC}

Table 77. ADC characteristics⁽¹⁾ (2) (3) (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
	Telegranasanyanaian	CKMODE = 00	1.5	2	2.5		
t _{LATR}	Trigger conversion latency Regular and	CKMODE = 01	-	-	2.0	1/f _{ADC}	
	injected channels without conversion abort	CKMODE = 10	-	-	2.25		
	without conversion about	CKMODE = 11	-	-	2.125		
	T.:	CKMODE = 00	2.5	3	3.5		
	Trigger conversion latency Injected	CKMODE = 01	-	-	3.0	A 15	
t _{LATRINJ}	channels aborting a	CKMODE = 10	-	-	3.25	1/f _{ADC}	
	regular conversion	CKMODE = 11	-	-	3.125		
t _s	Campling time	f _{ADC} = 64 MHz	0.039	-	10.0	μs	
	Sampling time	-	2.5	-	640.5	1/f _{ADC}	
t _{ADCVREG_STUP}	ADC voltage regulator start-up time	-	-	-	20	μs	
	Total conversion time	f _{ADC} = 64 MHz Resolution = 12 bits	0.234	-	1.019	μs	
t _{CONV}	(including sampling time)	Resolution = 12 bits	t _s + 12.5 cycles for successive approximations = 15 to 653			1/f _{ADC}	
		fs = 4.26 Msps	-	730	830		
I _{DDA} (ADC)	ADC consumption from the V _{DDA} supply	fs = 1 Msps	-	160	220	μA	
	and v _{DDA} supply	fs = 10 ksps	-	16	50		
	ADC consumption from	fs = 4.26 Msps	-	130	160		
I _{DDV_S} (ADC)	the V _{REF+} single ended	fs = 1 Msps	-	30	40	μA	
	mode	fs = 10 ksps	-	0.6	2		
	ADC consumption from	fs = 4.26 Msps	-	250	310		
I _{DDV_D} (ADC)	the V _{REF+} differential	fs = 1 Msps	-	60	70	μΑ	
	mode	fs = 10 ksps	-	1.3	3		

^{1.} Guaranteed by design

^{2.} The I/O analog switch voltage booster is enabled when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4V). It is disable when V_{DDA} \geq 2.4 V.

SMPS in bypass mode

^{4.} V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package. Refer to Section 4: Pinouts and pin description for further details.

Table 78. ADC sampling time⁽¹⁾⁽²⁾

D	54111	Fast chann	el	Slow chan	nel
Resolution (bits)	RAIN (kΩ)	Minimum sampling time (ns)	Sampling cycles	Minimum sampling time (ns)	Sampling cycles
	0	33	6.5	57	6.5
	0.05	37	6.5	62	6.5
	0.1	42	6.5	67	6.5
	0.2	51	6.5	76	6.5
	0.5	78	6.5	104	12.5
12	1	123	12.5	151	12.5
	5	482	47.5	526	47.5
	10	931	92.5	994	92.5
	20	1830	247.5	1932	247.5
	50	4527	640.5	4744	640.5
	100	9021	640.5	9430	640.5
	0	27	2.5	47	6.5
	0.05	30	2.5	51	6.5
	0.1	34	6.5	55	6.5
	0.2	41	6.5	62	6.5
	0.5	64	6.5	85	6.5
10	1	100	12.5	124	12.5
	5	395	47.5	431	47.5
	10	763	92.5	816	92.5
	20	1500	247.5	1584	247.5
	50	3709	640.5	3891	640.5
	100	7391	640.5	7734	640.5
	0	21	2.5	37	2.5
	0.05	24	2.5	40	6.5
	0.1	27	2.5	43	6.5
	0.2	32	6.5	49	6.5
	0.5	50	6.5	67	6.5
8	1	78	6.5	97	6.5
	5	308	47.5	337	24.5
	10	595	92.5	637	47.5
	20	1169	247.5	1237	92.5
	50	2891	247.5	3037	247.5
	100	5762	640.5	6038	640.5

Table 78. ADC sampling time⁽¹⁾⁽²⁾ (continued)

Resolution	DAIN	Fast channel		Slow channel		
(bits)	RAIN (kΩ)	Minimum sampling time (ns)	Sampling cycles	Minimum sampling time (ns)	Sampling cycles	
	0	15	2.5	26	2.5	
	0.05	17	2.5	28	2.5	
	0.1	19	2.5	31	2.5	
	0.2	23	2.5	35	2.5	
	0.5	36	6.5	48	6.5	
6	1	56	6.5	69	6.5	
	5 221		24.5	242	24.5	
	10	427	47.5	458	47.5	
	20	839	92.5	890	92.5	
	50	2074	247.5	2184	247.5	
	100	4133	640.5	4342	640.5	

^{1.} Guaranteed by design.

^{2.} V_{DD} = 1.62 V, C_{pcb} = 4.7 pF, 125 °C, booster enabled.

Table 79. ADC accuracy - Limited test conditions $1^{(1)(2)(3)}$

Symbol	Parameter		Conditions ⁽⁴⁾			Тур	Max	Unit				
			Single	Fast channel (max speed)	-	4	5					
ГТ	Total		ended	Slow channel (max speed)	-	4	5	-				
ET	unadjusted error		Differential	Fast channel (max speed)	-	3.5	4.5					
			Differential	Slow channel (max speed)	-	3.5	4.5					
			Single	Fast channel (max speed)	-	1	2.5					
EO Offset error		ended	Slow channel (max speed)	-	1	2.5						
		Differential	Fast channel (max speed)	-	1.5	2.5						
		Differential	Slow channel (max speed)	-	1.5	2.5						
			Single	Fast channel (max speed)	-	2.5	4.5					
F0	Cain array		ended	Slow channel (max speed)	-	2.5	4.5	LCD				
EG	Gain error		D:#t:-1	Fast channel (max speed)	-	2.5	3.5	LSB				
			Differential	Slow channel (max speed)	-	2.5	3.5					
		, Ż	Single	Fast channel (max speed)	-	1	1.5					
- FD	Differential	y ≤ 64 .26 Ms = 3 V,	ended	Slow channel (max speed)	-	1	1.5	-				
ED	inearity error		Differential	Fast channel (max speed)	-	1	1.2					
				Slow channel (max speed)	-	1	1.2					
		clock frequency ampling rate ≤ 4. V _{DDA} = V _{REF+}	Single ended	Fast channel (max speed)	-	1.5	2.5					
	Integral			Slow channel (max speed)	-	1.5	2.5	1				
EL	linearity error		Differential	Fast channel (max speed)	-	1	2					
		AD(Slow channel (max speed)	-	1	2					
							Single	Fast channel (max speed)	10.4	10.5	-	
ENOD	Effective		ended	Slow channel (max speed)	10.4	10.5	-	h:4a				
ENOB	number of bits	D:#	Fast channel (max speed)	10.8	10.9	-	bits					
			Differential	Slow channel (max speed)	10.8	10.9	-					
	0:11		Single	Fast channel (max speed)	64.4	65	-					
CINIAD	Signal-to- noise and		ended	Slow channel (max speed)	64.4	65	-					
SINAD	distortion		Differential	Fast channel (max speed)	66.8	67.4	-	-				
ratio	Tallo		Differential	Slow channel (max speed)	66.8	67.4	-					
			Single	Fast channel (max speed)	65	66	-	dB				
CND	Signal-to-		ended	Slow channel (max speed)	65	66	-					
SNR	noise ratio		Differential	Fast channel (max speed)	67	68	-					
			Differential	Slow channel (max speed)	67	68	-					

Table 79. ADC accuracy - Limited test conditions $1^{(1)(2)(3)}$ (continued)

Symbol	Parameter		Cond	itions ⁽⁴⁾	Min	Тур	Max	Unit
64 MHz, Msps, V,	Single	Fast channel (max speed)	-	-74	-73			
TUD	Total	ency s s 4.26 s EF+ = 3	ended	Slow channel (max speed)	-	-74	-73	10
THD	harmonic distortion	OC clock frequency Sampling rate ≤ 4.5 VDDA = VREF+ TA = 25 °C		Fast channel (max speed)	-	-79	-76	dB
		ADC clo Sampl V _D	Differential	Slow channel (max speed)	-	-79	-76	

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
 significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
 Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disable when $V_{DDA} \ge 2.4$ V. No oversampling.

Table 80. ADC accuracy - Limited test conditions 2⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions ⁽⁴⁾			Min	Тур	Max	Unit
			Single	Fast channel (max speed)	-	4	6.5	
ЕТ	Total		ended	Slow channel (max speed)	-	4	6.5	
ET	unadjusted error		D:#ti-1	Fast channel (max speed)	-	3.5	5.5	
			Differential	Slow channel (max speed)	-	3.5	5.5	
			Single	Fast channel (max speed)	-	1	4.5	
F0	Officet owner		ended	Slow channel (max speed)	-	1	5	
EO	Offset error		Differential	Fast channel (max speed)	-	1.5	3	
			Differential	Slow channel (max speed)	-	1.5	3	
			Single	Fast channel (max speed)	-	2.5	6	
EG	Coin orror		ended	Slow channel (max speed)	-	2.5	6	LSB
EG	Gain error		Differential	Fast channel (max speed)	-	2.5	3.5	LOB
			Dillerential	Slow channel (max speed)	-	2.5	3.5	
		, , ,	Single	Fast channel (max speed)	-	1	1.5	
ED	Differential	4 MI	ended	Slow channel (max speed)	-	1	1.5	
ED	linearity error	ADC clock frequency \leq 64 MHz, Sampling rate \leq 4.26 Msps, $V_{DDA} \geq$ 2 V TA = 25 °C	Differential	Fast channel (max speed)	-	1	1.2	
		g rate ≤ 4.2 V _{DDA} ≥ 2 V	Differential	Slow channel (max speed)	-	1	1.2	
		c frequencing rate \leq 4 V _{DDA} \geq 2 TA = 25	Single	Fast channel (max speed)	-	1.5	3.5	
EL	Integral	ock fi	ended	Slow channel (max speed)	-	1.5	3.5	
	linearity error	C clc	Differential	Fast channel (max speed)	-	1	3	
		AD. S	Differential	Slow channel (max speed)	-	1	2.5	
			Single	Fast channel (max speed)	10	10.5	-	
ENOB	Effective		ended	Slow channel (max speed)	10	10.5	-	hita
ENOB	number of bits		Differential	Fast channel (max speed)	10.7	10.9	-	bits
			Dillerential	Slow channel (max speed)	10.7	10.9	-	
	0:		Single	Fast channel (max speed)	62	65	-	
CINAD	Signal-to- noise and		ended	Slow channel (max speed)	62	65	-	
SINAD	distortion		Differential	Fast channel (max speed)	66	67.4	-	
	ratio		Differential	Slow channel (max speed)	66	67.4	-	-10
			Single	Fast channel (max speed)	64	66	-	dB
CND	Signal-to-		ended	Slow channel (max speed)	64	66	-	
SNR	noise ratio		Differential	Fast channel (max speed)	66.5	68	-	
			Differential	Slow channel (max speed)	66.5	68	-	

Table 80. ADC accuracy - Limited test conditions 2⁽¹⁾⁽²⁾⁽³⁾ (continued)

Symbol	Parameter		Cond	itions ⁽⁴⁾	Min	Тур	Max	Unit
64 MHz, MSDS,		Single	Fast channel (max speed)	ı	-74	-65		
TUE	Se S	ended	Slow channel (max speed)	-	-74	-67	<u>.</u>	
THD	harmonic distortion	frequ y rate /DDA FA =	D:"	Fast channel (max speed)	-	-79	-70	dB
		ADC clock Sampling	Differential	Slow channel (max speed)	-	-79	-71	

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
 significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
 Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disable when $V_{DDA} \ge 2.4$ V. No oversampling.

Table 81. ADC accuracy - Limited test conditions $3^{(1)(2)(3)}$

Symbol	Parameter		Conditions ⁽⁴⁾		Min	Тур	Max	Unit
			Single	Fast channel (max speed)	-	5.5	7.5	
ET	Total		ended	Slow channel (max speed)	-	4.5	6.5	
	unadjusted error		Differential	Fast channel (max speed)	-	4.5	7.5	
			Differential	Slow channel (max speed)	-	4.5	5.5	
			Single	Fast channel (max speed)	-	2	5	
EO	Offset error		ended	Slow channel (max speed)	-	2.5	5	
	Oliset elloi		Differential	Fast channel (max speed)	-	2	3.5	
			Dillerential	Slow channel (max speed)	-	2.5	3	
			Single	Fast channel (max speed)	-	4.5	7	
EG	Gain error		ended	Slow channel (max speed)	-	3.5	6	LSB
EG	Gain enoi		Differential	Fast channel (max speed)	-	3.5	4	LOD
			Differential	Slow channel (max speed)	-	3.5	5	
		AHz, ss, 6 V,	Single	Fast channel (max speed)	-	1.2	1.5	
ED	Differential	2 2 ~	ended	Slow channel (max speed)	-	1.2	1.5	
ED	linearity error	/ ≤ 6 26 N ≘F+ ≤ ≷ang	Differential	Fast channel (max speed)	-	1	1.2	
		C clock frequency \leq 64 M ampling rate \leq 4.26 Msp 5 V \leq V _{DDA} = V _{REF+} \leq 3. Voltage scaling Range 1	Dillerential	Slow channel (max speed)	-	1	1.2	
		requ rate DA =	Single	Fast channel (max speed)	-	3	3.5	
EL	Integral	ADC clock frequ Sampling ratu 1.65 V ≤ V _{DDA} Voltage sca	ended	Slow channel (max speed)	-	2.5	3.5	
EL.	linearity error	C clc amp 5 V : Volt	Differential	Fast channel (max speed)	-	2	2.5	
		ADO S 1.6	Differential	Slow channel (max speed)	-	2	2.5	
			Single	Fast channel (max speed)	10	10.4	-	
ENOR	Effective		ended	Slow channel (max speed)	10	10.4	-	hita
ENOB	number of bits		Differential	Fast channel (max speed)	10.6	10.7	-	bits
			Differential	Slow channel (max speed)	10.6	10.7	-	
	Oine al ta		Single	Fast channel (max speed)	62	64	-	
CINAD	Signal-to- noise and		ended	Slow channel (max speed)	62	64	-	
SINAD	distortion		Differential	Fast channel (max speed)	65	66	-	
	ratio		Differential	Slow channel (max speed)	65	66	-	-10
			Single	Fast channel (max speed)	63	65	-	dB
CND	Signal-to-		ended	Slow channel (max speed)	63	65	-	
SNR	noise ratio		Differential	Fast channel (max speed)	66	67	-	
			merential	Slow channel (max speed)	66	67	-	

Table 81. ADC accuracy - Limited test conditions $3^{(1)(2)(3)}$ (continued)

Symbol	Parameter		Cond	itions ⁽⁴⁾	Min	Тур	Max	Unit
64 MHz, Msps, ≤ 3.6 V, ge 1	Single	Fast channel (max speed)	-	-69	-67			
TUD	Total	7 ≤ 26 26 EF+	San + Landed	Slow channel (max speed)	-	-71	-67	٦D
THD	harmonic distortion	ock frequency pling rate ≤ 4 ≤ V _{DDA} = V _{RE} tage scaling F	Diff. and the	Fast channel (max speed)	-	-72	-71	dB
		ADC clock f Sampling 1.65 V ≤ V _C Voltage	Differential	Slow channel (max speed)	-	-72	-71	

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
 significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
 Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disable when $V_{DDA} \ge 2.4$ V. No oversampling.

Table 82. ADC accuracy - Limited test conditions $4^{(1)(2)(3)}$

Symbol	Parameter		Conditions ⁽⁴⁾		Min	Тур	Max	Unit
			Single	Fast channel (max speed)	-	5	5.4	
ET	Total		ended	Slow channel (max speed)	-	4	5	
	unadjusted error		Differential	Fast channel (max speed)	-	4	5	
			Differential	Slow channel (max speed)	-	3.5	4.5	
			Single	Fast channel (max speed)	-	2	4	
EO	Offset error		ended	Slow channel (max speed)	-	2	4	
	Oliset error		Differential	Fast channel (max speed)	-	2	3.5	
			Dilleteritial	Slow channel (max speed)	-	2	3.5	
			Single	Fast channel (max speed)	-	4	4.5	
EG	Gain error		ended	Slow channel (max speed)	-	4	4.5	LSB
EG	Gain enoi		Differential	Fast channel (max speed)	-	3	4	LOB
			Differential	Slow channel (max speed)	-	3	4	
		3.6 V,	Single	Fast channel (max speed)	-	1	1.5	
ED	Differential	6 MI ≤ 3.6 le 2	ended	Slow channel (max speed)	-	1	1.5	
ED	linearity error	/ ≤ 1 EF+ : Rang	Differential	Fast channel (max speed)	-	1	1.2	
		ADC clock frequency ≤ 16 MHz, 1.65 V ≤ V _{DDA} = VREF+ ≤ 3.6 V, Voltage scaling Range 2	Dillerential	Slow channel (max speed)	-	1	1.2	
		requ DA = scali	Single	Fast channel (max speed)	-	2.5	3	
EL	Integral	ock f VDI age	ended	Slow channel (max speed)	-	2.5	3	
CL.	linearity error	C clc 5 V s Volt	Differential	Fast channel (max speed)	-	2	2.5	
		AD 1.6	Differential	Slow channel (max speed)	-	2	2.5	
			Single	Fast channel (max speed)	10.2	10.5	-	
ENOB	Effective number of		ended	Slow channel (max speed)	10.2	10.5	-	bits
ENOB	bits		Differential	Fast channel (max speed)	10.6	10.7	-	DILS
			Dillerential	Slow channel (max speed)	10.6	10.7	-	
	Ciamal to		Single	Fast channel (max speed)	63	65	-	
SINAD	Signal-to- noise and		ended	Slow channel (max speed)	63	65	-	
SINAD	distortion		Differential	Fast channel (max speed)	65	66	-	
	ratio		Differential	Slow channel (max speed)	65	66	-	40
			Single	Fast channel (max speed)	64	65	-	dB
CND	Signal-to-		ended	Slow channel (max speed)	64	65	-	
SNR	noise ratio		Differential	Fast channel (max speed)	66	67	-	
		_	וופופווומו	Slow channel (max speed)	66	67	-	

Symbol	Parameter		Cond	itions ⁽⁴⁾	Min	Тур	Max	Unit
		16 MHz, · ≤ 3.6 V, ge 2	Single	Fast channel (max speed)	-	-71	-69	
	Total	ency ≤ 1 VREF+ : ng Rang	ended	Slow channel (max speed)	-	-71	-69	
THD	harmonic distortion	eque o _A = scali		Fast channel (max speed)	-	-73	-72	dB
		ADC clock fr 1.65 V ≤ V _{DC} Voltage 8	Differential	Slow channel (max speed)	-	-73	-72	

Table 82. ADC accuracy - Limited test conditions $4^{(1)(2)(3)}$ (continued)

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
 significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
 Schottky diode (pin to ground) to analog pins that may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enabled when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disabled when $V_{DDA} \ge 2.4$ V. No oversampling.

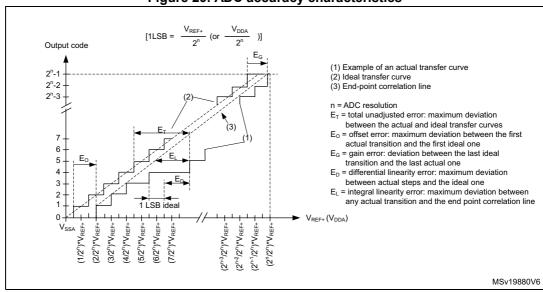


Figure 29. ADC accuracy characteristics

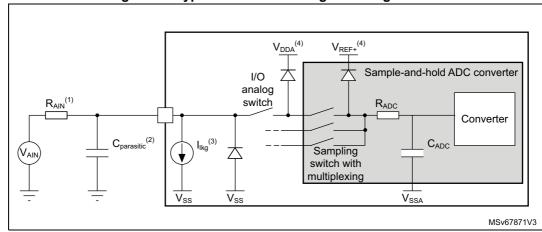


Figure 30. Typical connection diagram using the ADC

- 1. Refer to Table 77: ADC characteristics for the values of R_{AIN} , R_{ADC} and C_{ADC} .
- C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (refer to *Table 72: I/O static characteristics* for the value of the pad capacitance). A high C_{parasitic} value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.
- 3. Refer to Table 72: I/O static characteristics for the values of I_{lkq}.
- 4. Refer to Figure 16 and Figure 17.

General PCB design guidelines

Power supply decoupling has to be performed as shown in *Figure 16: Power supply scheme* (all packages except UFBGA129 and WLCSP100). The 10 nF capacitor needs to be ceramic (good quality), placed as close as possible to the chip.

6.3.21 Voltage reference buffer characteristics

Table 83. VREFBUF characteristics⁽¹⁾

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		Normal mode	V _{RS} = 0	2.4	-	3.6	
W	Analog supply	Normal mode	V _{RS} = 1	2.8	-	3.6	
V_{DDA}	voltage	Degraded mode ⁽²⁾	V _{RS} = 0	1.65	-	2.4	
		Degraded mode	V _{RS} = 1	1.65	-	2.8	V
		Normal mode ⁽³⁾	V _{RS} = 0	2.046	2.048	2.049	v
V _{REFBUF_}	_{JF} Voltage	Normal mode.	V _{RS} = 1	2.498	2.500	2.502	
OUT	reference output	Degraded mode ⁽²⁾	V _{RS} = 0	V _{DDA} -150 mV	-	2.049	
		Degraded mode	V _{RS} = 1	V _{DDA} -150 mV	-	2.502	
TRIM	Trim step resolution	-	-	-	±0.05	±0.1	%
CL	Load capacitor	-	-	0.5	1	1.5	μF
esr	Equivalent series resistor of C _{load}	-	-	-	-	2	Ω

Table 83. VREFBUF characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditio	ns	Min	Тур	Max	Unit
I _{load}	Static load current	-	-	-	-	4	mA
1	Line regulation	201/21/ 2261/	I _{load} = 500 μA	-	200	1000	nnm/\/
I _{line_reg}	Line regulation	$2.8 \text{ V} \le \text{V}_{\text{DDA}} \le 3.6 \text{ V}$	I _{load} = 4 mA	-	100	500	ppm/V
I _{load_reg}	Load regulation	500 μA ≤ I _{load} ≤4 mA	Normal mode	-	50	500	ppm/mA
т	Temperature	-40 °C < T _J < +125 °C	;	-	-	T _{coeff} vrefint + 50	ppm/°C
T _{Coeff}	coefficient	0 °C < T _J < +50 °C		-	-	T _{coeff_} vrefint + 50	тррии С
PSRR	Power supply	DC		40	60	-	dB
FORK	rejection	100 kHz		25	40	-	uБ
		$CL = 0.5 \mu F^{(4)}$		-	300	350	
t _{START}	Start-up time	$CL = 1.1 \mu F^{(4)}$		-	500	650	μs
		CL = 1.5 µF ⁽⁴⁾		-	650	800	
I _{INRUSH}	Control of maximum DC current drive on VREFBUF_OUT during start-up phase ⁽⁵⁾	-	-	-	8	-	mA
_	VREFBUF	I _{load} = 0 μA		-	16	25	
I _{DDA} (VREFBUF)	consumption	I _{load} = 500 μA			18	30	μA
,	from V _{DDA}	I _{load} = 4 mA		-	35	50	

^{1.} Guaranteed by design, unless otherwise specified.

In degraded mode the voltage reference buffer cannot maintain accurately the output voltage that will follow (V_{DDA} - drop voltage).

^{3.} V_{DDA} = 3 V, T_{J} = 30 °C, I_{load} = 100 μA .

^{4.} The capacitive load must include a 100 nF capacitor in order to cut-off the high frequency noise.

^{5.} To correctly control the VREFBUF in-rush current during start-up phase and scaling change, the V_{DDA} voltage must be in the range [2.4 V to 3.6 V] and [2.8 V to 3.6 V] respectively for $V_{RS} = 0$ and $V_{RS} = 1$.

6.3.22 Comparator characteristics

Table 84. COMP characteristics⁽¹⁾

Symbol	Parameter	(Conditions	Min	Тур	Max	Unit
V_{DDA}	Analog supply voltage		-	1.62	-	3.6	
V _{IN}	Comparator input voltage range		-	0	-	V _{DDA}	V
V _{BG} ⁽²⁾	Scaler input voltage		-		V _{REFINT}	Γ	
V _{SC}	Scaler offset voltage		-		±5	±10	mV
I (SCALED)	Scaler static consumption	BRG_EN=0 (bridge disable)		-	200	300	nA
I _{DDA} (SCALER)	from V _{DDA}	BRG_EN=1 (bi	BRG_EN=1 (bridge enable)		0.8	1	μA
t _{START_SCALER}	Scaler startup time		-	-	100	200	μs
		High-speed	V _{DDA} ≥ 2.7 V	-	-	5	
	Comparator startup time	mode	V _{DDA} < 2.7 V	-	-	7	
t _{START}	to reach propagation	Medium mode	V _{DDA} ≥ 2.7 V	-	-	15	μs
	delay specification	Medium mode	V _{DDA} < 2.7 V	-	-	25	
		Ultra-low-power mode		-	-	40	
		High-speed	V _{DDA} ≥ 2.7 V	-	55	80	ns
t _D ⁽³⁾	Propagation delay with	mode	V _{DDA} < 2.7 V	-	55	100	113
'D`	100 mV overdrive	Medium mode		-	0.55	0.9	116
		Ultra-low-powe	r mode	-	4	7	μs
V_{offset}	Comparator offset error	Full common m	node range	-	±5	±20	mV
		No hysteresis		-	0	-	
V.	Comparator hysteresis	Low hysteresis		-	8	-	mV
V_{hys}	Comparator hysteresis	Medium hyster	esis	-	15	-	IIIV
		High hysteresis	3	-	27	-	
		Ultra-low-	Static	-	400	600	
		power mode	With 50 kHz ±100 mV overdrive square signal	-	1200	-	nA
	Commonster consumention	Madium	Static	-	5	7	
I _{DDA} (COMP)	Comparator consumption from V _{DDA}	Medium mode	With 50 kHz ±100 mV overdrive square signal	-	6	-	
			Static	-	70	100	μA
		High-speed mode	With 50 kHz ±100 mV overdrive square signal	-	75	-	

^{1.} Guaranteed by design, unless otherwise specified.

^{2.} Refer to Table 36: Embedded internal voltage reference.

^{3.} Guaranteed by characterization results.

6.3.23 Temperature sensor characteristics

Table 85. TS characteristics

Symbol	Parameter	Min	Тур	Max	Unit
T _L ⁽¹⁾	V _{TS} linearity with temperature	-	±1	±2	°C
Avg_Slope ⁽²⁾	Average slope	2.3	2.5	2.7	mV / °C
V ₃₀	Voltage at 30 °C (±5 °C) ⁽³⁾	0.742	0.76	0.785	V
t _{START} (TS_BUF) ⁽¹⁾	Sensor buffer start-up time in continuous mode ⁽⁴⁾	-	8	15	μs
t _{START} (1)	Start-up time when entering in continuous mode ⁽⁴⁾	-	70	120	μs
t _{S_temp} ⁽¹⁾	ADC sampling time when reading the temperature	5	-	-	μs
I _{DD} (TS) ⁽¹⁾	Temperature sensor consumption from V_{DD} , when selected by ADC	-	4.7	7	μΑ

^{1.} Guaranteed by design.

6.3.24 V_{BAT} monitoring characteristics

Table 86. V_{BAT} monitoring characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Unit
R	Resistor bridge for V _{BAT}	-	3 x 39	-	kΩ
Q	Ratio on V _{BAT} measurement	-	3	-	-
Er ⁽²⁾	Error on Q	-10	-	10	%
t _{S_vbat} ⁽²⁾	ADC sampling time when reading V _{BAT}	12	-	-	μs

^{1. 1.55 &}lt; V_{BAT} < 3.6 V.

Table 87. V_{BAT} charging characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	Battery	VBRS = 0	-	5	-	- 0
R _{BC}	charging resistor	VBRS = 1	-	1.5	-	kΩ

^{2.} Guaranteed by characterization results.

Measured at V_{DDA} = 3.0 V ±10 mV. The V₃₀ ADC conversion result is stored in the TS_CAL1 byte. Refer to Table 11: Temperature sensor calibration values.

^{4.} Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.

^{2.} Guaranteed by design.

6.3.25 SMPS step-down converter characteristics

The SMPS step-down converter characteristic are given at 4 MHz clock, using a 10 μ H inductor and a 4.7 μ F capacitor.

6.3.26 LCD controller characteristics

The STM32WB55xx devices embed a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the VLCD pin to decouple this converter.

Table 88. LCD controller characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V_{LCD}	LCD external voltage		-	-	3.6		
V _{LCD0}	LCD internal reference volta	ge 0	-	2.62	-		
V _{LCD1}	LCD internal reference volta	D internal reference voltage 1		2.76	-		
V _{LCD2}	LCD internal reference volta	ge 2	-	2.89	-		
V _{LCD3}	LCD internal reference volta	ge 3	-	3.04	-	V	
V _{LCD4}	LCD internal reference volta	ge 4	-	3.19	-		
V _{LCD5}	LCD internal reference volta	ge 5	-	3.32	-		
V _{LCD6}	LCD internal reference volta	ge 6	-	3.46	-		
V _{LCD7}	LCD internal reference volta	ge 7	-	3.62	-		
	V _{LCD} external capacitance	Buffer OFF (BUFEN=0 is LCD_CR register)	0.2	-	2	uг	
C _{ext}	V _{CD} external capacitance	Buffer ON (BUFEN=1 is LCD_CR register)	1	-	2	μF	
, (2)	Supply current from V _{DD} at V _{DD} = 2.2 V	Buffer OFF (BUFEN=0 is LCD_CR register)	-	3	-		
I _{LCD} ⁽²⁾	Supply current from V _{DD} at V _{DD} = 3.0 V	Buffer OFF (BUFEN=0 is LCD_CR register)	-	1.5	-	μΑ	
		Buffer OFF (BUFFEN = 0, PON = 0)	-	0.5	-		
	Supply current from V _{LCD}	Buffer ON (BUFFEN = 1, 1/2 Bias)	-	0.6	-		
I _{VLCD}	(V _{LCD} = 3 V)	Buffer ON (BUFFEN = 1, 1/3 Bias)	-	0.8	-	μA	
		Buffer ON (BUFFEN = 1, 1/4 Bias)	-	1	-		
R _{HN}	Total High resistor value for Low drive resistive network		-	5.5	-	МΩ	
R _{LN}	Total Low resistor value for h	High drive resistive network	ı	240	-	kΩ	

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V ₄₄	Segment/Common highest le	evel voltage	-	V_{LCD}	-	
V ₃₄	Segment/Common 3/4 level voltage		-	3/4 V _{LCD}	-	
V ₂₃	Segment/Common 2/3 level voltage			2/3 V _{LCD}		
V ₁₂	Segment/Common 1/2 level	voltage	-	1/2 V _{LCD}		V
V ₁₃	Segment/Common 1/3 level	voltage	-	1/3 V _{LCD}	-	
V ₁₄	Segment/Common 1/4 level	voltage	-	1/4 V _{LCD}	-	
V ₀	Segment/Common lowest le	vel voltage	-	0	-	

Table 88. LCD controller characteristics⁽¹⁾ (continued)

6.3.27 Timer characteristics

The parameters given in the following tables are guaranteed by design. Refer to Section 6.3.17 for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 89. TIMx⁽¹⁾ characteristics

Symbol	Parameter	Conditions	Min	Max	Unit	
+	Timer resolution time	-	1	-	t _{TIMxCLK}	
^t res(TIM)	Timer resolution time	f _{TIMxCLK} = 64 MHz	15.625	-	ns	
f	Timer external clock frequency	-	0	f _{TIMxCLK} /2	MHz	
f _{EXT}	on CH1 to CH4	f _{TIMxCLK} = 64 MHz	0	40	IVITZ	
Pac	Timer resolution	TIM1, TIM16, TIM17	-	16	bit	
Res _{TIM}	Timer resolution	TIM2	-	32	Dit	
+	16-bit counter clock period	-	1	65536	t _{TIMxCLK}	
tCOUNTER	To-bit counter clock period	f _{TIMxCLK} = 64 MHz	0.015625	1024	μs	
t	Maximum possible count with	-	-	65536 × 65536	t _{TIMxCLK}	
^t MAX_COUNT	32-bit counter	f _{TIMxCLK} = 64 MHz	-	67.10	S	

^{1.} TIMx is used as a general term where x stands for 1, 2, 16 or 17.

^{1.} Guaranteed by design.

^{2.} LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio = 64, all pixels active, no LCD connected.

Prescaler divider	PR[2:0] bits	Min timeout RL[11:0] = 0x000	Max timeout RL[11:0] = 0xFFF	Unit
/4	0	0.125	512	
/8	1	0.250	1024	
/16	2	0.500	2048	
/32	3	1.0	4096	ms
/64	4	2.0	8192	
/128	5	4.0	16384	
/256	6 or 7	8.0	32768	

Table 90. IWDG min/max timeout period at 32 kHz (LSI1)⁽¹⁾

6.3.28 Clock recovery system (CRS)

The devices embed a special block for the automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range.

This automatic trimming is based on the external synchronization signal, which can be derived from USB Sart Of Frame (SOF) signalization, from LSE oscillator, from an external signal on CRS_SYNC pin or generated by user software.

For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

Communication interfaces characteristics 6.3.29

I²C interface characteristics

The I2C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): bit rate up to 100 kbit/s
- Fast-mode (Fm): bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): bit rate up to 1 Mbit/s.

Table 91. Minimum I2CCLK frequency in all I²C modes

Symbol	Parameter		Condition	Min	Unit
		Standard-mode	Standard-mode -		
		I2CCLK Fast-mode Fast-mode Fast-mode Plus	Analog filter ON, DNF = 0	9	
f _(I2CCLK)			Analog filter OFF, DNF = 1	9	MHz
			Analog filter ON, DNF = 0	19	
		rast-mode rius	Analog filter OFF, DNF = 1	16	

The I2C timings requirements are guaranteed by design when the I2C peripheral is properly configured (see the reference manual).

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^{1.} The exact timings still depend on the phasing of the APB interface clock vs. the LSI clock, hence there is always a full RC period of uncertainty.

The SDA and SCL I/O requirements are met with the following restriction: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present. The 20 mA output drive requirement in Fast-mode Plus is supported partially.

This limits the maximum load C_{load} supported in Fast-mode Plus, given by these formulas:

- $t_r(SDA/SCL) = 0.8473 \times R_p \times C_{load}$
- $R_p(min) = [V_{DD} V_{OL}(max)] / I_{OL}(max)$

where R_p is the I2C lines pull-up. Refer to Section 6.3.17 for the I2C I/Os characteristics.

All I2C SDA and SCL I/Os embed an analog filter, refer to Table 92 for its characteristics.

Table 92. I2C analog filter characteristics⁽¹⁾

Symbol	Parameter	Min	Max	Unit
t _{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	50 ⁽²⁾	110 ⁽³⁾	ns

- 1. Guaranteed by design.
- Spikes with widths below t_{AF(min)} are filtered.
- 3. Spikes with widths above $t_{\text{AF}(\text{max})}$ are not filtered

SPI characteristics

Unless otherwise specified, the parameters given in *Table 93* for SPI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in *Table 24: General operating conditions*.

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V_{DD}

Refer to Section 6.3.17 for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

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Table 93. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode 1.65 < V _{DD} < 3.6 V Voltage Range 1			32	
		Master transmitter mode 1.65 < V _{DD} < 3.6 V Voltage Range 1			32	
fsck 1/t _{c(SCK)}	SPI clock frequency	Slave receiver mode 1.65 < V _{DD} < 3.6 V Voltage Range 1	-	-	32	MHz
		Slave mode transmitter/full duplex 2.7 < V _{DD} < 3.6 V Voltage Range 1			32 ⁽²⁾	
		Slave mode transmitter/full duplex 1.65 < V _{DD} < 3.6 V Voltage Range 1			20.5 ⁽²⁾	
		Voltage Range 2			8	
t _{su(NSS)}	NSS setup time	Slave mode, SPI prescaler = 2	4xT _{PCLK}	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI prescaler = 2	2xT _{PCLK}	-	-	-
$\begin{matrix} t_{\text{w(SCKH)}} \\ t_{\text{w(SCKL)}} \end{matrix}$	SCK high and low time	Master mode	T _{PCLK} - 1.5	T _{PCLK}	T _{PCLK} + 1	
t _{su(MI)}	Data input setup time	Master mode	1.5	-	-	
t _{su(SI)}	Data input setup time	Slave mode	1	-	-	
t _{h(MI)}	Data input hold time	Master mode	5	-	-	ns
t _{h(SI)}	Data input noid time	Slave mode	1	-	-	115
t _{a(SO)}	Data output access time	Slave mode	9	-	34	
t _{dis(SO)}	Data output disable time	Slave mode	9	-	16	
		Slave mode 2.7 < V _{DD} < 3.6 V Voltage Range 1	-	14.5	15.5	
t _{v(SO)}	Data output valid time	Slave mode 1.65 < V _{DD} < 3.6 V Voltage Range 1	-	15.5	24	
		Slave mode 1.65 < V _{DD} < 3.6 V Voltage Range 2	-	19.5	26	ns
t _{v(MO)}		Master mode (after enable edge)	-	2.5	3	
t _{h(SO)}	Data output hold time	Slave mode (after enable edge)	8	-	-	
t _{h(MO)}	Data output noid time	Master mode (after enable edge)	1	-	-	

^{1.} Guaranteed by characterization results.

^{2.} Maximum frequency in Slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$, which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while Duty(SCK) = 50 %.

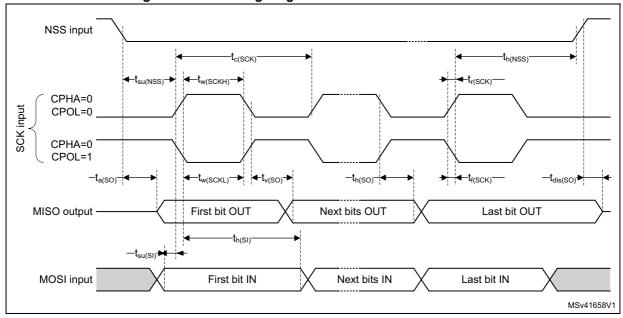
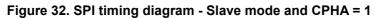
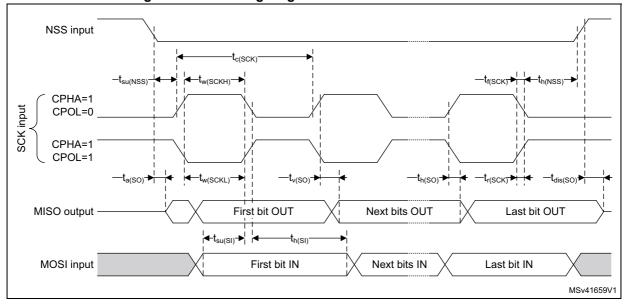


Figure 31. SPI timing diagram - Slave mode and CPHA = 0





1. Measurement points are set at CMOS levels: 0.3 $\rm V_{DD}$ and 0.7 $\rm V_{DD}.$

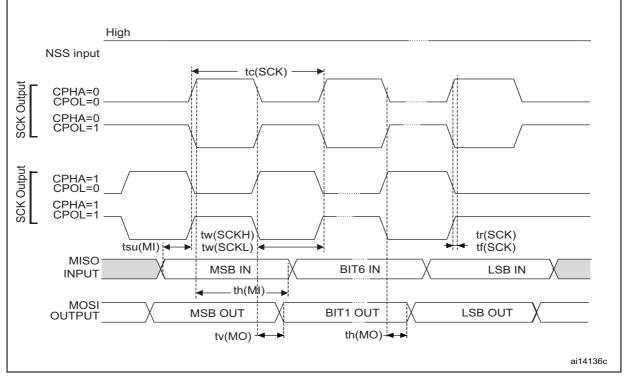


Figure 33. SPI timing diagram - master mode

1. Measurement points are set at CMOS levels: 0.3 $\rm V_{DD}$ and 0.7 $\rm V_{DD}$.

Quad-SPI characteristics

Unless otherwise specified, the parameters given in *Table 94* and *Table 95* for Quad-SPI are derived from tests performed under the ambient temperature, f_{AHB} frequency and V_{DD} supply voltage conditions summarized in *Table 24: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 15 or 20 pF
- Measurement points are set at CMOS levels: 0.5 x V_{DD}

Refer to *Section 6.3.17* for more details on the input/output alternate function characteristics.

Table 94. Quad-SPI characteristics in SDR mode⁽¹⁾

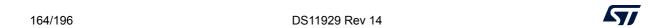
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$1.65 < V_{DD} < 3.6 \text{ V, C}_{LOAD} = 20 \text{ pF}$ Voltage Range 1	-	-	40	
F _{CK} Quad-SPI	1.65 < V _{DD} < 3.6 V, C _{LOAD} = 15 pF Voltage Range 1	-	-	48	MHz	
1/t _(CK)	clock frequency	$2.7 < V_{DD} < 3.6 \text{ V, } C_{LOAD} = 15 \text{ pF}$ Voltage Range 1	-	-	60	IVII IZ
		1.65 < V _{DD} < 3.6 V C _{LOAD} = 20 pF Voltage Range 2	-	-	16	
t _{w(CKH)}	Quad-SPI clock	f _{AHBCLK} = 48 MHz, presc=1	t _(CK) /2 - 0.5	-	t _(CK) /2 + 1	
t _{w(CKL)}	high and low time	IAHBCLK- 40 MITZ, presc-1	t _(CK) /2 - 1	-	$t_{(CK)}/2 + 0.5$	
	Data input actus time	Voltage Range 1	2	-	-	
t _{s(IN)}	Data input setup time	Voltage Range 2	3.5	-	-	
	Data input hold time	Voltage Range 1	4.5	-	-	20
t _{h(IN)}	Data input hold time	Voltage Range 2	6	-	-	ns
4	Data output valid time	Voltage Range 1	-	1	1.5	
t _{v(OUT)}	Data output valid time	Voltage Range 2	-	1	1.5	
+	Data output hold time	Voltage Range 1	0	-	-	
t _{h(OUT)}	Data output hold time	Voltage Range 2	0	-	-	

^{1.} Guaranteed by characterization results.

Table 95. Quad-SPI characteristics in DDR mode⁽¹⁾

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		1.65 < V _{DD} < 3.6 V, C _{LOAD} Voltage Range 1	= 20 pF	-	-	40	
F _{CK}	Quad-SPI clock	2.0 < V _{DD} < 3.6 V, C _{LOAD} = Voltage Range 1	= 20 pF	-	-	50	MHz
1/t _(CK)	frequency	1.65 < V _{DD} < 3.6 V, C _{LOAD} Voltage Range 1	= 15 pF	-	-	48	IVII IZ
		1.65 < V _{DD} < 3.6 V C _{LOAD} Voltage Range 2	= 20 pF	-	-	16	
t _{w(CKH)}	Quad-SPI clock	f _{AHBCLK} = 48 MHz, presc=	n	t _(CK) /2	-	t _(CK) /2 + 1	
t _{w(CKL)}	high and low time	I AHBCLK - 40 MI 12, presc-	U	t _(CK) /2 - 1	-	t _(CK) /2	
+	Data input setup	Voltage Range 1		2.5			
t _{sr(IN)}	time on rising edge	Voltage Range 2		3.5	-	-	
4	Data input setup	Voltage Range 1	Voltage Range 1				
t _{sf(IN)}	time on falling edge	Voltage Range 2		1.5	-		
+	Data input hold	Voltage Range 1 Voltage Range 2		5.5			
t _{hr(IN)}	time on rising edge			6.5	-	-	
t	Data input hold	Voltage Range 1		5			
t _{hf(IN)}	time on falling edge	Voltage Range 2		6	_	_	
		Voltage Range 1	DHHC=0		4	5.5	ns
t _{vr(OUT)}	Data output valid time on rising edge	Voltage Narige 1	DHHC=1	-	$t_{(CK)}/2 + 1$	t _(CK) /2 + 1.5	113
		Voltage Range 2			4.5	7	
		Voltage Range 1	DHHC=0		4	6	
t _{vf(OUT)}	Data output valid time on falling edge	Voltage Kange 1	DHHC=1	-	$t_{(CK)}/2 + 1$	t _(CK) /2 + 2	
	3 1 3 1	Voltage Range 2			6	7.5	
		Voltage Range 1	DHHC=0	2	-	-	
t _{hr(OUT)}	Data output hold time on rising edge	Voltage Range 1	DHHC=1	$t_{(CK)}/2 + 0.5$	-	-	
		Voltage Range 2		3.5	-	-	
		Voltage Range 1	DHHC=0	3	-	-	
t _{hf(OUT)}	Data output hold time on falling edge	Voltage Natige 1	DHHC=1	$t_{(CK)}/2 + 0.5$	-	-	
	3 2 3	Voltage Range 2		5	-	-	

^{1.} Guaranteed by characterization results.



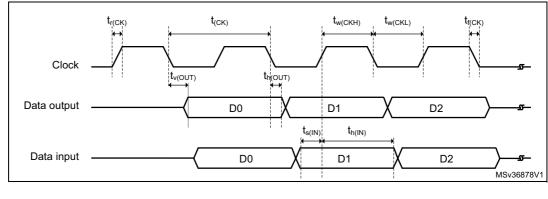
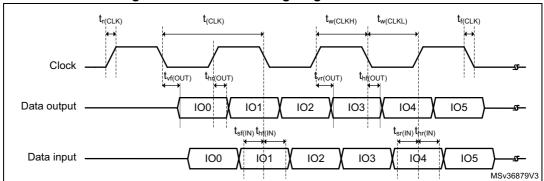


Figure 34. Quad-SPI timing diagram - SDR mode





SAI characteristics

Unless otherwise specified, the parameters given in *Table 96* for SAI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 24: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement are performed at CMOS levels: 0.5 x V_{DD}

Refer to Section 6.3.17 for more details on the input/output alternate function characteristics (CK,SD,FS).

Table 96. SAI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit	
f _{MCLK}	SAI main clock output	-	-	50		
		Master transmitter 2.7 V ≤ V _{DD} ≤ 3.6 V Voltage Range 1	-	23.5		
		Master transmitter 1.65 V ≤ V _{DD} ≤ 3.6 V Voltage Range 1	-	16		
		Master receiver Voltage Range 1	-	16	MHz	
f _{CK}	SAI clock frequency ⁽²⁾	Slave transmitter 2.7 V \leq V _{DD} \leq 3.6 V Voltage Range 1	-	26	IVITIZ	
		Slave transmitter 1.65 V ≤ V _{DD} ≤ 3.6 V Voltage Range 1	-	20		
		Slave receiver Voltage Range 1	-	32		
		Voltage Range 2	-	8		
+	FS valid time	Master mode 2.7 V ≤ V _{DD} ≤ 3.6 V	-	21		
t _{v(FS)}	r 3 valid time	Master mode 1.65 V \leq V _{DD} \leq 3.6 V	-	30		
t _{h(FS)}	FS hold time	Master mode	10	-		
t _{su(FS)}	FS setup time	Slave mode	1.5	-		
t _{h(FS)}	FS hold time	Slave mode	2.5	-		
t _{su(SD_A_MR)}	Data input setup time	Master receiver	1	-		
t _{su(SD_B_SR)}	Data input setup time	Slave receiver	1.5	-		
t _{h(SD_A_MR)}	Data input hold time	Master receiver	6.5	-		
t _{h(SD_B_SR)}	Data input noid time	Slave receiver	2.5	-	ns	
+	Data output valid time	Slave transmitter (after enable edge) 2.7 V \leq V _{DD} \leq 3.6 V	-	19		
t _{v(SD_B_ST)}	Data output valid time	Slave transmitter (after enable edge) 1.65 V \leq V _{DD} \leq 3.6 V	-	25	-	
t _{h(SD_B_ST)}	Data output hold time	Slave transmitter (after enable edge)	10	-		
t	Data output valid time	Master transmitter (after enable edge) 2.7 V \leq V _{DD} \leq 3.6 V	-	18.5	18.5	
t _v (SD_A_MT)	Data output vallu tiffle	Master transmitter (after enable edge) $1.65 \text{ V} \leq \text{V}_{\text{DD}} \leq 3.6 \text{ V}$	- 25			
t _{h(SD_A_MT)}	Data output hold time	Master transmitter (after enable edge)	10	_		

^{1.} Guaranteed by characterization results.

^{2.} APB clock frequency must be at least twice SAI clock frequency.

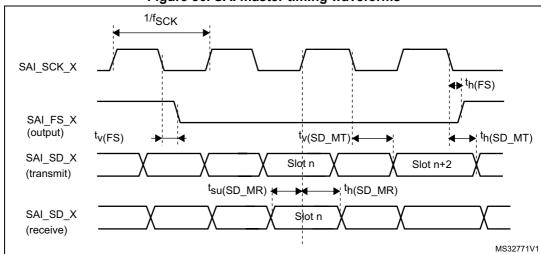
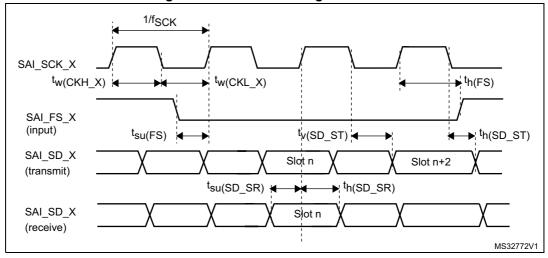


Figure 36. SAI master timing waveforms





USB characteristics

The STM32WB55xx and STM32WB35xx USB interface is fully compliant with the USB specification version 2.0, and is USB-IF certified (for Full-speed device operation).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DDUSB}	USB transceiver operating voltage	-	3.0 ⁽²⁾	-	3.6	V
T _{crystal_less}	USB crystal-less operation temperature	-	-15	-	85	°C
R _{PUI}	Embedded USB_DP pull-up value during idle	-	900	1250	1600	
R _{PUR}	Embedded USB_DP pull-up value during reception	-	1400	2300	3200	Ω
Z _{DRV} ⁽³⁾	Output driver impedance ⁽⁴⁾	Driving high and low	28	36	44	

Table 97, USB electrical characteristics⁽¹⁾

JTAG/SWD interface characteristics

Unless otherwise specified, the parameters given in *Table 98* and *Table 99* are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in *Table 24: General operating conditions*, with the following configuration:

- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V_{DD}

Table 98. JTAG characteristics

Symbol	Parameter	Parameter Conditions		Тур	Max	Unit
1/t _{c(TCK)}	TCK clock frequency	2.7 < V _{DD} < 3.6 V	-	-	29	MHz
	TCK clock frequency	1.65 < V _{DD} < 3.6 V	-	-	21	IVI⊓Z
t _{isu(TMS)}	TMS input setup time	-	2.5	-	-	
t _{ih(TMS)}	TMS input hold time	-	2	-	-	
t _{isu(TDI)}	TDI input setup time	-	1.5	-	-	
t _{ih(TDI)}	TDI input hold time	-	2	-	-	ns
t _{ov(TDO)}	TDO output valid time	2.7 < V _{DD} < 3.6 V	-	13.5	16.5	
		1.65 < V _{DD} < 3.6 V	-	13.5	23	
t _{oh(TDO)}	TDO output hold time	-	11	-	-	

^{1.} $T_A = -40$ to 125 °C unless otherwise specified.

^{2.} The STM32WB55xx and STM32WB35xx USB functionality is ensured down to 2.7 V, but the full USB electrical characteristics are degraded in the 2.7 to 3.0 V voltage range.

^{3.} Guaranteed by design.

^{4.} No external termination series resistors are required on USB_DP (D+) and USB_DM (D-); the matching impedance is already included in the embedded driver.

Table 99. SWD characteristics

Symbol	Parameter Conditions		Min	Тур	Max	Unit
1/t _{c(SWCLK)}	2.7 < V _{DD} < 3.6 V		-	-	55	MHz
	SWCLK clock frequency	1.65 < V _{DD} < 3.6 V	-	-	35	IVITZ
t _{isu(TMS)}	SWDIO input setup time	-	2.5	-	-	
t _{ih(TMS)}	SWDIO input hold time	-	2	-	-	
	SWDIO output valid time	2.7 < V _{DD} < 3.6 V	-	16	18	ns
^t ov(TDO)		1.65 < V _{DD} < 3.6 V	-	16	28	
t _{oh(TDO)}	SWDIO output hold time	-	13	-	-	

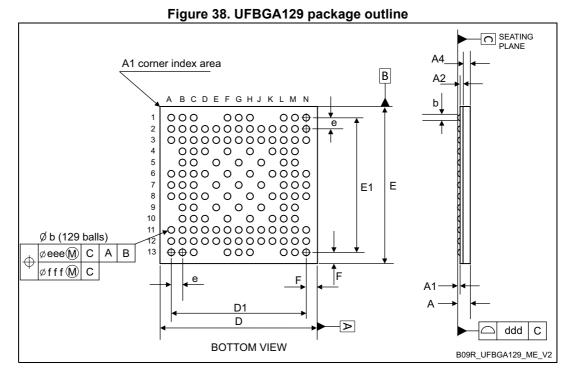
Refer to Section 6.3.17 for more details on the input/output alternate function characteristics (CK, SD, WS).

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

7.1 UFBGA129 package information

This UFBGA is a 129-ball, 7 x 7 mm, 0.5 mm fine pitch, square ball grid array package.



- 1. Drawing is not to scale.
- The terminal A1 corner must be identified on the top surface by using a corner chamfer, ink or metalized
 markings, or other feature of package body or integral heat slug.
 A distinguishing feature is allowable on the bottom surface of the package to identify the terminal A1
 corner. Exact shape of each corner is optional.

Symbol	millimeters			inches ⁽¹⁾			
	Min	Тур	Max	Min	Тур	Max	
A ⁽²⁾	-	-	0.60	-	-	0.024	
A1	-	-	0.11	-	-	0.004	
A2	-	0.13	-	-	0.005	-	
A4	-	0.32	-	-	0.013	-	
b ⁽³⁾	0.24	0.29	0.34	0.009	0.011	0.013	

Table 100. UFBGA129 mechanical data

Symbol	millimeters			inches ⁽¹⁾			
	Min	Тур	Max	Min	Тур	Max	
D	6.85	7.00	7.15	0.270	0.276	0.281	
Е	6.85	7.00	7.15	0.270	0.276	0.281	
D1	-	6.00	-	-	0.236	-	
E1	-	6.00	-	-	0.236	-	
е	-	0.50	-	-	0.020	-	
F	-	0.50	-	-	0.020	-	
ddd	-	-	0.08	-	-	0.003	
eee ⁽⁴⁾	-	-	0.15	-	-	0.006	
fff ⁽⁵⁾	-	-	0.05	-	-	0.002	

Table 100. UFBGA129 mechanical data (continued)

- 1. Values in inches are converted from mm and rounded to four decimal digits.
- 2. UFBGA stands for Ultra Thin Profile Fine Pitch Ball Grid Array.
 - Ultra thin profile: 0.50 < A ≤ 0.65 mm / Fine pitch: e < 1.00 mm pitch.
 The total profile height (Dim A) is measured from the seating plane to the top of the component
 - The maximum total package height is calculated by the following methodology:
 A Max = A1 Typ + A2 Typ + A4 Typ + √ (A1² + A2² + A4² tolerance values).
- 3. The typical balls diameters before mounting is 0.20 mm.
- 4. The tolerance of position that controls the location of the pattern of balls with respect to datum A and B. For each ball there is a cylindrical tolerance zone eee perpendicular to datum C and located on true position with respect to datum A and B as defined by e. The axis perpendicular to datum C of each ball must lie within this tolerance zone.
- 5. The tolerance of position that controls the location of the balls within the matrix with respect to each other. For each ball there is a cylindrical tolerance zone fff perpendicular to datum C and located on true position as defined by e. The axis perpendicular to datum C of each ball must lie within this tolerance zone. Each tolerance zone fff in the array is contained entirely in the respective zone eee above The axis of each ball must lie simultaneously in both tolerance zones.

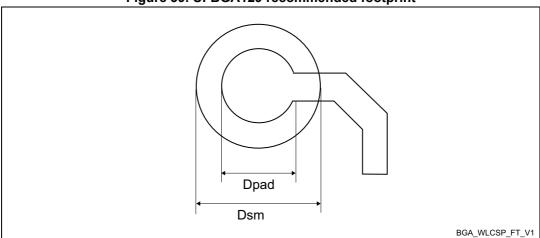


Figure 39. UFBGA129 recommended footprint

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 Dimension
 Recommended values

 Pitch
 0.5 mm

 Dpad
 0,275 mm

 Dsm
 0.400 mm typ. (depends on soldermask registration tolerance)

 Stencil opening
 0.300 mm

 Stencil thickness
 0.100 mm

Table 101. UFBGA129 recommended PCB design rules

Device marking for UFBGA129

Figure 40 gives an example of topside marking orientation versus pin 1 identifier location. The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

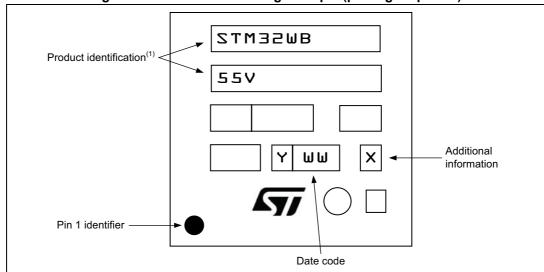


Figure 40. UFBGA129 marking example (package top view)

1. Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

7.2 WLCSP100 package information

This WLCSP is a 100-ball, 4.40 x 4.38 mm, 0.4 mm pitch, wafer level chip scale package.

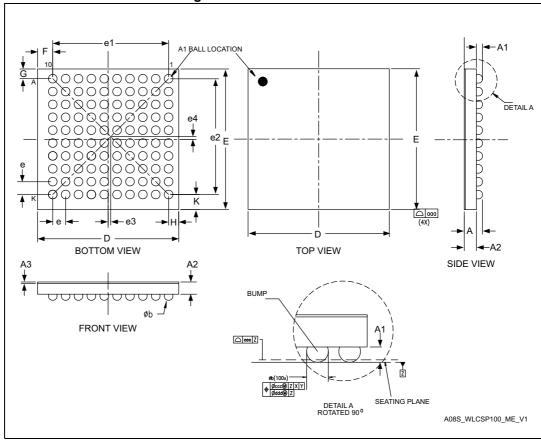


Figure 41. WLCSP100 outline

- 1. Primary datum Z and seating plane are defined by the spherical crowns of the bump.
- 2. Bump position designation per JESD 95-1, SPP-010.

Table 102. WLCSP100 mechanical data

Symbol	millimeters			inches ⁽¹⁾			
	Min	Тур	Max	Min	Тур	Max	
А	-	-	0.59	-	-	0.023	
A1	-	0.18	-	-	0.007	-	
A2	-	0.38	-	-	0.015	-	
A3 ⁽²⁾	-	0.025 ⁽³⁾	-	-	0.001	-	
b	0.22	0.25	0.28	0.009	0.010	0.011	
D	4.38	4.40	4.42	0.1724	0.1732	0.1740	
E	4.36	4.38	4.40	0.1716	0.1724	0.1732	
е	-	0.40	-	-	0.016	-	
e1	-	3.60	-	-	0.142	-	
e2	-	3.60	-	-	0.142	-	
e3	-	0.08	-	-	0.003	-	
e4	-	0.08	-	-	0.001	-	
F	-	0.480 ⁽⁴⁾	-	-	0.0189	-	
G	-	0.306 ⁽⁴⁾	-	-	0.0120	-	
Н	-	0.320 ⁽⁴⁾	-	-	0.0126	-	
K	-	0.474 ⁽⁴⁾	-	-	0.0187	-	
aaa	-	-	0.10	-	-	0.004	
bbb	-	-	0.10	-	-	0.004	
ccc	-	-	0.10	-	-	0.004	
ddd	-	-	0.05	-	-	0.002	
eee	-	-	0.05	-	-	0.002	

^{1.} Values in inches are converted from mm and rounded to the third decimal place.

^{2.} Back side coating.

^{3.} Nominal dimension rounded to the third decimal place results from process capability.

^{4.} Dimensions are calculated and rounded to the third decimal place.

Dpad Dsm BGA_WLCSP_FT_V1

Figure 42. WLCSP100 recommended footprint

Table 103. WLCSP100 - Recommended PCB design rules

Dimension	Recommended values				
Pitch	0.4 mm				
Dpad (PCB Cu pad diameter)	0.250 mm				
Dsm	0.325 mm typ. (depends on the soldermask registration tolerance)				
Stencil opening	0.250 mm				
Stencil thickness	0.100 mm				

Device marking for WLCSP100

Figure 43 gives an example of topside marking orientation versus pin 1 identifier location. The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

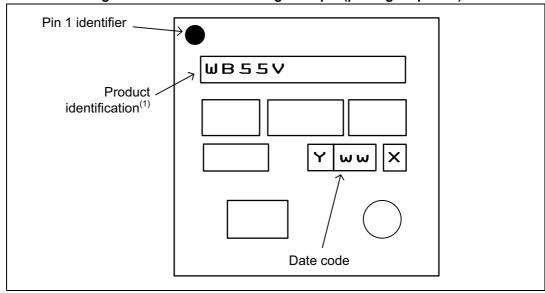


Figure 43. WLCSP100 marking example (package top view)

Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified
and therefore not approved for use in production. ST is not responsible for any consequences resulting
from such use. In no event will ST be liable for the customer using any of these engineering samples in
production. ST's Quality department must be contacted prior to any decision to use these engineering
samples to run a qualification activity.

7.3 VFQFPN68 package information

VFQFPN68 is a 8 x 8 mm, 0.4 mm pitch, very thin fine pitch quad flat package.

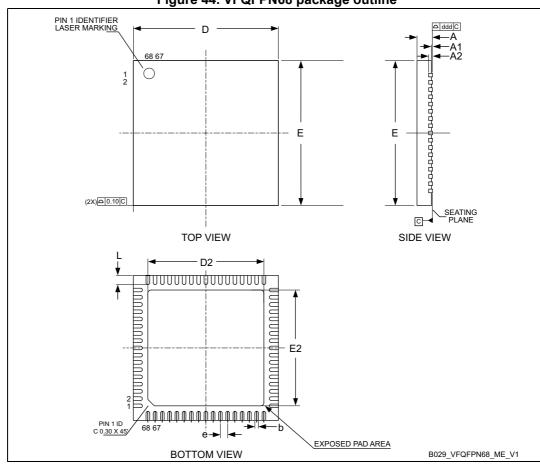


Figure 44. VFQFPN68 package outline

- 1. VFQFPN stands for Thermally Enhanced Very thin Fine pitch Quad Flat Packages No lead. Sawed version. Very thin profile: 0.80 < A ≤ 1.00 mm.
- 2. The pin #1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body. Exact shape and size of this feature is optional.

Table 104. VFQFFN00 Illectiallical data								
Symbol	millimeters			inches ⁽¹⁾				
	Min	Тур	Max	Min	Тур	Max		
А	0.80	0.90	1.00	0.0315	0.0354	0.0394		
A1	0	0.02	0.05	0	0.0008	0.0020		
A3	-	0.20	-	-	0.0008	-		
b	0.15	0.20	0.25	0.0059	0.0079	0.0098		
D	7.85	8.00	8.15	0.3091	0.3150	0.3209		
D2	6.30	6.40	6.50	0.2480	0.2520	0.2559		

Table 104. VFQFPN68 mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Тур	Max	Min	Тур	Max
Е	7.85	8.00	8.15	0.3091	0.3150	0.3209
E2	6.30	6.40	6.50	0.2480	0.2520	0.2559
е	-	0.40	-	-	0.0157	-
L	0.40	0.50	0.60	0.0157	0.0197	0.0236
ddd	-	-	0.08	-	-	0.0031

Table 104. VFQFPN68 mechanical data (continued)

^{1.} Values in inches are converted from mm and rounded to four decimal digits.

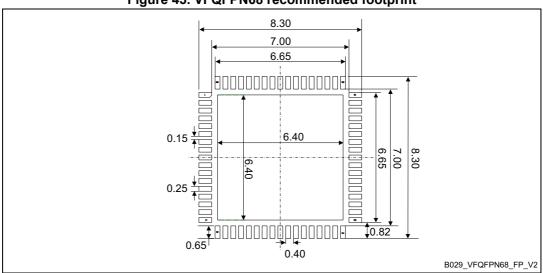


Figure 45. VFQFPN68 recommended footprint

1. Dimensions are expressed in millimeters.

Device marking for VFQFPN68

Figure 45 gives an example of topside marking orientation versus pin 1 identifier location. The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

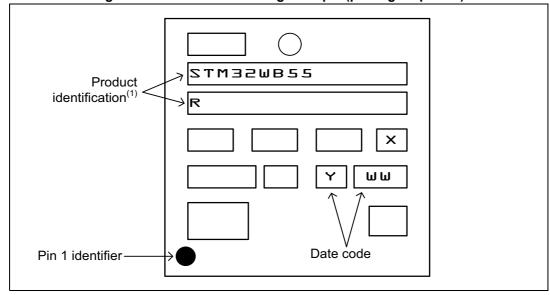


Figure 46. VFQFPN68 marking example (package top view)

Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified
and therefore not approved for use in production. ST is not responsible for any consequences resulting
from such use. In no event will ST be liable for the customer using any of these engineering samples in
production. ST's Quality department must be contacted prior to any decision to use these engineering
samples to run a qualification activity.

7.4 UFQFPN48 package information

UFQFPN48 is a 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package.

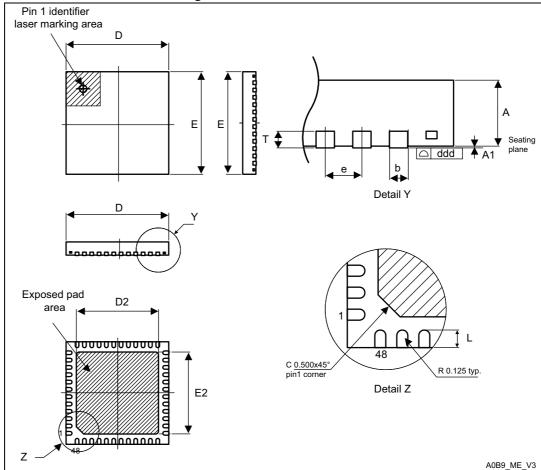


Figure 47. UFQFPN48 outline

- 1. Drawing is not to scale.
- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- There is an exposed die pad on the underside of the UFQFPN package, it must be electrically connected to the PCB ground.

Table	105.	UFQF	PN48	med	chanical	data

Symbol	millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
Т	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
е	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

^{1.} Values in inches are converted from mm and rounded to four decimal digits.

7.30 5.80 **◆** 0.50 0.75 0.55 A0B9_FP_V2

Figure 48. UFQFPN48 recommended footprint

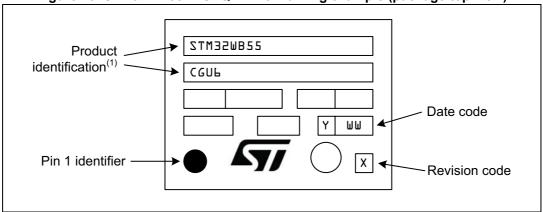
1. Dimensions are expressed in millimeters.

Device marking for UFQFPN48

Figure 49 and *Figure 50* give examples of topside marking orientation versus pin 1 identifier location. The printed markings may differ depending on the supply chain.

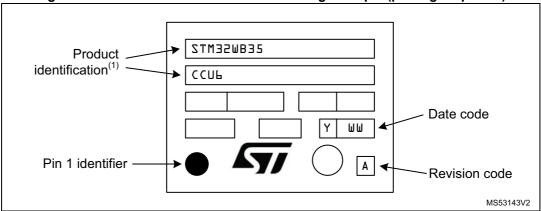
Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 49. STM32WB55xx UFQFPN48 marking example (package top view)



Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet
qualified and therefore not yet ready to be used in production and any consequences deriving from such
usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering
samples in production. ST Quality has to be contacted prior to any decision to use these Engineering
samples to run qualification activity.

Figure 50. STM32WB35xx UFQFPN48 marking example (package top view)



Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet
qualified and therefore not yet ready to be used in production and any consequences deriving from such
usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering
samples in production. ST Quality has to be contacted prior to any decision to use these Engineering
samples to run qualification activity.

7.5 Thermal characteristics

The maximum chip junction temperature (T_Jmax) must never exceed the values given in *Table 24: General operating conditions*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, can be calculated using the equation:

$$T_J \max = T_A \max + (P_D \max x \Theta_{JA})$$

where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C / W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$ max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watt. This is the maximum chip internal power.

P_{I/O} max represents the maximum power dissipation on output pins:

• $P_{I/O} \max = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DD} - V_{OH}) \times I_{OH})$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Note:

When the SMPS is used, a portion of the power consumption is dissipated into the external inductor, therefore reducing the chip power dissipation. This portion depends mainly on the inductor ESR characteristics.

Note:

As the radiated RF power is quite low (< 4 mW), it is not necessary to remove it from the chip power consumption.

Table 106. Package thermal characteristics

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient UFQFPN48 - 7 mm x 7 mm	24.9	
	Thermal resistance junction-ambient VFQFPN68 - 8 mm x 8 mm	47.0	°C/W
Θ_{JA}	Thermal resistance junction-ambient WLCSP100 - 0.4 mm pitch	35.8	C/VV
	Thermal resistance junction-ambient UFBGA129 - 0.5 mm pitch	41.5	
	Thermal resistance junction-board UFQFPN48 - 7 mm x 7 mm	13.0	
0	Thermal resistance junction-board VFQFPN68 - 8 mm x 8 mm	36.1	°C/W
Θ_{JB}	Thermal resistance junction-board WLCSP100 - 0.4 mm pitch	N/A	C/VV
	Thermal resistance junction-board UFBGA129 - 0.5 mm pitch	16.2	



Symbol	Parameter	Value	Unit
Θ_{JC}	Thermal resistance junction-case UFQFPN48 - 7 mm x 7 mm	1.3	
	Thermal resistance junction-case VFQFPN68 - 8 mm x 8 mm	13.7	°C/W
	Thermal resistance junction-case WLCSP100 - 0.4 mm pitch	N/A	C/VV
	Thermal resistance junction-case UFBGA129 - 0.5 mm pitch	34.9	

Table 106. Package thermal characteristics (continued)

7.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

7.5.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the information scheme shown in *Section 8*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and to a specific maximum junction temperature.

As applications do not commonly use the device at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine the temperature range that best suits the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_A max = 82 °C (measured according to JESD51-2), I_{DD} max = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL} = 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

 P_{INT} max = 50 mA × 3.5 V = 175 mW

 P_{IO} max = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INT} max = 175 mW and P_{IO} max = 272 mW

 $P_D \max = 175 + 272 = 447 \text{ mW}$

Using the values obtained in *Table 106* T_J max is calculated as follows:

For VFQFPN68, 47 °C / W

 $T_1 \text{ max} = 82 \text{ °C} + (47 \text{ °C} / \text{ W} \times 447 \text{ mW}) = 82 \text{ °C} + 21 \text{ °C} = 103 \text{ °C}$

This is within the range of the suffix 6 version parts ($-40 < T_J < 105$ °C), see Section 8.

In this case, parts must be ordered at least with the temperature range suffix 6.

Note:

With this given P_D max user can find the T_A max allowed for a given device temperature range (order code suffix 7).

Suffix 7:
$$T_A \max = T_J \max - (47 \ ^{\circ}\text{C} / W \times 447 \ \text{mW}) = 125 \ ^{\circ}\text{C} - 21 \ ^{\circ}\text{C} = 103 \ ^{\circ}\text{C}$$

Example 2: High-temperature application

Using the same rules, it is possible to address applications running at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_A max = 100 °C (measured according to JESD51-2), I_{DD} max = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

 P_{INT} max = 50 mA × 3.5 V = 175 mW

 P_{10} max = 20 × 8 mA × 0.4 V = 64 mW

This gives: $P_{INTmax} = 175 \text{ mW}$ and $P_{IO} \text{ max} = 64 \text{ mW}$

 $P_D \max = 175 + 64 = 239 \text{ mW}$

Thus: P_D max = 239 mW

Using the values obtained in *Table 106* T_J max is calculated as follows:

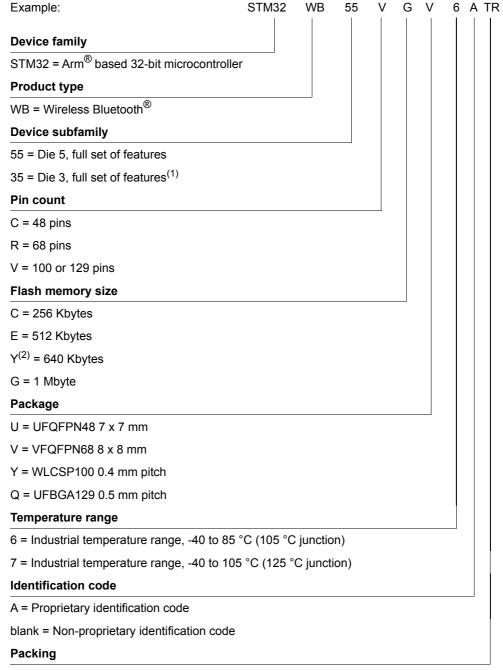
For UFQFPN48, 24.9 °C / W

 T_{J} max = 100 °C + (24.9 °C / W × 239 mW) = 100 °C + 6 °C = 106 °C

This is above the range of the suffix 6 version parts ($-40 < T_J < 105$ °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see Section 8), unless user reduces the power dissipation to be able to use suffix 6 parts.

8 Ordering information



TR = tape and reel

xxx = programmed parts

- STM32WB35xx only available with 48-pin UFQFPN48 package, 256 or 512 Kbytes flash memory.
- 2. Only STM32WB55VY, WLCSP100 package, temperature range -40 to 85 °C (105 °C junction).

9 Important security notice

The STMicroelectronics group of companies (ST) places a high value on product security, which is why the ST product(s) identified in this documentation may be certified by various security certification bodies and/or may implement our own security measures as set forth herein. However, no level of security certification and/or built-in security measures can guarantee that ST products are resistant to all forms of attacks. As such, it is the responsibility of each of ST's customers to determine if the level of security provided in an ST product meets the customer needs both in relation to the ST product alone, as well as when combined with other components and/or software for the customer end product or application. In particular, take note that:

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- Certification bodies have the right to evaluate, grant and revoke security certification in relation to ST products. These certification bodies are therefore independently responsible for granting or revoking security certification for an ST product, and ST does not take any responsibility for mistakes, evaluations, assessments, testing, or other activity carried out by the certification body with respect to any ST product.
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10 Revision history

Table 107. Document revision history

Date	Revision	Changes
25-Jul-2017	1	Initial release.
04-Apr-2018	2	Updated document title, Features, Section 1: Introduction, Section 2: Description, Section 3.1: Architecture, Section 3.3.2: Memory protection unit, Section 3.6: RF subsystem, Section 3.6.1: RF front-end block diagram, Section 3.6: RF subsystem, Section 3.6.1: RF front-end block diagram, Section 3.6: RF subsystem, Section 3.6.1: RF front-end block diagram, Section 3.6: RF subsystem, Section 3.6.1: RF front-end block diagram, Section 3.6: RF subsystem, Section 3.6.1: RF front-end block diagram, Section 3.6: RF subsystem, Section 3.7.4: Power supply distribution, Section 3.70: Clocks and startup, Section 3.74: Analog to digital converter (ADC), Section 3.19: True random number generator (RNG), Section 5: Memory mapping, Section 6.3.25: SMPS step-down converter characteristics and Section 7.5.2: Selecting the product temperature range. Updated Table 2: STM32WB55xx devices features and peripheral counts, Table 6: Power supply typical components, Table 7: Features over all modes, Table 8: STM32WB55xx modes overview, Table 13: Timer features, Table 15: Legend/abbreviations used in the pinout table, Table 16: STM32WB55xx pin and ball definitions, Table 17: Alternate functions, Table 23: RF transmitter BLE characteristics, Table 26: RF receiver BLE characteristics (1 Mbps) and added footnote to it, Table 28: RF BLE power consumption for VDD = 3.3 V, Table 31: RF 802.15.4 power consumption for VDD = 3.3 V, Table 37: Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART enable (Cache ON Prefetch OFF), VDD= 3.3 V, Table 38: Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1, VDD = 3.3 V, Table 40: Current consumption in Low-power sleep modes, Flash memory in Power down, Table 41: Current consumption in Stop 2 mode, Table 42: Current consumption in Stop 1 mode, Table 43: Current consumption in Stop 0 mode, Table 44: Current consumption in Standby mode, Table 45: Current consumption, Table 104: Package thermal characteristic

Table 107. Document revision history (continued)

Date	Revision	Changes
08-Oct-2018	3	Changed document classification to Public. Updated Features, Section 3.6.2: BLE general description, Section 3.7.2: Power supply schemes, Section 3.7.3: Linear voltage regulator, Section 3.10: Clocks and startup, Section 6.3.10: External clock source characteristics, Section 6.3.29: Communication interfaces characteristics, Section 6.3.29: Communication interfaces characteristics, Section 7.2: WLCSP100 package information and Section 7.5: Thermal characteristics, Section 8.29: Communication interfaces characteristics, Section 7.2: WLCSP100 package information and Section 7.5: Thermal characteristics, Section 7.2: WLCSP100 package information and Section 7.5: Thermal characteristics, Section 7.2: WLCSP100 package information and Section 7.5: Thermal characteristics and the section of the section of the section 7.5: Thermal characteristics and the section of the section of the section 7.5: Thermal characteristics and the section of the se



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Table 107. Document revision history (continued)

Date	Revision	Changes
08-Oct-2018		Updated Figure 2: STM32WB55xx RF front-end block diagram, Figure 14: Power supply scheme (all packages except UFBGA129), Figure 18: Typical energy detection (T = 27°C, VDD = 3.3 V) and Figure 25: I/O input characteristics. Added Figure 5: Power-up/down sequence, Figure 17: Typical link quality indicator code vs. Rx level and Figure 18: Typical energy detection (T =
	3 (cont'd)	27°C, VDD = 3.3 V). Added Table 24: RF transmitter BLE characteristics (1 Mbps), Table 25: RF transmitter BLE characteristics (2 Mbps), Table 27: RF receiver BLE characteristics (2 Mbps), Table 52: HSE crystal requirements and Table 89: Minimum I2CCLK frequency in all I2C modes.
		Added Device marking for UFQFPN48. Removed former Figure 22: I/O AC characteristics definition ⁽¹⁾ and Figure 27: SMPS efficiency - VDDSMPS = 3.6 V.
		Updated document title.
		Product status moved to Production data.
20-Feb-2019	4	Introduced BGA129 package, hence updated image on cover page, Table 16: STM32WB55xx pin and ball definitions and Section 8: Ordering information, and added Figure 11: STM32WB55Vx UFBGA129 ballout ⁽¹⁾ and Section 7.1: UFBGA129 package information.
		Updated Features, Section 3.3.4: Embedded SRAM, Section 3.17: Touch sensing controller (TSC) and Section 3.24: Low-power universal asynchronous receiver transmitter (LPUART).
		Added Section 6.3.28: Clock recovery system (CRS).
		Added Table 76: ADC sampling time.
	S	Removed former <i>Table 75: Maximum ADC RAIN</i> and <i>Table 84: SMPS</i> step-down converter characteristics.
		Updated captions of figures 8, 9 and 10.
		Updated Figure 43: VFQFPN68 recommended footprint.

Table 107. Document revision history (continued)

Date	Revision	Changes
20-Feb-2019	4 (cont'd)	Updated Table 2: STM32WB55xx devices features and peripheral counts, Table 8: STM32WB55xx modes overview and its footnotes, Table 21: Main performance at VDD = 3.3 V, Table 22: General operating conditions, Table 23: RF transmitter BLE characteristics, Table 24: RF transmitter BLE characteristics (1 Mbps), Table 25: RF transmitter BLE characteristics (2 Mbps), Table 26: RF receiver BLE characteristics (1 Mbps), Table 27: RF receiver BLE characteristics (2 Mbps), Table 27: RF receiver BLE characteristics (2 Mbps), Table 28: RF BLE power consumption for VDD = 3.3 V, Table 29: RF transmitter 802.15.4 characteristics, Table 31: RF 802.15.4 power consumption for VDD = 3.3 V, Table 35: Current consumption in Run and Low-power run modes, code with data processing running from Flash, ART enable (Cache ON Prefetch OFF), VDD = 3.3 V, Table 36: Current consumption in Run and Low-power run modes, code with data processing running from SRAM1, VDD = 3.3 V, Table 37: Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART enable (Cache ON Prefetch OFF), VDD = 3.3 V, Table 38: Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1, VDD = 3.3 V, Table 39: Current consumption in Sleep and Low-power sleep modes, Flash memory ON, Table 40: Current consumption in Low-power sleep modes, Flash memory in Power down, Table 41: Current consumption in Stop 1 mode, Table 43: Current consumption in Stop 0 mode, Table 44: Current consumption in Standby mode, Table 45: Current consumption in Shutdown mode, Table 46: Current consumption in VBAT mode, Table 47: Current under Reset condition, Table 48: Peripheral current consumption and its footnotes, Table 49: Low-power mode wakeup timings, Table 50: Regulator modes transition times and its footnote 1, Table 65: EMS characteristics, Table 66: EMI characteristics, Table 67: ESD absolute maximum ratings, Table 66: EMI characteristics, Table 67: ESD absolute maximum ratings, Table 69: I/O current injecti
04-Oct-2019	5	Updated Features, Section 2: Description, Section 6.1.6: Power supply scheme, Section 6.2: Absolute maximum ratings and Section 7.2: WLCSP100 package information. Updated Table 6: Power supply typical components, Table 7: Features over all modes, Table 11: Temperature sensor calibration values, Table 16: STM32WB55xx pin and ball definitions, Table 17: Alternate functions, Table 21: Main performance at VDD = 3.3 V, Table 26: RF receiver BLE characteristics (1 Mbps), Table 34: Embedded internal voltage reference, Table 62: PLL, PLLSAI1 characteristics and Table 67: ESD absolute maximum ratings. Updated Figure 6: Power supply overview and Figure 33: Quad-SPI timing diagram - DDR mode. Added Figure 15: Power supply scheme (UFBGA129 package) and Figure 21: Low-speed external clock source AC timing diagram. Added Table 56: Low-speed external user clock characteristics — Bypass mode.



Table 107. Document revision history (continued)

Date	Revision	Changes
		Updated Features, Section 2: Description, I/O system current consumption, Section 3.17: Touch sensing controller (TSC), Section 7.1: UFBGA129 package information, Section 7.2: WLCSP100 package information, Section 7.3: VFQFPN68 package information, Section 7.4: UFQFPN48 package information, Section 7.5: Thermal characteristics and Section 8: Ordering information. Added JTAG/SWD interface characteristics, Device marking for UFBGA129, Device marking for WLCSP100 and Device marking for VFQFPN68.
19-Feb-2020	6	Updated Table 2: STM32WB55xx devices features and peripheral counts, Table 7: Features over all modes, Table 16: STM32WB55xx pin and ball definitions, Table 17: Alternate functions, Table 18: Voltage characteristics, Table 22: General operating conditions, Table 26: RF receiver BLE characteristics (1 Mbps), Table 27: RF receiver BLE characteristics (2 Mbps), Table 30: RF receiver 802.15.4 characteristics, Table 47: Current under Reset condition, Table 61: LSI2 oscillator characteristics and Table 104: Package thermal characteristics. Added footnote 5 to Table 15: Legend/abbreviations used in the pinout table.
		Updated Figure 2: STM32WB55xx RF front-end block diagram, Figure 6: Power supply overview, Figure 7: Clock tree, Figure 11: STM32WB55Vx UFBGA129 ballout ⁽¹⁾ , Figure 14: Power supply scheme (all packages except UFBGA129), Figure 36: UFBGA129 package outline and Figure 47: UFQFPN48 marking example (package top view).
10-Apr-2020	7	Updated Section 3.6.5: Typical RF application schematic and Section 6.3.10: External clock source characteristics. Updated Table 16: STM32WB55xx pin and ball definitions and Table 54: HSE crystal requirements. Updated Figure 11: STM32WB55Vx UFBGA129 ballout ⁽¹⁾ and Figure 14:
		Power supply scheme (all packages except UFBGA129). Minor text edits across the whole document.
17-Jun-2020	8	Introduced STM32WB55VY. Updated Section 3.3.4: Embedded SRAM, Section 3.4: Security and safety, Section 3.14: Analog to digital converter (ADC), Section 6.3.10: External clock source characteristics and Section 8: Ordering information. Updated Table 1: Device summary, Table 2: STM32WB55xx and STM32WB35xx devices features and peripheral counts, Table 26: RF transmitter Bluetooth Low Energy characteristics (1 Mbps), Table 27: RF transmitter Bluetooth Low Energy characteristics (2 Mbps), Table 65: Flash memory characteristics and Table 77: ADC characteristics. Updated Figure 10: STM32WB55Cx and STM32WB35Cx UFQFPN48 pinout (1)(2), Figure 11: STM32WB55Rx VFQFPN68 pinout (1)(2) and Figure 17: Power supply scheme (UFBGA129 and WLCSP100 packages). Updated footnote 5 of Table 15: Legend/abbreviations used in the pinout table and footnote 8 of Table 16: STM32WB55xx pin and ball definitions. Added footnote 3 to Table 16, footnote 2 to Figure 16, footnote 1 to Table 86 and footnotes to tables 23, 30 and 33. Added Table 55: HSE clock source requirements.



Table 107. Document revision history (continued)

Date	Revision	Changes
02-Jul-2020	9	Added STM32WB35xx devices. Updated Section 2: Description, Section 3.3.4: Embedded SRAM and Section 8: Ordering information. Updated Table 1: Device summary, Table 2: STM32WB55xx and STM32WB35xx devices features and peripheral counts, Table 7: Features over all modes and Table 106: Package thermal characteristics. Added Table 17: STM32WB35xx pin and ball definitions and Table 19: Alternate functions (STM32WB35xx). Added Figure 2: STM32WB35xx block diagram, Figure 8: STM32WB35xx - Power supply overview and Figure 50: STM32WB35xx UFQFPN48 marking example (package top view), Updated Figure 1: STM32WB55xx block diagram, Figure 4: External components for the RF part, Figure 16: Power supply scheme (all packages except UFBGA129 and WLCSP100), Figure 17: Power supply scheme (UFBGA129 and WLCSP100 packages) and added footnote to Figure 9: Clock tree. Added footnote 1 to Table 8: STM32WB55xx and STM32WB35xx modes overview.
23-Nov-2020	10	Updated Features, Section 3.15: Voltage reference buffer (VREFBUF) and Section 3.28.2: Embedded Trace Macrocell™. Updated Table 9: STM32WB55xx and STM32WB35xx CPU1 peripherals interconnect matrix, Table 17: STM32WB35xx pin and ball definitions, Table 26: RF transmitter Bluetooth Low Energy characteristics (1 Mbps), Table 27: RF transmitter Bluetooth Low Energy characteristics (2 Mbps), Table 31: RF transmitter 802.15.4 characteristics, Table 50: Peripheral current consumption, Table 54: HSE crystal requirements, Table 55: HSE clock source requirements, footnote 2 of Table 57: Low-speed external user clock characteristics and Table 86: V _{BAT} monitoring characteristics. Added footnote 2 to Table 24, footnote 2 to Table 26 and footnote 2 to Table 27. Updated Figure 9: Clock tree and Figure 13: STM32WB55Vx UFBGA129 ballout(¹¹). Minor text edits across the whole document.

Table 107. Document revision history (continued)

Date	Revision	Changes
07-Apr-2021	11	Updated document title, Features, Section 1: Introduction, Section 2: Description, Section 3.3.4: Embedded SRAM, Section 3.6: RF subsystem, Section 3.6.2: Bluetooth Low Energy general description and Section 6.1.2: Typical values, Section 6.3.10: External clock source characteristics. Updated Table 2: STM32WB55xx and STM32WB35xx devices features and peripheral counts, Table 16: STM32WB55xx pin and ball definitions, Table 17: STM32WB35xx pin and ball definitions, Table 18: Alternate functions (STM32WB55xx), Table 19: Alternate functions (STM32WB35xx), Table 23: Main performance at VDD = 3.3 V, Table 50: Peripheral current consumption, Table 53: Wakeup time using USART/LPUART and Table 55: HSE clock source requirements. Updated Figure 3: STM32WB55xx and STM32WB35xx RF front-end block diagram, Figure 9: Clock tree, Figure 16: Power supply scheme (all packages except UFBGA129 and WLCSP100), Figure 17: Power supply scheme (UFBGA129 and WLCSP100 packages) and Figure 29: ADC accuracy characteristics. Removed former footnote 3 from Table 83: VREFBUF characteristics.
11-Jan-2022	12	Updated Features, Section 3.6.2: Bluetooth Low Energy general description, Section 3.10: Clocks and startup and Section 7.5: Thermal characteristics. Updated Figure 7: STM32WB55xx - Power supply overview, Figure 29: ADC accuracy characteristics, Figure 30: Typical connection diagram using the ADC and its footnotes, Figure 41: WLCSP100 outline and its footnotes, Figure 42: WLCSP100 recommended footprint and Figure 49: STM32WB55xx UFQFPN48 marking example (package top view). Updated Table 24: General operating conditions, Table 26: RF transmitter Bluetooth Low Energy characteristics (1 Mbps), Table 27: RF transmitter Bluetooth Low Energy characteristics (2 Mbps), Table 83: VREFBUF characteristics, Table 101: UFBGA129 recommended PCB design rules, Table 102: WLCSP100 mechanical data and Table 103: WLCSP100 - Recommended PCB design rules. Minor text edits across the whole document.
07-Jun-2022	13	Updated document title, Features, Section 2: Description, Section 3.6: RF subsystem, Section 3.6.2: Bluetooth Low Energy general description, and Section 6.3.25: SMPS step-down converter characteristics. Updated footnote 2 of Table 23: Main performance at VDD = 3.3 V, footnotes of Table 54: HSE crystal requirements, and added footnote to Table 56: HSE oscillator characteristics. Updated Table 68: EMI characteristics for fHSE / fCPUM4, fCPUM0 = 32 MHz / 64 MHz, 32 MHz, Table 72: I/O static characteristics and its footnote 7. Updated Figure 31: SPI timing diagram - Slave mode and CPHA = 0, Figure 32: SPI timing diagram - Slave mode and CPHA = 1, Figure 40: UFBGA129 marking example (package top view), Figure 43: WLCSP100 marking example (package top view), and Figure 46: VFQFPN68 marking example (package top view). Added Section 9: Important security notice. Minor text edits across the whole document.

Table 107. Document revision history (continued)

Date	Revision	Changes
12-Aug-2022	14	Updated Features. Added footnote 9 to Table 72: I/O static characteristics. Minor text edits across the whole document.

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